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AB INITIO CALCULATIONS OF THE PROPERTIES OF INDIUM ANTIMONIDE
AND INDIUM ARSENIDE

by

David Singh

Submitted to the School of Graduate Studies in
partial fulfillment of the requirements
for the degree of Ph.D. in Physics

Department of Physics

University of Ottawa

Ottawa, Canada



UNIVERSITÉ D'OTTAWA
UNIVERSITY OF OTTAWA

"The underlying physical laws necessary for the mathematical theory of a large part of physics and the whole of chemistry are thus completely known, and the difficulty is only that the exact application of these laws leads to equations much too complicated to be soluble. It therefore becomes desirable that approximate practical methods of applying quantum mechanics should be developed, which can lead to an explanation of the main features of complex atomic systems without too much computation."

P.A.M. Dirac

Proc. Roy. Soc. (London) 123, 714 (1929)

ABSTRACT

In this thesis *ab initio* pseudopotential calculations of structural properties and valence charge densities in InSb are reported both under normal conditions and at high pressures. The method is also applied to calculate valence charge densities in the related compound InAs. The results thus obtained are discussed in relation to the high pressure semiconductor-metal phase transitions.

In addition a calculation of second sound velocities for a number of hexagonal crystals is reported and related to experimental data on solid Helium. It is found that a previously noted discrepancy between the experimental and theoretical velocities in this material can be significantly reduced by using a different set of elastic constants.

The convergence of the special points method for Brillouin zone averages, which was used in the pseudopotential calculations, is studied in the context of self-consistent phonon calculations for rare gas crystals, the method being found to converge rapidly. Lastly a simple intuitive method for evaluating Madelung constants in layer crystals is given. The method is applied to the transition metal dichalcogenides and in particular to TaS₂.

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INTRODUCTION

The bonding and chemical nature of semiconductors has been a focal point of interest to solid state physicists for some time (1). - An important motivation has been to be able to calculate the properties of bulk semiconductors from a microscopic point of view in order to obtain a better understanding of the physical and chemical properties of these materials. The open 4-fold coordinated structure of these materials and the importance of chemical bonding in determining their properties makes an understanding of these materials in terms of the distribution of electronic charge in them particularly attractive. Although the work described here was undertaken for this reason it is worth noting that with the increasing commercial interest in novel structures such as strained layers (eg. Germanium/Silicon alloys on Silicon) and quantum well structures the interest in the nature of the bonding in semiconductors has become more than academic, the ability to reliably predict and understand the properties of semiconductor structures being of great importance.

InSb is an interesting material with potentially important device applications (2). Over a relatively small pressure and temperature range it is found to occur in a number of structures. In particular InSb occurs in zinc blende, body centered tetragonal and two orthorhombic structures in the range 0-400 degrees Celsius and 0-5 gigapascals (3). Amorphous InSb has been observed to transform to a crystalline NaCl type structure under pressure at room temperature and to remain in this phase at atmospheric pressure (4). It is intriguing that this structure cannot be obtained from crystalline InSb by applying pressure. The tetragonal phase is also metastable at atmospheric pressure and low temperatures. The extent of this polymorphism suggests that

InSb is a borderline material with considerable instability in its bonding. It seems reasonable that worthwhile insights into the nature of covalently bonded materials may be obtained from the study of such borderline substances, and particularly their similarities with and differences from prototypical materials such as Silicon. Here structural properties of InSb are studied in relation to its electronic charge distribution both under normal conditions and also under pressure.

The theoretical basis for the calculation is reviewed in Chapter 1; the methods used being discussed in detail in Chapter 2. A brief overview of the implementation of the total energy calculations is given in Appendix A. In Chapter 3 valence charge densities of InSb and the related material, InAs, are given both under normal conditions and also at reduced volumes corresponding to high pressures. These are discussed in terms of the high pressure semiconductor-metal phase transition and recent X-ray scattering measurements. Extending the work described in Chapter 3 polarization charge densities for a variety of distortions are reported in Chapter 4 along with calculated structural properties again at the free volume as well as at reduced volumes.

In Chapters 5, 6 and 7 some work in solid state physics not directly related to the above problem is reported. In Chapter 5 a calculation of second sound velocities in hexagonal crystals is described and it is shown that a discrepancy between the experimental and theoretical values for ω pointed out by Maris can be reduced if another set of elastic constants is used. In Chapter 6 the convergence of the special points method is studied for the evaluation of Brillouin zone averages used in self-consistent phonon calculations. It is found that the method converges rapidly in the cases studied. Finally in Chapter 7 formulae are derived for the evaluation of Madelung constants in layer crystals. These are applied to the transition

metal dichalcogenides. It is found that the results of Shen and Liang for the cation charges in TaS_2 can be significantly improved by using our more accurate Madelung constants.

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CHAPTER 1

Theoretical Background

A) Introduction

In solid state physics it has been a long standing goal to be able to calculate bulk properties of solids without resorting to empirical models. It was realized that one way to do this was to calculate the total energy of a solid under various conditions and thereby derive its response (1-3). From such calculations it is possible to derive a large amount of information. For example, it is possible to calculate the equilibrium structures of solids and the stability of different phases at $T=0$. By applying static external influences the elastic properties and other responses can be determined. Moreover, within the adiabatic approximation lattice dynamical properties such as phonon frequencies, anharmonic terms and phonon-phonon interactions can be calculated (4). The ability to calculate such anharmonic terms is of considerable importance since they are usually not directly measurable and cannot be reliably obtained using phenomenological models. For some time interatomic potentials have been used to calculate various properties of simple solids such as rare gas crystals. This work has been reviewed in detail elsewhere (5). To the extent that the atoms in a solid can be regarded as unaffected by the environment, if the potentials used are derived from atomic calculations, these results may be regarded as being obtained by an ab initio method.

However, in more complex solids such as semiconductors one would not expect such an approach to succeed. In the case of semiconductors it was recognized that a successful calculation would likely involve consideration of the electronic structure as opposed to regarding the solid as a collection of

atoms which interact amongst themselves as separate units.

While it was realized that in principle by using quantum mechanics the total energy of a system of electrons and ions could be calculated (1) until the late 1970's it was not recognized that such work might be feasible for semiconductors. The reasons why such calculations were regarded as impractical are several. First of all it is important to recognize that the changes in the total energy of semiconductors associated with, for example, structural changes or phonons are very small in relation to the total energy. This point is illustrated by some typical precisions that might be required to evaluate some properties from an energy calculation (see Table 1-1). In comparison typically the total energy might be of the order of 10 Ry/atom in a pseudopotential calculation and 1000 Ry/atom in an all electron calculation. Thus it is easy to see why it was not at all clear that the changes of interest would not be lost in numerical 'noise' were such a calculation undertaken. Special considerations for semiconductors include the following:

- (1) The charge density in these materials is highly nonspherical; in fact covalent bonds may be characterized by the buildup of charge in the bonding region.
- (2) The valence electrons interact fairly strongly with the ion cores compared with the situation in simple metals.
- (3) Both exchange and correlation (which is important in the bonds, i.e., in the region which is expected to be of interest) are important in these materials. To illustrate the importance of correlation, one may examine the case of Silicon (6) for which the Hartree-Fock band structure in which exchange is treated exactly is even worse than the results of SCF Hartree calculations which completely ignore exchange. The failure of the Hartree-Fock method arises from its neglect of correlation and subsequent overweighting of ionic configurations. In fact even for

Diamond the Hartree-Fock method is not entirely satisfactory (7).

TABLE 1-1. Precision Requirements for Total Energy Calculations

Quantity Desired	Precision Required (Ry/atom)
Cohesive energy	0.01
Lattice constant	0.001
Bulk modulus	0.001
Phonon eigenvectors	0.0001
Phonon anharmonicity	0.0001

B) Density Functionals and the Local Density Approximation

The key ingredient in treating the electronic structure of a covalent material is a way to include correlation in the calculation. Until a scheme could be devised for doing this calculations of the total energy in semiconductors could not be reliably accomplished. The breakthrough came in 1964 with the development of the density functional formalism by Hohenberg, Kohn and Sham (8,9). They showed:

- (1) All aspects of the electronic structure of a nondegenerate ground state are completely determined by its density, $n(r)$. That is that all physical properties of the ground state are functionals of its density and in particular the total energy is a functional of the density, $E(n)$.
- (2) For a given applied potential the true density is that which minimizes the total energy, $E(n)$. This property is known as the variational principle. In addition to establishing a way to determine the density the variational principle has an important consequence. An error in the charge density results in only a second order error in the energy.

The above is known as the Hohenberg-Kohn theorem. This result is particularly elegant because it shows that any physically interesting property

of the ground state can in principle be determined from an observable as opposed to a wave function which is not observable and which is to some degree arbitrary.

In 1965 Kohn and Sham (9) showed that the formalism could be expressed in terms of effective one particle equations.

$$[-\frac{1}{2} \nabla^2 + v(r) + V_H(n,r) + v_{xc}(n,r)] \phi_i = \epsilon_i \phi_i \quad (1-1)$$

$$n(r) = \sum_i |\phi_i(r)|^2 \quad (1-2)$$

$$v_{xc} = \frac{\delta \mathcal{E}_{xc}}{\delta n(r)} \quad (1-3)$$

Where the sum in Equation (1-2) is over the occupied orbitals.

$$E(n) = T(n) + \int v(r) n(r) dr + \frac{1}{2} \iint \frac{n(r) n(r')}{|r - r'|} dr dr' + \mathcal{E}_{xc}(n) \quad (1-4)$$

Equations (1-1)-(1-4) are the Kohn-Sham equations in atomic units. Equation (1-3) defines the exchange-correlation potential, $v_{xc}(n)$, in terms of the corresponding energy functional defined by Equation (1-4). Here $E(n)$ is the total energy functional, $T(n)$ is the kinetic energy, v is the external (to the electron system) potential and $V_H(n)$ is the Hartree potential. The total energy is given by

$$E(n) = \sum_i \epsilon_i - \frac{1}{2} \iint \frac{n(r) n(r')}{|r - r'|} dr dr' + \mathcal{E}_{xc}(n) - \int v_{xc}(n) n(r) dr \quad (1-5)$$

The above represents an exact formulation of the many particle problem. While the Kohn-Sham equations may not seem much more complicated than the Hartree SCF equations, in fact the many body problem is 'hidden' in the exchange-correlation potential which is an unknown functional of the charge density. Determining it would involve an exact solution of the many body problem. The utility of the formulation lies in the possibility of obtaining

accurate results using approximate functionals. The most commonly used method revolves around the local density approximation (LDA). The LDA consists of replacing the exchange correlation energy by the same local function of the density in all cases. The function used is that for the homogeneous electron gas which is for practical purposes known from Monte Carlo simulations (10). This approximation was first proposed in 1965 by Kohn and Sham in the paper they derived the Kohn-Sham equations in (9), although its origins can be traced back to the Thomas-Fermi approach and to Slater's local exchange potential (11).

Although solving the Kohn-Sham equations in the LDA is from a computational point of view not much more difficult than a Hartree calculation, in many cases the results are much better than the results of Hartree-Fock calculations which for solids are extremely time consuming. For the electron gas the LDA is exact by construction.

In general one would expect the LDA to work best in situations characterized by a nearly uniform charge density and to be unreliable in situations where the charge density fluctuates significantly on a scale of the reciprocal of the Fermi wavevector. In fact, the cases of interest here, atoms, molecules and solids, are in the latter category. In spite of this, good results have been obtained using the LDA in these cases.

Arguments explaining this unexpectedly good performance of the LDA have been given by Gunnarsson and Lundqvist (12). The explanation can be summarized as follows:

- (1) The exchange correlation energy depends on a spherical average over the exchange correlation hole.
- (2) In the LDA the charge excluded from the exchange correlation hole is exact.

(3) The LDA gives a fairly good description of the spherically averaged exchange correlation hole (13). In particular its size varies with density in the correct way.

These arguments unfortunately fall short of a demonstration that the LDA will give good results in all solid state applications. Perhaps the best reason to expect the approximation to be a good one is the large number of calculations in diverse situations for which it has been successful. These include calculations on bulk semiconductors, semiconductor surfaces, interfaces, metals, molecules and defects (13-30). For semiconductors ab initio calculations based on the use of the LDA typically yield lattice parameters, bulk moduli and phonon frequencies within a few percent of experimental values. This is a remarkable result in view of the fact that the only inputs to these calculations are atomic numbers.

It should be noted that in spite of its successes the LDA is not a panacea. First of all the density functional formalism is useful only for the ground state. Secondly, excitation energies and one-electron removal energies are not correctly described in the density functional formalism (31-36) and the LDA does not lead to accurate band structures (though it does normally yield the correct topology (37)). In particular the LDA tends to underestimate band gaps. This results from an incomplete cancellation of the self-interaction terms between the Coulomb interaction and the approximate exchange term in the Kohn-Sham equations (31) which yields a raising of the valence band eigenvalues relative to the conduction bands which are less localized. This effect is most important in systems with highly localized states such as rare gas solids, ionic crystals, and transition metals. The LDA is not adequate for calculating the band gaps of semiconductors typically underestimating them by about 40%.

C) Ab Initio Norm Conserving Pseudopotentials

The second key ingredient in making total energy calculations in semiconductors feasible came into being with the development of ab initio norm conserving pseudopotentials in 1979 (38-43). These enabled the carrying out of total energy calculations without explicitly treating the ion cores. Treating the cores explicitly in most systems would have resulted in a many fold increase in the computation required without contributing anything to the results. This is because most physically interesting properties of semiconductors are related to the arrangement of the valence electrons. Moreover, full nuclear potentials are very hard, that is plane wave matrix elements with these do not decrease rapidly with increasing wave vectors. This is in contrast with the situation using norm conserving pseudopotentials which are normally constructed to have a soft core. Thus the development of these pseudopotentials made it possible to use plane wave bases in ab initio calculations. This is of importance because although 'more efficient' basis sets exist they are in general optimal for a given structure. Thus in examining the changes in total energy with various distortions they would tend to yield unreliable results. For example while a basis of s and p localized orbitals might give good results in an undistorted tetrahedrally coordinated solid it would very likely yield very stiff bond bending force constants because of the lack of variational freedom in accommodating that distortion. This is in contrast to the situation using a plane wave basis which would likely require more computation to treat the undistorted solid but which could yield reliable results in the distorted solid as well. In fact it seems likely that in the case of a semiconductor with distortions, in order to obtain the same variational freedom using a localized basis as obtained with plane waves approximately the same number of basis functions may be required. This is related to the fact that the valence charge densities of the solid and

the free atoms are of similar magnitude suggesting that the nearly free electron and linear combination of atomic orbitals (LCAO) treatments are equally valid (or invalid) in these materials. Thus ab initio norm conserving pseudopotentials offer an advantage even in cases such as Hydrogen where treating the core presents no difficulty. Ho, Tao and Zhu (30) have recently treated NbH using norm conserving pseudopotentials with no localized basis functions at the Hydrogen atoms (they used localized d orbitals at the Nb sites to facilitate treatment of the highly localized d states in the transition metal).

The basic idea of a pseudopotential is to include the orthogonalization of the valence electron wavefunctions to the core by transforming the Hamiltonian. In this way the core electrons are included in an effective way without treating them explicitly. Thus all interactions between the core and valence electrons are transferred to the pseudopotential. The use of pseudopotentials can be traced back at least 50 years (44).

The procedure for generating these ab initio pseudopotentials is as follows:

- (1) Do an all electron density functional calculation on the atomic system in the configuration desired.
- (2) Construct a pseudopotential that gives the same lowest valence eigenvalues as the all electron calculation, and the same wavefunction outside a chosen core radius, r_c . These pseudopotentials are constructed to be norm conserving in that even when normalized the wavefunctions they yield are identical to those of the all electron calculation outside the core radius. Norm conservation is crucial in making these pseudopotentials transferable.

Hamann, Schluter and Chiang (38) showed that the above procedure leads to

pseudopotentials with two desirable features. The scattering properties of the all electron atoms are reproduced with minimum error and the electrostatic potential produced outside r_c is identical for the all electron and pseudocharge distributions. It should be noted that these pseudopotentials are not unique and that some schemes for generating them yield softer potentials than others. Moreover they are non-local, that is ℓ dependent.

Recently complete sets of norm conserving ab initio pseudopotentials have been published (45,46). These sets are expanded in error functions and Gaussians. As a result it is possible to evaluate the plane wave matrix elements analytically although the expressions that result are somewhat lengthy.

It should be noted that aside from the frozen core approximation, the use of pseudopotentials in a LDA calculation builds in the assumption that the overlap between the valence and core charge densities is small. This is because the exchange correlation potential is nonlinear. Thus if there is a significant overlap between the charge densities an error results from the implied linearization in using pseudopotentials, thereby reducing their transferability. This is not important in most materials with the exception of those containing 3d transition metal atoms. In these atoms the 3d electrons are highly localized in the core region. One scheme for dealing with this is to carry a representation of the core charge density along in the pseudopotential calculation using it in determining the exchange correlation potential (42,46). An alternate scheme is to treat both the outer-core and valence electrons explicitly using a pseudopotential for the inner-core electrons (43). This scheme involves more computational effort but may be superior in cases where the outer-core contributes to the bonding.

D) The Special Points Method for Brillouin Zone Averages

In a density functional calculation the charge density must be evaluated in each iteration of the Kohn-Sham equations. This charge density is defined as a sum over the occupied states which implies a Brillouin zone average. Moreover at each point in the sum the Hamiltonian matrix must be diagonalized. Because of the large number of basis functions required for convergence in a calculation based on plane waves (normally more than 100 per atom in the unit cell) it is crucial to evaluate the sum as efficiently as possible.

The special points method (47-49) is a highly efficient method for evaluating Brillouin zone averages. Using this method it has proved possible to accurately evaluate the charge densities in semiconductors (50) using a small number of points in the Brillouin zone (typically 2-10, although in some cases just one point may be adequate (47)). Singh and Varshni (51) have studied the scheme's convergence in the context of self-consistent phonon formalism and found that in the cases studied the convergence is equally rapid. This work is described in Chapter 6.

The basic idea behind the special points method is to replace a Brillouin zone average by a weighted average over a few representative q points in the zone. In this way the evaluation of the function to be averaged at a large number of points is avoided as is the explicit use of an interpolation formula. Since the method is discussed in detail elsewhere (47,48) here only the main results are given.

A function, $f(q)$, with the complete symmetry of the lattice can be expanded in symmetrized plane waves

$$f(q) = f_0 + \sum_{m=1}^{\infty} f_m A_m(q) \quad (1-6)$$

where

$$A_m(q) = \sum_j \exp(iq \cdot R_{jm}) \quad (1-7)$$

where the sum in equation (1-7) is over the m'th set of equivalent lattice vectors. The average of $f(q)$ over the Brillouin zone is f_0 . A set of special points is a set of n points, q_i , with weights, w_i , such that

$$\sum_{i=1}^n w_i A_m(q_i) = 0 \quad m = 1, \dots, N \quad (1-8)$$

$$\sum_{i=1}^n w_i = 1 \quad (1-9)$$

If N is sufficiently large it may be expected that the weighted average of $f(q)$ should be a good approximation to the average since the first N terms in the sum of equation (1-6) cancel while for a smooth function the coefficients f_m may be expected to decrease with increasing m . The method can also be applied in a direct way to functions lacking the complete symmetry of the lattice as discussed in reference 49. This is done by constructing a symmetric function with the same average. For electron densities this is done using information about the space group of the crystal in question. We note that the choice of the representative points does not depend on the function, f , although the convergence of the procedure depends critically on f . In particular the procedure does not converge rapidly for the charge density of metals because in this case the function to be averaged has a sharp edge (the Fermi surface) which gives rise to large Fourier components, f_m , even for large m .

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CHAPTER 2

Implementation of the Ab Initio Method

A) Introduction

In this chapter implementation of the LDA pseudopotential calculations for zinc blende structure semiconductors is discussed. The main equations used are given and some of the computational considerations are discussed.

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B) Formulation in Terms of a Plane Wave Basis

The equations giving the total energy of a crystal in the context of a pseudopotential calculation using the LDA have been presented elsewhere in detail (1,2). Here the main results are restated.

In order to use a plane wave basis the pseudopotential $V(r)$ must be divided into short and long range components. This is because the long ranged part must be treated differently as its Fourier transform diverges at $G=0$. For a physical pseudopotential the long ranged part is local. That is for an ℓ -dependent (non-local) pseudopotential all the angular momentum components have the same form for large r . The pseudopotential is divided as follows

$$V(r) = V_L(r) + \sum_{\ell=0}^{\infty} V_{\ell}(r) \hat{P}_{\ell} \quad (2-1)$$

where \hat{P}_{ℓ} are the angular momentum projection operators, V_L is the local component of the pseudopotential with the V_{ℓ} 's being the non-local components.

In a plane wave basis the pseudo Hamiltonian matrix elements for the Kohn-Sham equations at wavevector k in the Brillouin zone are given by:

$$H(k, G, G') = V_H(G'-G) + v_{xc}(G'-G) + \sum_{\tau} S_{\tau}(G'-G) \\ \times [V_{L\tau}(G'-G) + \sum_{\ell} V_{\ell\tau}(k+G, k+G')] \quad G \neq G' \quad (2-2)$$

$$H(k, G, G') = \frac{(k+G)^2}{2} + \sum_{\tau} \sum_{\ell} V_{\ell\tau}(k+G, k+G') \quad G = G' \quad (2-3)$$

where V_H is the Hartree potential and v_{xc} is the exchange correlation potential. In the $G=G'$ matrix elements the Hartree, exchange correlation and local pseudopotential terms have been set to zero. Although the Hartree and pseudopotential matrix elements diverge at $G=G'$ the result of setting them to zero is a constant finite shift in the eigenvalues because of the overall electrical neutrality of the crystal. The expression for the total energy per unit cell is

$$E = \sum_i \langle \epsilon_i \rangle_k - V_c \sum_{G \neq 0} [V_H^{in}(G) + v_{xc}^{in}(G)] n^{out}(G) + \\ \frac{1}{2} V_c \sum_{G \neq 0} V_H^{out}(G) n^{out}(G) + V_c \sum_G \epsilon_{xc}^{out}(G) n^{out}(G) + \\ \gamma_{Ewald} + \left(\sum_{\tau} \alpha_{1\tau} \right) \cdot \left(\sum_{\tau} Z_{\tau} \right) \quad (2-4)$$

Where V_c is the volume of the unit cell, Z_{τ} is the charge on core τ , γ_{Ewald} is the Ewald energy of the cores in a uniform compensating background and

$$\alpha_{1\tau} = \frac{1}{V_c} \int (V_{L\tau} + Z_{\tau}/r) d^3r \quad (2-5)$$

arises from the neglect of the $V_L(G=0)$ terms in the Hamiltonian. In equation (2-4) the superscripts in and out refer to the input and output of a cycle of the self-consistent loop. Although at the end of a true self-consistent calculation the inputs and outputs would be identical, the distinction has been retained in order to show which terms cancel self interactions in the eigenvalue sum. Chelikowsky and Louie (2) have shown that for a charge density close to the self-consistent charge density retaining the distinction

between inputs and outputs as in equation (2-4) ensures that the error in the energy is second order in the charge density error. Thus by retaining the distinction the energy can be made to converge much more rapidly in the self-consistent calculation. In order to calculate the exchange correlation energy the charge density was evaluated at about 12,000 points in the unit cell. At each point the exchange correlation energy was evaluated and thus the required average was obtained.

C) Pseudopotentials

The set of pseudopotentials used here are those tabulated by Bachelet, Hamann and Schluter (3). The exchange correlation energy used by them was generated from Monte Carlo simulations (4) and parameterized in Reference 5. In order to maintain consistency the same parameterization was used here. In this set the local component is expanded in error functions

$$V_L(r) = -\frac{Z_v}{r} \left[\sum_{i=1}^2 c_i^{\text{core}} \text{erf} [(\alpha_i^{\text{core}})^{1/2} r] \right] \quad (2-6)$$

and the non-local components are expanded in Gaussians

$$V_L(r) = \sum_{i=1}^3 (A_i^L + r^2 A_{i+3}^L) \exp(-\alpha_i r^2) \quad (2-7)$$

Here Z_v is the number of valence electrons in the neutral atom and the c 's, A 's and α 's are parameters. Because of degree of linear dependence among Gaussians, a transformed set of weights c was tabulated in Reference 3, instead of the A 's. Tabulating the latter would have required the retention of large numbers of significant figures.

$$c_i = -\sum_{j=1}^6 A_j Q_{ij} \quad (2-8)$$

where Q is the orthogonality matrix,

$$Q_{ij} = \begin{cases} 0 & i > j \\ S_{ij} - \sum_{k=1}^{i-1} Q_{ki}^2 & i = j \\ [S_{ij} - \sum_{k=1}^{i-1} Q_{ki} Q_{kj}] / Q_{ii} & i < j \end{cases} \quad (2-9)$$

and

$$S_{ij} = \int_0^{\infty} r^2 \phi_i(r) \phi_j(r) dr \quad (2-10)$$

with

$$\phi_i(r) = \begin{cases} e^{-\alpha_i r^2} & i = 1, 2, 3 \\ r^2 e^{-\alpha_i r^2} & i = 4, 5, 6 \end{cases} \quad (2-11)$$

Thus

$$S_{ij} = \begin{cases} \frac{\sqrt{\pi}}{4(\alpha_i + \alpha_j)^{3/2}} & i, j \leq 3 \\ \frac{3\sqrt{\pi}}{8(\alpha_i + \alpha_j)^{5/2}} & i \text{ or } j > 3 \\ \frac{5\sqrt{\pi}}{16(\alpha_i + \alpha_j)^{7/2}} & i, j > 3 \end{cases} \quad (2-12)$$

Equation (2-8) was inverted by factoring Q into a product of lower and upper triangular matrices and then performing back and forward substitutions. This algorithm was selected because of its high numerical stability which was important in view of the non-orthogonality of the basis. In terms of these pseudopotentials the required integrals can be evaluated analytically. They are

$$I_{\alpha} = \int_0^{\infty} r \operatorname{erfc}(ar) dr = 1/4a^2 \quad (2-13)$$

for the evaluation of α_1 ,

$$\frac{4\pi Z}{G V_c} \sum_{i=1}^2 \int_0^{\infty} c_i^{\text{core}} \operatorname{erf}(\sqrt{\alpha_i} r) \sin(\beta r) dr = \frac{-4\pi Z}{G^2 V_c} \sum_{i=1}^2 c_i^{\text{core}} e^{-\beta^2/4\alpha_i} \quad (2-14)$$

for the local matrix elements and

$$V_{\ell}(k, k') = (2\ell+1) \frac{4\pi}{V_c} \int_0^{\infty} V_{\ell}(r) j_{\ell}(|k|r) j_{\ell}(|k'|r) r^2 dr \quad (2-15)$$

$$\times P_{\ell}(\cos \gamma)$$

where

$$\cos(\gamma) = \frac{k \cdot k'}{|k| |k'|} \quad (2-16)$$

This requires the evaluation of two integrals

$$I_1 = \int_0^{\infty} \exp(-\alpha r^2) j_{\ell}(\beta r) j_{\ell}(\gamma r) r^2 dr \quad (2-17)$$

$$I_2 = \int_0^{\infty} \exp(-\alpha r^2) j_{\ell}(\beta r) j_{\ell}(\gamma r) r^4 dr \quad (2-18)$$

These are as follows.

$$I_1 = \frac{\pi}{4\alpha} e^{-(\beta^2 + \gamma^2)/4\alpha} \frac{1}{\sqrt{\beta\gamma}} I_{\ell + \frac{1}{2}} \left(\frac{\beta\gamma}{2\alpha} \right) \quad (2-19)$$

where I_n is a modified Bessel function. These were evaluated using a recursion relation for arguments greater in magnitude than 1.0 and a series expansion for smaller arguments.

$$I_2 = \frac{2}{\pi\sqrt{\beta\gamma}} U_{\ell}(\beta, \gamma, \sqrt{\alpha}) \quad (2-20)$$

where

$$U_{\ell}(a,b,p) = \frac{\Gamma(\ell + \frac{5}{2})}{2\pi p^4 \Gamma(2\ell+2)} \left(\frac{ab}{p^2}\right)^{\ell+\frac{1}{2}} \left\{ \left[1 - \frac{(a^2+b^2)}{(\ell + \frac{3}{2})4p^2} \right] S_{\ell}(a,b,p) + \frac{2ab}{(\ell + \frac{3}{2})4p^2} T_{\ell}(a,b,p) \right\} \quad (2-21)$$

with

$$S_{\ell}(a,b,p) = e^{-(a^2+b^2)/4p^2} \sum_{i=0}^{\ell} \frac{(-1)^i i! (2i)! (\ell-i)!}{\ell!} F_i^{-} \left(\frac{ab}{2p^2}\right) \quad (2-22)$$

$$T_{\ell}(a,b,p) = e^{-(a^2+b^2)/4p^2} \sum_{i=0}^{\ell} \frac{(-1)^i i! (2i+1)! (\ell-i)!}{\ell!} F_{i+\frac{1}{2}}^{+} \left(\frac{ab}{2p^2}\right) \quad (2-23)$$

and

$$F_i^{\pm}(x) = e^x \sum_{j=0}^{2i} \frac{(-1)^j x^{-(j+1)}}{(2i-j)!} \pm e^{-x} \sum_{j=0}^{2i} \frac{x^{-(j+1)}}{(2i-j)!} \quad (2-24)$$

Equation (2-24) was evaluated directly as written for arguments greater than 1.0 in magnitude. For smaller arguments it was evaluated by a power series expansion in the argument.

In this calculation spin-orbit interactions were neglected. While such an approximation is certainly not justified for a calculation of the band structure of a material such as InSb where spin-orbit splittings can be larger than the band gap (6) it may be expected to be reasonable in the context of the present calculation which is concerned with averaged properties i.e. charge densities and total energies and not the properties of states in a specific band at a specific point in the Brillouin zone. Recent relativistic calculations on SnTe and PbTe (7) tend to confirm this indicating that neglecting spin-orbit couplings is adequate for most purposes. Further support to this conclusion is provided by energy minimization calculations of

the surface structure of InSb using a tight binding method in which it was found that the structure of InSb surfaces is not affected very much by spin-orbit interactions (8). Errors resulting from this approximation are probably largest in the calculation of anharmonic force constants which are expected to be more dependent on the details of the band structure than harmonic quantities.

D) Ewald, Hartree and exchange correlation terms

In each iteration of the Kohn-Sham equations above the charge density, $n(\mathbf{g})$, must be evaluated in order to calculate the Hartree and exchange correlation potentials. In a plane wave basis the calculation of $n(\mathbf{g})$ is simplified by the fact that each of the basis functions has a definite crystal momentum so that the Fourier components $n(\mathbf{g})$ could be computed directly in reciprocal space.

In evaluating the charge density for a $N \times N$ Hamiltonian, N corresponding to the plane wave, G' , giving the largest kinetic energy, in principle Fourier components up to $G = 2G'$ result. Thus about $8N$ Fourier components of the charge density are produced which may contribute to the Hartree and exchange correlation potentials on the next iteration of the Kohn-Sham equations. In this calculation, however, Fourier components beyond $n(G')$ were set to zero. This had the advantage of a substantial saving in the computational resources required both because these terms did not have to be evaluated and because the reduced off-diagonal elements made the eigenvalue problem less time consuming. Thus an increase in the size of the Hamiltonians which could be considered resulted. Because only the lowest states are used in evaluating the ground state properties this procedure yields only a small change in the results for a given size, N , which is compensated by the larger Hamiltonian size which

could be treated.

The local exchange correlation functional used here was that calculated for the uniform electron gas by Ceperly and Alder (4) and parameterized by Perdew and Zunger (5). This is the same functional which was used in generating the pseudopotentials of Reference 3. Because the resulting local density functional is non-linear, the Fourier components of the exchange correlation potential could not be evaluated directly from the Fourier components of the charge density. Thus it was necessary to transform the charge densities at a number of points in the direct space unit cell, evaluate the exchange correlation potential at these points and then back transform these into reciprocal space. For this purpose a grid of about 12,000 points in the zinc blende unit cell were used, the exchange correlation energy term in the total energy expression also being evaluated in direct space as previously noted.

The remaining term in the total energy expression is the electrostatic interaction of the ion cores with each other and with a uniform compensating background. This was evaluated directly using Ewald's method (9) which permits the rapid evaluation of such energies in periodic structures. Ewald's method has also been used in calculating the energies of layers (see Chapter 7). It should be noted that all other interactions between the ion cores have been neglected in this calculation. In particular Born-Mayer repulsions and van der Waals' interactions were neglected. This was done because these were expected to result in negligible contributions to the total energy, the former because of the open tetrahedral structures in question and the later because the strong covalent bonds in these materials would render such effects negligible. Moreover, consideration of correlation between electrons in different ion cores is clearly beyond the scope of a pseudopotential calculation.

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CHAPTER 3

Valence charge densities in InSb and InAs

A) Introduction

For some time there has been considerable interest in the semiconductor-metal phase transitions diamond and zinc blende structure materials undergo when subjected to high pressures. With some exceptions (1-4) the transition at low temperatures is to a tetragonal β -Sn like structure or a rock salt structure, the high pressure structure being related to the ionicity of the material in question (4). Materials with low ionicities tend to have β -Sn like high pressure phases while more ionic materials tend to transform to rock salt structures. Among the III-V Indium compounds InP and InAs have rock salt high pressure phases while InSb has a β -Sn like phase. In either case the phase transition under pressure involves a change in coordination number and the breaking of covalent bonds.

Covalently bonded materials may be characterized by their highly nonspherical charge densities which are associated with a charge buildup in the bonds. The first (5) and perhaps the most direct experimental evidence of the existence of these bond charges was the observation of quasiforbidden X-ray reflections such as the (222) reflection in diamond structure materials. For zinc blende materials whose constituent atoms have similar atomic numbers such as AlP, GaAs and InSb the X-ray structure factors $F(222)$ and $F(\bar{2}\bar{2}\bar{2})$ can yield a considerable amount of information regarding the valence electron distributions (6), specifically the (222) component of the Fourier transform. In zinc blende materials the (222) components of the valence charge densities may be regarded as containing contributions from two sources, the bond charges and charge buildups about the anions. This is in contrast to the situation in

diamond structure materials where only the first contribution can occur.

Recently the intensities of these X-ray reflections have been measured as a function of pressure for both Silicon and InSb (7). It was found that as the pressure was increased both materials behaved similarly in that these intensities fell off sharply just before the transition pressures were reached. This is a remarkable result in view of the fact that for such a strongly first order transition large fluctuations in the vicinity of the phase transition are not normally expected. Subsequently it was suggested that the (222) X-ray intensity may be a useful order parameter for the semiconductor-metal phase transition in diamond structure materials (8). Two interpretations of the experimental observations were offered (7). Firstly it was suggested that the valence electrons may have redistributed just before the transition volume was reached, this redistribution presumably destabilizing the tetrahedrally coordinated structures and leading to the phase transition. The second interpretation offered was that the decrease in the intensities may have resulted from the enhancement of an anharmonic effect related to the phase transition. The first possibility has been excluded for Silicon by an ab initio calculation of the valence charge density as a function of pressure (9), which showed that the low temperature X-ray structure factor, $F(222)$, does not display any rapid changes near the transition volume. As yet the exact cause of the experimental observation is not known.

In this chapter charge densities and X-ray structure factors for InSb, calculated using the ab initio pseudopotential method described in Chapter 2, are reported at several volumes. In addition since it was felt that it would be desirable to study the behaviour of the valence electrons as a function of volume for a more ionic material having a rock salt high pressure phase,

valence charge densities for InAs were also calculated and are reported here.

B) Method and Results

For both InSb and InAs the calculations were done using a set of two special points in the irreducible wedge of the Brillouin zone. A basis of about 600 plane waves was employed for the calculations on InAs whereas for InSb about 530 plane waves were used. Increasing the number of plane waves to 725 at the experimental free volume, Ω_0 , was found to change the lower Fourier components of the charge density by less than 0.002 electrons per cell for InSb. For InAs comparison with a calculation using about 530 plane waves implied that a similar convergence had been attained.

In Table 3-1 the first few Fourier components of the charge densities are given at the free volume. These are compared with the results of an earlier calculation by Chelikowsky and Cohen (10). In spite of the fact that they used an empirical pseudopotential and only about 90 plane waves in their calculation, it may be noted that the results of their calculation agree fairly well with the results presented here. In Table 3-2 values of the X-ray structure factors $F(222)$ and $F(\bar{2}\bar{2}\bar{2})$ of zinc blende structure InSb for Cu K α radiation are presented. For InSb the transition occurs at about $\Omega/\Omega_0 = 0.945$. The requisite ionic scattering factors were taken from published results of Hartree-Fock calculations (11,12). It will be noted that the free volume results are in fairly good agreement with the low temperature values obtained by Bilderback and Collela. The effect of any errors in the ionic scattering factors would be to change the values obtained somewhat but leave the trend, i.e., the absence of any dramatic changes under pressure, intact. Correspondingly for InAs values of $n(222)$ at several volumes are presented in Table 3-3, the transition of InAs occurring at about $\Omega/\Omega_0 = 0.91$.

In addition the positions of the bond charge maxima are given in Table 3-4.

In Figure 3-1 contour plots of the calculated valence charge densities of zinc blende structure InSb at Ω_0 and at $\Omega/\Omega_0 = 0.847$ are presented in a (110) section. The difference is also shown. The results are qualitatively very similar to those obtained for Silicon in Reference 9. From these contour plots and the X-ray structure factors it may be concluded that there is no evidence for a dramatic redistribution of the valence charge density in InSb near the transition volume or even at volumes much smaller than it and moreover that the redistribution which does occur is mainly spherical about the ions. This result implies that the experimentally observed drop in the X-ray structure factors is very likely due to an anharmonic effect.

In Figure 3-2 (110) sections of the valence charge densities of zinc blende structure InAs are shown at $\Omega/\Omega_0 = 1.000, 0.898$ and 0.850 . These indicate that just as in the case of InSb there is no dramatic redistribution of the valence electrons as InAs is compressed and in particular that the bond charge remains a prominent feature of the zinc blende structure. There is however a gradual shift of the bond charge maxima away from the anion sites under pressure. This is reflected in the values of $n(222)$ which show a gradual phase shift and a small decrease in magnitude as the volume is reduced. This observation is consistent with the results of Raman scattering measurements which show that the splitting of the optical phonon decreases with increasing pressure implying that the effective charge, e_T^* , also decreases under pressure (14). There is a similar but smaller effect present in InSb as may be noted from Figure 3-1.

These results lend support to the idea that the semiconductor-metal phase transition is not caused by a redistribution of the electrons in the semiconductor but is related to the competition between the covalent bonding

energy with Madelung and repulsive energies as suggested by Yin and Cohen (9). This point will be discussed further in Chapter 4 where polarization charge densities associated with various distortions of the zinc blende lattice are reported.

TABLE 3-1 Fourier components of the charge density in electrons per cell for InSb and InAs at the free volume. The origin is at the cation site.

Component	Fourier Components			
	InAs		InSb	
	Ref. 10	This calculation	Ref. 10	This calculation
111	0.885, -1.998	0.659, -2.202	0.994, -1.915	0.846, -1.882
200	-0.860, 0	-1.238, 0	-0.718, 0	-0.766, 0
220	0.135, 0	0.177, 0	0.144, 0	-0.024, 0
311	-0.200, -0.151	-0.222, -0.092	-0.223, -0.161	-0.227, -0.267
222	0.030, -0.437	-0.035, -0.228	-0.020, -0.409	0.091, -0.252
400	-0.215, 0	-0.368, 0	-0.245, 0	-0.467, 0
331	0.040, 0.047	-0.022, 0.209	0.045, 0.038	-0.054, 0.223
420	0.055, 0	0.167, 0	0.048, 0	0.152, 0
422	-0.042, 0.020	-0.232, 0.031	-0.043, 0.024	-0.235, 0.015

TABLE 3-2 X-ray structure factors for InSb in the ZnS structure for Cu $k\alpha$ radiation.

Ω/Ω_0	F(222)	F($\bar{2}\bar{2}\bar{2}$)
1.035	6.41	5.23
1.000	6.42	5.26
0.985	6.42	5.26
0.938	6.44	5.29
0.892	6.45	5.33
0.847	6.46	5.37
0.804	6.48	5.41
0.762	6.49	5.46
0.722	6.50	5.51
0.646	6.51	5.61

TABLE 3-3 Fourier components of the charge density for InAs

Ω/Ω_0	n(222)	magnitude
1.055	(-0.060, -0.230)	0.238
1.000	(-0.035, -0.228)	0.231
0.948	(-0.001, -0.225)	0.225
0.898	(0.001, -0.221)	0.221
0.850	(0.037, -0.216)	0.219
0.804	(0.058, -0.211)	0.219

TABLE 3-4 Location of the bond charge maximum in zinc blende InAs.
x = 0 is a cation site whereas x = 1 is the anion site.
As-BC is the distance in atomic units of the bond charge
from an anion site.

Ω/Ω_0	x	As-BC
1.055	0.712	1.447
1.000	0.706	1.451
0.948	0.698	1.465
0.898	0.690	1.477
0.850	0.682	1.487
0.804	0.674	1.496

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CHAPTER 4

Structural Properties and Polarization Charges in InSb

A) Introduction

In Chapter 3 valence charge densities for zinc blende structure InSb at its free volume and at a reduced volume for which the semiconducting phase is unstable were reported. It was concluded that under pressure the behaviour of the valence electrons in InSb is qualitatively very similar to that found in Silicon (1) and InAs.

Here polarization charge densities and energies associated with various zone center phonons are reported for zinc blende structure InSb at its free volume and also at a reduced volume. These are discussed in relation to the corresponding quantities in other covalently bonded materials (2-4).

B) Results and Discussion

i) Total energy calculations

In Table 4-1 the equilibrium lattice constant, a_0 , bulk modulus, B , and its pressure derivative, B' , obtained by fitting total energies calculated using the method described in Chapter 2, at a variety of volumes, Ω , to Murnaghan's equation of state (5), are presented. The shear elastic constant, $2c_s = c_{11} - c_{12}$, c_{44} and the internal strain parameter, ζ , calculated both at the experimental free volume, Ω_0 , and at a reduced volume for which the zinc blende structure is unstable are also presented. (In InSb the semiconductor-metal phase transition occurs at about $\Omega/\Omega_0 = 0.945$.) The shear constant, c_s , was calculated from the total energy changes associated with homogeneous

tetragonal distortions in which one of the cube axes was stretched or compressed by a small amount (typically 1%) while the other two axes were also changed in order to keep the volume of the unit cell constant. The internal strain parameter and c_{44} were calculated from the energy changes associated with homogeneous trigonal distortions, relative displacements of the anion and cation sublattices along a bond direction and combinations of these. The values of c_s and c_{44} were found to change somewhat as the volume was reduced to $\Omega/\Omega_0=0.935$ from Ω_0 . However in view of the probable accuracy of this calculation it is difficult to attach much significance to these changes. However the increase in the internal strain parameter as the volume is reduced is significant, this increase reflecting an expected weakening of bond bending forces relative to bond stretching forces under pressure. The calculated elastic constants are compared with the low temperature experimental values obtained by Slutsky and Garland (6), the pressure derivative of the bulk modulus being compared to that measured by Bashkin and Peresada (7). It may be noted that the agreement between the experimental and theoretical values is reasonable although not quite as good as obtained for certain other materials using similar methods (8). The calculated internal strain parameter at the free volume, $\zeta=0.43$, is somewhat lower than experimental values (9-12) for Silicon (0.74,0.72), Germanium (0.72) and GaAs (0.764) but is comparable to previous ab initio calculations (13,14) on these materials which all yielded values lower than those found experimentally. As noted in Reference 13 the discrepancy is outside the probable limits of the theoretical uncertainty and may be due to the assumption of overlapping spherical atoms in the analysis of the experimental data (see Chapter 3) and anharmonicity due to finite strains. In fact the magnitude of $n(600)$ obtained in this calculation is 0.05 at zero strain and increases by about 6% under a 1% strain along a (111) direction. More importantly it is found that the transverse optical phonon becomes highly

anharmonic under strain as discussed below.

In Table 4-2 calculated frequencies of the zone center transverse optical phonon, ω_{TO} , and the corresponding anharmonic force constant, k_{xyz} , defined by:

$$\Delta E_{tot}(u) = ku^2 + 8 k_{xyz} \left(\frac{u}{\sqrt{3}}\right)^3 \quad (4-1)$$

are presented for the zinc blende structure. Here $\Delta E_{tot}(u)$ is the change in total energy per unit cell for a relative displacement between the two sublattices of $2u$. ω_{TO} and k_{xyz} were calculated with the same distortions used for c_{44} and ζ . It will be noted that at the free volume the experimental (15) and theoretical frequencies are in excellent agreement. The phonon frequency and anharmonic force constant increase smoothly over the entire volume range studied including the range for which the structure is unstable and can be well described by a Gruneisen parameter, $\gamma_{TO}=0.97$. The corresponding parameters for InP and InAs have been measured to be 1.44 (16) and 1.2 (17) respectively. Thus the present results would seem to suggest that InSb follows the chemical trend. However a recent state of the art Raman scattering study (18) has yielded a value of $\gamma_{TO}=1.41$. Although the phonon frequency obtained in that study does not agree to within the stated precision with a previous neutron scattering measurement (15), it seems unlikely that the discrepancy in the Gruneisen parameter can be explained by an experimental error. At present its source is unknown. In any case the present results do show that neither ω_{TO} nor k_{xyz} display any exceptional behaviour near the transition volume.

In Table 4-3 the anharmonic force constant k_{xyz} is given for (111) strains of 0.5% and 1%. The frequency, ω_{TO} , remained unchanged under these strains to within the accuracy of this calculation and thus is not shown. Under strain

k_{xyz} changes sign and increases dramatically in magnitude. While not conclusive, this result suggests that experimental determinations of the internal strain parameters in similar materials may indeed be affected by anharmonic effects caused by finite strains as suggested by Nielsen and Martin (13). This might also be related to a recently reported anisotropic stress sensitive temperature dependence of the lattice constant of Silicon (19) although it is not possible to arrive at any definite conclusion based on the present results.

ii) Charge densities

In Figure 4-1 (110) sections of the valence charge densities (a) and polarization charge densities for a frozen zone center TO phonon (b) and a homogeneous tetragonal distortion (c) are shown for zinc blende structure InSb both at the free volume and at a reduced volume, $\Omega/\Omega_0 = 0.935$. The polarizations shown correspond to 1% stretches of the 111 bonds for the optical phonon whereas for the tetragonal distortion a 1% stretch of the z-axes with a corresponding compression of the other two axes in order to maintain a constant volume was used. In order to make the redistribution more evident for the later case (c) the component corresponding to a rigid homogeneous distortion of the electron density has been eliminated.

As discussed in Chapter 3 the valence charge densities at the two volumes are very similar, the main difference consisting of a small movement of the bond charge maximum away from the anion sites under pressure consistent with Raman scattering measurements which indicate that under pressure the zone center LO-TO phonon splitting decreases in most zinc blende materials (17,18,20-24) implying a reduction in the effective charge, e_T^* . It is interesting to note that similar reductions are observed at high temperatures (25) perhaps reflecting the the similar nature of the high

pressure and high temperature (melting) phase transitions (26). Like the charge density it will be noted from Figure 4-1 that both the polarization charge of the TO phonon and that of the tetragonal shear distortion are very similar under pressure to the corresponding quantities at the free volume. While this may be expected for the TO phonon for which the forces are dominated by ion-ion interactions (27), this result for the tetragonal distortion lends further support to the conclusion of Yin and Cohen (1) that the semiconductor-metal phase transition is not caused by an instability in the electron distribution but rather a competition between the covalent bonding energies and the Ewald interactions.

The polarization associated with the TO phonon contains a strong dipole-like contribution which corresponds to a rigid displacement of much of the bond charge with the anion. There is also a small charge transfer from the stretched bond to the compressed bonds. This transfer is slightly off center in that the charge tends to flow to the region of the compressed bonds furthest from the stretched bond. The dominance of this dipole-like contribution in InSb is very similar to that found in ZnSe (3,4) in spite of the fact that InSb is much less ionic, having a Phillips ionicity of 0.321 as compared to 0.63 for ZnSe. The charge transfer among the bonds is less evident than that found in Silicon (2,14) and Germanium (3). The present results indicate that even for covalent materials with moderate ionicities the bond charges are fairly strongly associated with the anions.

The polarizations for the tetragonal distortion consist of small movements of the valence electrons towards the ions between bonds where the bond angles are reduced and conversely, a redistribution away from the ions between bonds where the bond angle is increased. The total bond charge is not changed much by this distortion.

To summarize, the behaviour of the valence electrons under high pressures, for which the zinc blende structure is unstable, is almost the same as that at the free volume. The fact that the covalent bonds are not destroyed under pressure as discussed here and in Chapter 3 may be qualitatively understood by making use of some of Phillips' ideas (28) and noting the strengthening of the pseudopotential in the bonding region as the volume is reduced. This arises because under pressure the minima in the Indium pseudopotentials move towards the bond charges which are located near the minima of the Antimony pseudopotentials. (The minimum of the Antimony pseudopotential is about 1.7 a.u. away from the anion sites while at the free volume the minimum of the Indium pseudopotential is about 3.7 a.u. away. The bond charge maximum is located about 1.85 a.u. from the anion.) This mechanism also helps to account for the movement of the bond charges away from the anions as the crystal is compressed since as the anion-cation distance is reduced the bond charges are expected to be influenced to a greater extent by the cation pseudopotentials.

C) Conclusion

In conclusion charge densities, polarizations and structural properties of zinc blende InSb have been calculated, reasonable agreement with experimental data being obtained. InSb is found not to behave much differently than other zinc blende materials in that the near instability of its bonding was found not to manifest itself in a substantially different response of its valence electrons to the distortions studied. This is consistent with the fact that even at greatly reduced volumes the responses were found not to be largely different from those at the free volume.

TABLE 4-1 Structural properties of zinc blende InSb. n denotes the size of the plane wave basis. The elastic constants are given in GPa while the lattice constant, a_0 , is in angstroms.

	Ω/Ω_0	This study		Experiment
		$n=531$	$n=725$	
a_0		6.34	6.34	6.49
B		50	50.7	48.31
B'		4.7	4.9	4.91
c_{44}	1.000	35		31.32
	0.935	34		
$c_{11}-c_{12}$	1.000	36		31.30
	0.935	38		
ζ	1.000	0.43		
	0.935	0.55		

TABLE 4-2 Frequency of the transverse optical phonon and the anharmonic force constant associated with it for zinc blende InSb. The frequencies are given in THz, whereas the force constants are in units of eV/angstrom³. The experimental value is denoted by (exp).

Ω/Ω_0	ω_{TO}	k_{xyz}
1.000	35.0	-38
1.0 (exp)	34.8	
0.985	35.6	-42
0.935	37.4	-44
0.892	39.3	-58
0.847	41.2	-71

TABLE 4-3 Anharmonic force constant as a function of strain, $e_{12}=e_{23}=e_{13}=e$, at the free volume.

e	k_{xyz}
0	-38
0.005	0
0.010	214

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CHAPTER 5

Second Sound Velocities in Hexagonal Crystals

A) Introduction

In 1944 Peshkov (1) observed second sound in superfluid ^4He and in 1947 proposed that similar propagating temperature waves may exist in solids (2). The first observation of second sound in a solid was for hcp ^4He (3). Second sound has since then provided valuable information on phonon scattering processes (4) and particularly normal processes. The condition for the existence of second sound is that there exist scattering mechanisms which cause a nonequilibrium phonon distribution to relax to an intermediate thermalized distribution with a net energy flux in a time that is short compared with that required for other processes to destroy it (5,6). Based on this two types of second sound have been identified by Enz (5), drifting second sound with a propagation velocity v_{II} , which occurs when normal processes yield a drifting phonon distribution in a time short compared with that required for other mechanisms to destroy it, and driftless second sound with a propagation velocity v'_{II} , which may occur when momentum (wave vector) correlations decay rapidly as compared with the energy flux.

All observations of second sound appear to be of the drifting variety with the possibility of observing driftless second sound uncertain at best (7). Despite this both v_{II} and v'_{II} are of considerable interest in studying scattering processes, the drifting velocity directly in experiments involving second sound and the driftless velocity because it enters in the Callaway expression for the thermal conductivity (8-10) which is frequently used in the analysis of experimental data on heat conduction.

Numerical calculations of second sound velocities for some cubic crystals have been performed by Varshni and Konti (11), Hardy and Jaswal (12) and Jaswal and Hardy (13). For anisotropic materials drifting second sound velocities have been calculated for hcp ^4He at $20.97 \text{ cm}^3/\text{mole}$ and Bismuth by Maris (14).

Here values of the drifting and driftless second sound velocities are presented for 12 hexagonal crystals with arbitrary orientations. The variation of the velocities with density for solid Helium is also given. Further it is shown that the discrepancy pointed out by Maris (14) between the experimental and theoretical values of v_{II} in hcp ^4He can be reduced if another set of elastic constants is used in the calculations.

B) Theory

i) Drifting second sound

It has recently been shown that neglecting dispersion, that is at temperatures much smaller, the Debye temperature, the drifting second sound propagation velocity is given by (14):

$$v_{II}^2 = n_1 n_2 (c_d^2)_{ij} \quad (5-1)$$

where (n_1, n_2, n_3) is a unit vector specifying the direction of second sound propagation and where

$$(c_d^2)_{ij} = \frac{1}{9} T_0 C_{ij}^{-1} \quad (5-2)$$

in which

$$C = (2 \frac{2}{3} k_B^4 T_0^3 / 5 \pi^3) \sum_{i=1}^5 \langle c_i^{-3}(\hat{k}) \rangle \quad (5-3)$$

$$\rho_{ij} = (2\pi^2 k_B^4 T_0^4 / 5\hbar^3) \sum_{\zeta=1}^3 \langle k_i k_j c_{\zeta}^{-5}(\hat{k}) \rangle \quad (5-4)$$

Here k_B is the Boltzmann constant, \hbar is Plank's constant and T_0 is the crystal temperature. The sum on ζ is over the three acoustic modes, c_{ζ} being the phase velocity of mode ζ in the direction \hat{k} . The averages are over \hat{k} .

Thus for hexagonal crystals the nonzero elements of $(c_d^2)_{ij}$ are

$$(c_d^2)_{xx} = (c_d^2)_{yy} = \frac{1}{9} \left[\sum_{\zeta=1}^3 \langle c_{\zeta}^{-3}(\hat{k}) \rangle \right] \left[\sum_{\zeta=1}^3 \langle k_y^2 c_{\zeta}^{-5}(\hat{k}) \rangle \right]^{-1} \quad (5-5)$$

$$(c_d^2)_{zz} = \frac{1}{9} \left[\sum_{\zeta=1}^3 \langle c_{\zeta}^{-3}(\hat{k}) \rangle \right] \left[\sum_{\zeta=1}^3 \langle k_z^2 c_{\zeta}^{-5}(\hat{k}) \rangle \right]^{-1}$$

x,y,z being orthogonal with z coinciding with the hexad axis.

ii) Driftless second sound

For the driftless case the following expression for the time derivative of the energy flux, $\vec{S}(\vec{r}, t)$, may be obtained (6):

$$\left[\frac{\partial}{\partial t} + \frac{1}{\tau} \right] S_i(\vec{r}, t) = - \frac{1}{\tau} K_{ij} \frac{\partial T(\vec{r}, t)}{\partial r_j} \quad (5-6)$$

where τ is a relaxation time characterizing the decay of modes giving rise to the energy flux, T is a local temperature and \vec{K}_{ij} is a single relaxation time approximation to the thermal conductivity,

$$K_{ij} = \tau (2\pi^2 k_B^4 T_0^3 / 5\hbar^3) \sum_{\zeta=1}^3 \langle \tilde{c}_{i\zeta}(\vec{k}) \tilde{c}_{j\zeta}(\vec{k}) / c_{\zeta}^3(\vec{k}) \rangle \quad (5-7)$$

where \tilde{c} is the group velocity. When Equation (5-6) is combined with the energy balance equation,

$$c \frac{\partial}{\partial t} T(r,t) + \frac{\partial}{\partial r_i} S_i(r,t) = 0 \quad (5-8)$$

a damped wave equation for $T(r,t)$ results

$$\frac{\partial^2 T(r,t)}{\partial t^2} + \frac{1}{\tau} \frac{\partial T(r,t)}{\partial t} - \frac{K_{ij}}{\tau c} \frac{\partial^2 T(r,t)}{\partial r_i \partial r_j} = 0 \quad (5-9)$$

which has three solutions, two of which do not involve heat propagation, the third one having a propagation velocity v'_{II} given by

$$v'_{II} = n_i n_j (c_{dl}^2)_{ij} \quad (5-10)$$

where the unit vector (n_1, n_2, n_3) specifies the direction of driftless second sound propagation.

For hexagonal crystals the nonzero elements of $(c_{dl}^2)_{ij}$ are

$$(c_{dl}^2)_{xx} = (c_{dl}^2)_{yy} = \left[\sum_{\zeta=1}^3 \langle \tilde{c}_{\zeta x}(k) / c_{\zeta}^3(k) \rangle \right] \left[\sum_{\zeta=1}^3 \langle c_{\zeta}^{-3}(k) \rangle \right]^{-1}$$

$$(c_{dl}^2)_{zz} = \left[\sum_{\zeta=1}^3 \langle \tilde{c}_{\zeta z}(k) / c_{\zeta}^3(k) \rangle \right] \left[\sum_{\zeta=1}^3 \langle c_{\zeta}^{-3}(k) \rangle \right]^{-1} \quad (5-11)$$

C) Hexagonal Symmetry

At low temperatures where second sound is dominated by low energy acoustic phonons the phonon frequencies $\omega_{\zeta}(k)$ and hence velocities $\tilde{c}_{\zeta}(k)$ are determined by the elastic constants c_{ijkl} of the material in question,

$$|c_{ijkl} k_j k_l - \rho \omega^2 \delta_{ik}| = 0 \quad (5-12)$$

$$\tilde{c}_\zeta(k) = \nabla_k \omega_\zeta(k) \quad (5-13)$$

For hexagonal crystals there are five independent elastic constants in terms of which the above eigenvalue problem can be solved exactly (15).

In this dispersionless case in order to obtain the second sound velocities it is necessary only to average over the direction of k . Thus

$$(c_d^2)_{xx} = (c_d^2)_{yy} = \frac{2}{9} \left[\int_0^{\pi/2} \sum_{\zeta=1}^3 c_\zeta^{-3}(\theta) \sin^3 \theta d\theta \right] \left[\int_0^{\pi/2} \sum_{\zeta=1}^3 c_\zeta^{-5}(\theta) \sin^3 \theta d\theta \right]^{-1}$$

$$(c_d^2)_{zz} = \frac{1}{9} \left[\int_0^{\pi/2} \sum_{\zeta=1}^3 c_\zeta^{-3}(\theta) \sin \theta d\theta \right] \left[\int_0^{\pi/2} \sum_{\zeta=1}^3 c_\zeta^{-5}(\theta) \cos^2 \theta \sin \theta d\theta \right]^{-1}$$

$$(c_{d\ell}^2)_{xx} = (c_{d\ell}^2)_{yy} = \left[\int_0^{\pi/2} \sum_{\zeta=1}^3 \bar{c}_{\zeta x}^2(\theta) c_\zeta^{-3}(\theta) \sin \theta d\theta \right] \quad (5-14)$$

$$\times \left[\int_0^{\pi/2} \sum_{\zeta=1}^3 \bar{c}_\zeta^{-3}(\theta) \sin \theta d\theta \right]^{-1}$$

$$(c_{d\ell}^2)_{zz} = \left[\int_0^{\pi/2} \sum_{\zeta=1}^3 \bar{c}_{\zeta z}^2(\theta) c_\zeta^{-3}(\theta) \sin \theta d\theta \right] \left[\int_0^{\pi/2} \sum_{\zeta=1}^3 c_\zeta^{-3}(\theta) \sin \theta d\theta \right]^{-1}$$

where the \bar{c} 's are appropriate averages over the angle $\phi = \tan^{-1}(k_2/k_1)$ and we have used the fact that for hexagonal crystals it is not necessary to average the phase velocities over ϕ .

D) Data and Results

The experimental data employed in the calculation are summarized in Table 5-1. For BeO two sets of elastic constants have been measured which differ from each other and appear to have the same sort of accuracy;

calculations were carried out for both sets and these are represented by BeO-1 and BeO-2 in the tables. The required integrals were evaluated numerically. The calculated values of the second sound velocities are shown in Table 5-2.

E) Discussion

There are a number of substances in Table 5-1 for which elastic constants are available only at room temperature. In such cases it is expected that the true low temperature second sound velocities will be slightly higher than those given in Table 5-2. Based on the temperature variations of the elastic constants of several tetrahedrally coordinated compounds and the melting points of the materials in question it is estimated that the deviation is less than 1% for SiC and BeO, 2% for ZnO, ZnS and CdS and 3% for ZnTe and CdSe. For CeF_3 we have not been able to find any data on the temperature variation of the elastic constants of similar compounds but it seems unlikely that the actual second sound velocities at 0K will be higher than those given in Table 5-2 by more than 10%.

To our knowledge so far the only detailed measurements of the anisotropy of v_{II} are those on hcp ^4He at 25 bar made by Mueller and Fairbank (16). Table 5-2 shows that the anisotropy of v_{II} is expected to be about 5% for AgI. For all other substances in the table with the exception of Helium the anisotropy in the v_{II} turns out to be less than 3%.

The propagation of second sound in ^4He has been studied by a number of workers. It was of some interest to examine the variation of second sound velocities with density for this substance. Greywall (17) has proposed that the elastic constants of ^4He have the following molar volume dependence:

$$c_{ij} = c_{ij} (v_0) (v_0/v)^{5.73} \quad (5-15)$$

This implies that the variations of second sound velocities with density are given by

$$v_{II}(\rho) = v_{II}(\rho_0) (\rho/\rho_0)^{2.365} \quad (5-16)$$

The variations of the velocities with density as given by this relation are shown by the full line curves in Figure 5-1 taking the velocities at ρ_0 to be those calculated using the elastic constants of Crepeau et al. (18). Also shown in Figure 5-1 are the second sound velocities calculated from the elastic constants of Frank and Wanner (19) at $\rho=0.19698 \text{ g/cm}^3$ and at $\rho=0.20760 \text{ g/cm}^3$ (second and third entries for ^4He in Table 5-2). It will be noticed that several of the points lie substantially above the corresponding curves. Thus it seems that there is an inconsistency between the elastic constants of Crepeau et al (18) and those of Frank and Wanner (19) or else that the relation (5-15) is not good enough. To further illustrate this point in Figure 5-2 the variation of the second sound velocities with density as calculated from the elastic constants of Frank and Wanner at $\rho=0.19698 \text{ g/cm}^3$ and Equation (5-16). The points calculated from the elastic constants at $\rho=0.20760 \text{ g/cm}^3$ lie close enough to the theoretical curve but those from the elastic constants of Crepeau et al. show substantial discrepancies.

Maris (14) has recently calculated the anisotropy of v_{II} in ^4He using elastic constants which are almost the same as those of Crepeau et al. and has found that the experimental second sound velocities measured by Mueller and Fairbank (16) are somewhat higher than the theoretical values. In view of the findings of the last paragraph it was of interest to examine whether this discrepancy can be accounted for by using the elastic constants of Frank and

Wanner. In Figure 5-3 we show the second sound velocity as a function of propagation direction in ⁴He. The solid line theoretical curve calculated from the elastic constants of Frank and Wanner extrapolated to $\rho=0.19087 \text{ g/cm}^3$ by Equation 5-15 is seen to lie nearer the experimental points than the dashed-line curve obtained by Maris. However it seems that a certain amount of discrepancy between experiment and theory still remains to be explained.

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TABLE 5-1 Experimental data used in the calculations. For Hydrogen and Deuterium X represents the concentration of molecules with rotational angular momentum J=1. The source of the elastic constant data is given under Ref. RT stands for room temperature. The elastic constants are in GPa.

Substance	T(K)	Density (g/cm ³)	c ₁₁	c ₃₃	c ₄₄	c ₁₂	c ₁₃	Ref.
⁴ He	1.4	0.19087	0.0405	0.0554	0.0124	0.0213	0.0105	a
⁴ He		0.19698	0.055	0.071	0.0140	0.029	0.0131	b
⁴ He		0.20760	0.076	0.098	0.0196	0.042	0.0198	b
H ₂ (X=0)	4.2	0.0880	0.42	0.51	0.11	0.18	0.05	c
H ₂ (X=.75)	4.2	0.0882	0.362	0.440	0.083	0.119	0.041	c
H ₂ (X=.75)	4.2	0.0936	0.537	0.644	0.132	0.179	0.072	c
D ₂ (X=.02)	4.2	0.2000	0.82	1.02	0.23	0.29	0.09	c
D ₂ (X=.33)	4.2	0.1996	0.668	0.788	0.164	0.232	0.111	c
D ₂ (X=.33)	4.2	0.2045	0.791	0.904	0.196	0.270	0.158	c
AgI	10	5.994	37.4	43.9	4.10	28.8	23.8	d
BeO-1	RT	3.010	460.6	491.6	147.7	126.5	88.48	e
BeO-2	RT	3.010	470.0	494.0	153.0	168.0	119.0	f
ZnO	RT	5.676	207.0	209.5	44.8	117.7	106.1	g
ZnS	RT	4.089	124.2	140.0	28.64	60.15	45.4	e
ZnTe	RT	6.34	86.0	93.0	20.2	37.0	30.0	h
CdS	4.2	4.8217	87.5	95.70	14.80	54.55	48.25	i
CdSe	RT	5.684	74.90	84.51	13.15	46.09	39.26	e
SiC	RT	3.2145	502.0	565.0	169.0	95.0	56.0	j
CeF ₃	RT	6.160	180.0	225.0	34.2	88.0	64.0	k

a) Reference 18

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TABLE 5-2 Calculated values of the two second sound velocities in m/s. The densities have been repeated for Hydrogen and Helium for identification purposes.

Substance	Density	v_{IIx}	v_{IIz}	v'_{IIx}	v'_{IIz}
⁴ He	0.19087	141.3	158.9	153.5	174.9
⁴ He	0.19698	158.3	169.7	172.3	194.4
⁴ He	0.20760	177.7	194.3	193.9	220.1
H ₂ (X=0)	0.0880	702.9	723.7	761.9	840.7
(X=.75)	0.0882	661.5	645.9	725.9	792.6
(X=.75)	0.0936	793.2	782.4	860.9	927.5
D ₂ (X=.02)	0.2000	685.8	695.1	736.7	800.1
(X=.33)	0.1996	601.2	594.6	650.7	695.9
(X=.33)	0.2045	647.1	639.2	697.4	733.8
AgI		504.6	528.5	556.7	637.2
BeO-1		4396	4404	4634	4711
BeO-2		4283	4388	4519	4639
ZnO		1670	1701	1779	1810
ZnS		1656	1680	1775	1864
ZnTe		1140	1136	1219	1253
CdS		1085	1100	1166	1219
CdSe		941	960	1014	1074
SiC		4651	4623	4894	5003
CeF ₃		1564	1543	1711	1871

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CHAPTER 6

Special Points in Self-Consistent Phonon Calculations

A) Introduction

The self-consistent phonon (SCP) formalism (1-5) has proved quite successful in accurately describing various dynamical and bulk thermodynamic properties of anharmonic solids. Unfortunately these calculations are very time consuming since they require the calculation of averages of functions of eigenvectors and eigenvalues over the Brillouin zone at each iteration. Thus it would be desirable if a scheme could be found which would allow the averages to be rapidly but accurately evaluated. Here the convergence of the special points method for this purpose is studied. We test the scheme's applicability in the self-consistent harmonic (SCH) approximation for ^{36}Ar and Kr at various temperatures. Although this method has proved rapidly convergent in electronic problems (6-9), it has not been studied in this context.

The results given show that the scheme is rapidly convergent in the cases studied and thus should be of use in this context.

B) Special Points and the SCH Approximation

The SCP formalism has been derived by a number of authors (1-4). Here only the main equations are stated. The lowest order SCP theory is the SCH approximation in which the frequency of the phonon with wave vector q and branch λ is given by

$$\omega_{q\lambda}^2 = \sum_{\alpha, \beta} \mathcal{E}_{\alpha}(q, \lambda) D_{\alpha\beta}(q) \mathcal{E}_{\beta}(q, \lambda) \quad (6-1)$$

where ϵ is the corresponding polarization vector and D is the dynamical matrix.

$$D_{\alpha\beta}(q) = \frac{1}{M} \sum_{\ell} (e^{-iq \cdot R_{\ell}} - 1) \phi_{\alpha\beta}(0, \ell) \quad (6-2)$$

Here

$$\begin{aligned} \phi_{\alpha\beta}(0, \ell) &= \langle \nabla_{\alpha}(0) \nabla_{\beta}(\ell) v(r_{0\ell}) \rangle \\ &= [(2\pi)^3 |\Lambda|]^{-\frac{3}{2}} \int d^3u \exp(-\frac{1}{2} u \Lambda^{-1} u) \nabla_{\alpha}(0) \nabla_{\beta}(\ell) v(r_{0\ell}) \end{aligned} \quad (6-3)$$

is the averaged force constant between atoms 0 and ℓ . The displacement-displacement correlation function is taken to be Gaussian with width

$$\begin{aligned} \Lambda_{\alpha\beta}(0, \ell) &= \langle u_{\alpha}(0, \ell) u_{\beta}(0, \ell) \rangle \\ &= \frac{\hbar}{MN} \sum_{q\lambda} (1 - e^{iq \cdot R_{\ell}}) \mathcal{E}_{\alpha}(q, \lambda) \mathcal{E}_{\beta}(q, \lambda) \coth \left[\frac{\beta \hbar \omega_{q\lambda}}{2} \right] \frac{1}{\omega_{q\lambda}} \end{aligned} \quad (6-4)$$

where \hbar , M , N and β have their usual meanings and Equations (6-1)-(6-4) are solved iteratively for a given lattice parameter and temperature. As discussed in Chapter 1 the convergence of the special points method depends critically on the form of the function to be averaged. Thus it was of considerable interest to examine its applicability in the context of SCH calculations. Here the special points method is used to reduce the average in Equation (6-4).

C) Results

In order to study the applicability of the special points method we performed calculations using the Baldereschi point (6) which satisfies Equations (1-8) and (1-9) for $N = 2$ and minimizes the $m = 3$ term, as well as sets of 2, 10 and 60 points generated using the method of Chadi and Cohen (7) which satisfy Equations (1-8) and (1-9) for $N = 7, 36$ and about 150

respectively. In the tables these are referred to as (1B), (2), (10) and (60) respectively. In order to ensure that the 60 point scheme was in fact converged, calculations were also carried out using a 408 point scheme. These data are not shown as they are the same as the results using the 60 point scheme excepting changes of one in the last figure. As a further test the data were compared to SCH dispersion curves for Kr calculated under the same conditions by L.K. Moleko. The discrepancies found were negligible and could be explained by the different techniques for the numerical integration of the three dimensional integral in equation (6-3). In Table 6-1 phonon energies at some selected wave vectors for ^{36}Ar in the SCH approximation are given at temperatures of 10K, 35K, 55K and 82K. These were calculated using the Aziz-Chen potential (10). In Table 6-2 similar data for Kr at 10K and 115K calculated using the potential of Aziz (11) is presented.

From these data it may be observed that reasonable results (as compared to the fully converged calculation) are obtained using the one point scheme. Computationally this scheme is not substantially more complicated than a self-consistent Einstein approximation (12,13). To within the accuracy of the calculation performed, the scheme is fully converged using 10 points for the cases studied. This represents a substantial improvement over conventional methods for which it is not uncommon to use several hundred points.

D) Conclusion

In view of the above the special points method should be applicable to SCP calculations for the rare gas solids. These materials are characterized by the large contribution of nearest neighbour interactions to their lattice dynamics. It would be worthwhile to examine the applicability of the method to other classes of materials, in particular the alkali metals and the Wigner electron solid.

TABLE 6-1. SCH Phonon Energies for ^{36}Ar (meV)

Phonon	T(K)	Points			
		1B	2	10	60
0.2 0 0 T	10	1.8970	1.8944	1.8946	1.8946
	35	1.8604	1.8591	1.8596	1.8596
	55	1.8118	1.8102	1.8109	1.8109
	82	1.7193	1.7171	1.7180	1.7181
0.2 0 0 L	10	2.5235	2.5188	2.5192	2.5192
	35	2.4716	2.4686	2.4695	2.4696
	55	2.4043	2.4003	2.4016	2.4017
	82	2.2747	2.2693	2.2713	2.2715
0.6 0 0 T	10	4.9514	4.9446	4.9451	4.9452
	35	4.8560	4.8524	4.8535	4.8536
	55	4.7292	4.7247	4.7264	4.7266
	82	4.4876	4.4816	4.4839	4.4842
0.6 0 0 L	10	6.9756	6.9639	6.9648	6.9649
	35	6.8331	6.8265	6.8286	6.8288
	55	6.6467	6.6380	6.6411	6.6414
	82	6.2902	6.2785	6.2829	6.2833
1 0 0 T	10	6.1116	6.1031	6.1037	6.1038
	35	5.9938	5.9892	5.9906	5.9908
	55	5.8374	5.8316	5.8337	5.8339
	82	5.5394	5.5314	5.5344	5.5346
1 0 0 L	10	8.8373	8.8232	8.8243	8.8244
	35	8.6576	8.6498	8.6523	8.6525
	55	8.4214	8.4115	8.4152	8.4156
	82	7.9712	7.9578	7.9629	7.9634
0.2 0.2 0.2 T	10	2.4030	2.4000	2.4003	2.4003
	35	2.3593	2.3581	2.3585	2.3585
	55	2.3009	2.2993	2.2999	2.2999
	82	2.1888	2.1867	2.1878	2.1879
0.2 0.2 0.2 L	10	5.0578	5.0489	5.0497	5.0497
	35	4.9533	4.9479	4.9496	4.9497
	55	4.8170	4.8098	4.8123	4.8125
	82	4.5561	4.5463	4.5499	4.5502
0.5 0.5 0.5 T	10	4.0861	4.0811	4.0814	4.0815
	35	4.0119	4.0098	4.0104	4.0105
	55	3.9125	3.9098	3.9108	3.9109
	82	3.7220	3.7186	3.7203	3.7205

(TABLE 6-1 continued on next page)

TABLE 6-1, continued

Phonon	T(K)	Points			
		1B	2	10	60
0.5 0.5 0.5 L	10	8.7882	8.7732	8.7745	8.7745
	35	8.6070	8.5980	8.6008	8.6010
	55	8.3696	8.3578	8.3620	8.3623
	82	7.9163	7.9004	7.9063	7.9068
0.4 0.4 0.4 T ₁	10	3.3253	3.3213	3.3216	3.3216
	35	3.2662	3.2647	3.2651	3.2652
	55	3.1869	3.1849	3.1856	3.1856
	82	3.0344	3.0319	3.0333	3.0334
0.4 0.4 0.4 T ₂	10	5.1439	5.1365	5.1371	5.1371
	35	5.0428	5.0390	5.0403	5.0404
	55	4.9090	4.9043	4.9061	4.9063
	82	4.6541	4.6478	4.6503	4.6506
0.4 0.4 0.4 L	10	6.8212	6.8095	6.8105	6.8105
	35	6.6814	6.6743	6.6765	6.6767
	55	6.4984	6.4892	6.4924	6.4927
	82	6.1486	6.1360	6.1407	6.1411

TABLE 6-2. SCH Phonon Energies for Kr (meV)

Phonon	T(K)	Points			
		1B	2	10	60
0.2 0 0 T	10	1.3655	1.3647	1.3648	1.3648
	115	1.2269	1.2253	1.2259	1.2260
0.2 0 0 L	10	1.8089	1.8074	1.8075	1.8075
	115	1.6186	1.6141	1.6156	1.6157
0.6 0 0 T	10	3.5637	3.5616	3.5618	3.5618
	115	3.2023	3.1977	3.1995	3.1996
0.6 0 0 L	10	5.0131	5.0093	5.0097	5.0098
	115	4.4837	4.4746	4.4779	4.4782
1 0 0 T	10	4.3987	4.3961	4.3963	4.3964
	115	3.9527	3.9467	3.9490	3.9492
1 0 0 L	10	6.3563	6.3518	6.3523	6.3523
	115	5.6848	5.6750	5.6788	5.6791
0.2 0.2 0.2 T	10	1.7300	1.7290	1.7291	1.7291
	115	1.5626	1.5606	1.5614	1.5614
0.2 0.2 0.2 L	10	3.6318	3.6290	3.6293	3.6293
	115	3.2455	3.2380	3.2406	3.2409
0.5 0.5 0.5 T	10	2.9415	2.9399	2.9400	2.9400
	115	2.6570	2.6537	2.6549	2.6550
0.5 0.5 0.5 L	10	6.3181	6.3133	6.3138	6.3138
	115	5.6441	5.6320	5.6363	5.6367
0.4 0.4 0 T ₁	10	2.3940	2.3927	2.3928	2.3928
	115	2.1666	2.1639	2.1648	2.1648
0.4 0.4 0 T ₂	10	3.7016	3.6993	3.6996	3.6996
	115	3.3205	3.3158	3.3177	3.3179
0.4 0.4 0 L	10	4.9014	4.8977	4.8981	4.8981
	115	4.3823	4.3725	4.3760	4.3763

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CHAPTER 7

Madelung Constants for Layer Crystals

The transition metal dichalcogenides are a family of layer compounds, each layer consisting of two close packed sheets of chalcogen atoms sandwiching a layer of transition metal atoms. Within a layer two arrangements occur: the trigonal prismatic (TP) and octahedral (OCTA) coordinations (referring to the metal atoms). The former structure is favoured by the group 6B compounds and the later by the 4B compounds. The group 5B compounds may be found in either structure.

In order to understand why one structure is favoured over the other it is necessary to examine the energy difference between them. We note that the interlayer forces are weak in these materials and thus probably do not play a role in distinguishing the energies of the two structures.

An important component of the energy difference between the two structures is the Madelung energy. Recently Shen and Liang (1) calculated Madelung constants for the two structures using a real space scheme. This method converged slowly and as a result they were only able to report values accurate to about 1% leading to an uncertainty of about 10% in the electrostatic energy difference between the two structures. Here Ewald's method (2) is applied to this problem in order to obtain a more accurate result.

This method is in my view more intuitive and computationally easier to implement than the Poisson summation formula for planes (3) used by Johnston and Scholl (4) when they treated this problem concurrently with us (5). In particular using Ewald's method the entire layer is treated at once rather than as an assembly of planes of atoms and the evaluation of modified Bessel

functions is avoided.

To apply Ewald's method to layers one may note that the energy of an isolated layer can be obtained by considering the energy of a stack of layers in the limit as the interlayer separation becomes infinite. To this end we consider a unit cell defined by \underline{a} , \underline{b} , and \underline{c} with \underline{a} and \underline{b} in the plane of the layer and \underline{c} perpendicular to the layers. The z axis is also taken to be perpendicular to the layers so that $\underline{c} = (0,0,c)$ where c is the interlayer spacing. By Ewald's method we have

$$\sum_{\underline{l} \neq 0} \frac{1}{|\underline{l}-\underline{r}|} = \frac{\pi}{v_c} \frac{1}{G^2} \sum_{\underline{g}} \exp(i\mathbf{g} \cdot \mathbf{r}) \frac{\exp(-g^2/4G^2)}{g^2/4G^2} + \sum_{\underline{l} \neq 0} \frac{1}{|\underline{l}-\underline{r}|} \operatorname{erfc}(G|\underline{l}-\underline{r}|) \quad (7-1)$$

and

$$\sum_{\underline{l} \neq 0} \frac{1}{|\underline{l}|} = \frac{\pi}{v_c} \frac{1}{G^2} \sum_{\underline{g}} \frac{\exp(-g^2/4G^2)}{g^2/4G^2} + \sum_{\underline{l} \neq 0} \frac{1}{|\underline{l}|} \operatorname{erfc}(G|\underline{l}|) - \frac{2G}{\sqrt{\pi}} \quad (7-2)$$

where v_c is the volume of the unit cell, \underline{r} is an arbitrary vector, \underline{l} is a lattice vector, \underline{g} is a reciprocal lattice vector and G is an arbitrary parameter chosen to accelerate the convergence of the sums. In the limit where c becomes infinite the real space sums reduce to sums over a single layer. For the reciprocal space sums let $\underline{g} = (g_x, g_y, g_z)$ and $\underline{r} = (r_x, r_y, r_z)$ so that

$$\frac{4\pi}{v_c} \sum_{\underline{g}} \exp(i\mathbf{g} \cdot \mathbf{r}) \frac{\exp(-g^2/4G^2)}{g^2} = \frac{4\pi}{v_c} \sum_{g_x, g_y} \cos(g_x r_x + g_y r_y) \times \exp[-(g_x^2 + g_y^2)/4G^2] \sum_{g_z} \frac{\exp(-g_z^2/4G^2) \cos(g_z r_z)}{g_x^2 + g_y^2 + g_z^2} \quad (7-3)$$

Letting $v_c = A c$ and noting that the sum over g_z becomes an integral in the limit

$$\frac{4}{A} \sum_{g_x g_y} \cos(g_x r_x + g_y r_y) \exp [-(g_x^2 + g_y^2)/4G^2] \int_0^{\infty} \frac{\exp(-g_z^2/4G^2) \cos(g_z r_z)}{g_x^2 + g_y^2 + g_z^2} dg_z$$

$$= \frac{4}{A} \sum_{g_x g_y} \cos(g_x r_x + g_y r_y) \exp [-(g_x^2 + g_y^2)/4G^2] I(r_z, \frac{1}{4G^2}, \sqrt{g_x^2 + g_y^2}) \quad (7-4)$$

The integral can be evaluated analytically (6).

$$I(\alpha, \beta, \gamma) = \frac{\pi \exp(\beta \gamma^2)}{4\gamma} \times [\exp(-\alpha\gamma) \operatorname{erfc}(\gamma\sqrt{\beta} - \alpha/2\sqrt{\beta}) + \exp(\alpha\gamma) \operatorname{erfc}(\gamma\sqrt{\beta} + \alpha/2\sqrt{\beta})] \quad (7-5)$$

The reciprocal space sums in equations (1) and (2) are identical for $r=0$. The $g_x=g_y=0$ term in the sum of equation (4) diverges, as might be expected from the long range of the Coulomb potential. However, since the layers are electrically neutral, in evaluating the Madelung constant the divergences cancel and only the remaining part is required. We note that for small γ

$$I(\alpha, \beta, \gamma) = \left(\frac{\pi}{4\gamma}\right) \{2 - \gamma[2\alpha \operatorname{erfc}(\alpha/2\sqrt{\beta}) + 4\sqrt{\beta/\pi} \exp(-\alpha^2/4\beta)]\} \quad (7-6)$$

so that in evaluating the Madelung constant $I(\alpha, \beta, \gamma)$ is to be replaced by $I_0(\alpha, \beta, \gamma)$ in the $g_x=g_y=0$ terms of the reciprocal lattice sums where

$$I_0(\alpha, \beta, 0) = \left(-\frac{\pi\alpha}{2}\right) \operatorname{erf}\left(\frac{\alpha}{2\sqrt{\beta}}\right) - \sqrt{\pi\beta} \exp(-\alpha^2/4\beta) \quad (7-7)$$

Applying this to the ideal structures of Table 7-1, Madelung constants of 10.166078 and 12.334424 are obtained for the TP and OCTA structures respectively. These values are much more accurate than those obtained by Shen and Liang.

TaS₂, which is of particular interest because it occurs in both structures,

has been studied in detail by Shen and Liang. Because in this case the two structures must have similar energies they set the sum of the electrostatic and electron band structure energy differences between the two structures to be zero. It was of interest to re-examine their conclusions using the Madelung constants obtained above. Following them the difference in the electron band structure energy between the OCTA and TP structures is taken to be in the range 1.0 eV to 1.5 eV. Thus assuming the Ta charge to be the same for both structures the Ta ions carry a charge of between 0.95e and 1.2e. This overlaps the lower end of the range 0.97e to 1.5e given by Shen and Liang and is considerably narrower than it. Allowing the electron band structure energy difference to be as high as 2.0 eV increases the upper limit of the the range obtained here to about 1.35e.

By the argument given by Lucovsky et. al. (7) that the TP structure favours the formation of covalent bonds in these materials it may be expected that the Ta charge might be somewhat larger in the OCTA structure. This implies that the actual charges should lie in the lower end of the range given above or perhaps somewhat below the lower limit.

TABLE 7-1 Ideal Structures for the MX_2 Compounds
(lattice constant = 1.0)

	Trigonal prismatic	Octahedral
a	(1,0,0)	(1,0,0)
b	(-1/2, $\sqrt{3}/2$, 0)	(-1/2, $\sqrt{3}/2$, 0)
r_m	(0,0,0)	(0,0,0)
r_{x1}	(0, $1/\sqrt{3}$, 1/2)	(0, $1/\sqrt{3}$, $1/\sqrt{6}$)
r_{x2}	(0, $1/\sqrt{3}$, -1/2)	(1/2, $1/2\sqrt{3}$, $-1/\sqrt{6}$)

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APPENDIX A

A' Brief Overview of the Total Energy Program

A) The SCF loop

As previously discussed in Chapters 1 and 2, the calculation of the total energies and charge densities proceeded by the iteration of the Kohn-Sham equations, (1-1) and (1-2), to self-consistency, the SCF loop consisting of the construction of an output charge density based on a given input charge density. Accordingly, for each iteration the Hamiltonian matrix (see equations 2-2 and 2-3) was constructed at each special point in the irreducible wedge of the Brillouin zone, using the input charge density and the results from Chapter 2, and its first few eigenvectors and eigenvalues calculated. Using the occupied eigenvectors an unsymmetrized valence charge density was accumulated in reciprocal space. The weighted sum of the eigenvalues of the occupied states was also accumulated to be used in the calculation of the total energy. Once the sum over the irreducible wedge of the Brillouin zone was completed the resulting charge density was symmetrized to obtain the output charge density. This was done using the space group elements of the crystal under consideration, which relate different Fourier components of the charge density within a given star (a set consisting of a reciprocal lattice vector and those vectors which may be obtained by applying operations in the point group of the crystal in question to it). Having thus obtained the output charge density, it was Fourier transformed into real space in order to calculate the Fourier components of the exchange-correlation potential and the exchange-correlation energy, needed for the evaluation of the total energy as discussed in Chapter 2. Next the Ewald term, γ_{Ewald} , was calculated for the lattice in question and the total energy evaluated using

Equation (2-4), thereby completing the iteration in question.

B) Potential Mixing

As discussed above an input charge density is required for each pass through the SCF loop. The most obvious choice would be to use the output charge density and corresponding potential from the previous iteration as the input to the current pass. However this scheme does not converge sufficiently rapidly to obtain self-consistency in a reasonable number of iterations. In order to obtain faster convergence a simple mixing of the inputs and outputs was used.

$$(n^{in})_{i+1} = \alpha (n^{in})_i + (1-\alpha)(n^{out})_i \quad (A-1)$$

$$(V_{xc}^{in})_{i+1} = \alpha (V_{xc}^{in})_i + (1-\alpha)(V_{xc}^{out})_i \quad (A-2)$$

In Equations (A-1) and (A-2) the subscripts, i and $i+1$ refer to the i 'th and $(i+1)$ 'th iterations respectively, α being a constant adjusted to obtain rapid convergence. It may be noted from (A-1) and (A-2) that the input exchange-correlation potential to be used in constructing the Hamiltonian matrices in the $(i+1)$ 'th iteration is not that corresponding to the input charge density except for the special case, $\alpha=0$, or at self-consistency. This is because the exchange-correlation potential is a non-linear function of the charge density. The reason for using (A-2) instead of calculating v_{xc} from the charge density at the start of each iteration is that it was found that this scheme did not seem to change the number of iterations required to obtain self-consistency while permitting the saving of one Fourier transform per iteration.

About four iterations were typically required to converge the total energy to 10^{-6} Ry. per unit cell using a mixing parameter, α , of about 0.2 with the input for the first iteration constructed as discussed below.

The simple mixing scheme used in the calculations described here would probably not have been adequate for calculations on a system with a large unit cell where a more powerful technique such as Broyden's method (1) might have been necessary. The success of the scheme used was probably due to the fact that for the lattices considered the unit cells were fairly small and thus there were no small G Fourier components of the charge density except of course $n(G=0)$ which is fixed by the condition of overall electrical neutrality. This is significant because the Coulomb potential diverges as G^{-2} .

C) The Input Charge Density

In order for the self-consistent calculation to converge in a reasonable number of iterations it was necessary to have a reasonable estimate of the charge density to use as an input to the first pass through the SCF loop. In this calculation many of the required input charge densities were obtained from a calculation using a small basis consisting of about half the number of plane waves used in the main calculation. This small basis set calculation typically used seven or eight iterations to find a stable solution starting from an initial uniform charge distribution, the seven or eight iterations using about as much computer time as would have been required to do two iterations with the full basis set.

In some cases which involved small distortions of a unit cell for which a self-consistent charge density had already been obtained an alternate method

of obtaining an input charge density for the first iteration was used. This consisted of applying the same homogeneous deformation to charge density of the existing calculation as was to be applied to the unit cell. For the sort of distortions this scheme was used for (of the order of 1-2%) input charge densities of sufficient quality to reach the required degree of self-consistency in about five iterations were obtained. Thus in the cases for which it was applicable the use of this scheme resulted in the saving of a significant amount of computer time.

REFERENCE

- (1) C.G. Broyden, Math. Comput. 19, 577 (1965)

APPENDIX B

The Fits Used in the Total Energy Calculations

In order to obtain structural properties from calculations of the total energy of a solid subjected to various distortions it is necessary to fit these to appropriate parameterized functions, the desired structural constants being obtained from the parameters. In this appendix the fits used are described and their accuracy discussed. In addition some total energies which were used in the fits are given in Table B-1. It should be noted that it was found that the total energies tended to converge more slowly than the charge densities and structural properties as the size of the basis was increased. The values given are not fully converged with respect to the size of the basis.

i) The lattice constant, bulk modulus and its pressure derivative

As previously discussed, the lattice constant, bulk modulus and the pressure derivative of the bulk modulus were calculated by fitting the total energies calculated at six volumes to Murnaghan's equation of state,

$$E = \frac{B_0 V}{B_0' (B_0' - 1)} \left[B_0' \left(1 - \frac{V_0}{V} \right) + \left(\frac{V_0}{V} \right)^{B_0'} - 1 \right] + E(V_0) \quad (\text{B-1})$$

In order to test the quality of this procedure several additional fits were performed using different subsets of the total energy data obtained by deleting various points. As a further test a fit was also performed using eight values of the total energy, the two additional values being at greatly reduced volumes ($\Omega/\Omega_0 = 0.762$ and $\Omega/\Omega_0 = 0.804$). Based on these fits it is

estimated that the errors due to the fit employed are most likely less than five in the last digits of the value of the bulk modulus using 731 plane waves, the error in the other quantities probably being beyond the last figure quoted.

ii) The shear elastic constant, c_s

The shear elastic constant was calculated from the total energy changes associated with 1% stretches and compressions of the unit cell along the z-axis with compensating changes in the other two axes designed to keep the volume of the unit cell unchanged. As expected, it was found that to within the numerical noise level (estimated to be less than 2×10^{-6} Ry./cell) the energy of a unit cell stretched by 1% along the z-axis was the same as that when compressed by the same amount. Accordingly, the shear constants were determined by fitting the energies of the deformed and undeformed unit cells to a quadratic, $E = E_0 + au^2$, where E_0 is the energy of the undeformed unit cell, u is the deformation (Here the strains are $e_{33}=u$ and $e_{11}=e_{22}=(1+u)^{-1/2}-1$) and a is the parameter to be determined. Thus

$$c_{11} - c_{12} = 1.961 \times 10^{13} \text{ a./}\Omega \quad (\text{B-2})$$

where a is in Ry./cell, the cell volume is in atomic units and the elastic constants are in GPa. In order to test the reliability of the technique; a more complicated fit was undertaken at $\Omega/\Omega_0 = 0.935$. This consisted of fitting the energies of the undistorted unit cell and unit cells with 1% and 2% stretches along the z-axis to a polynomial with both second and fourth order terms. Based on this test it is estimated that the fitting errors in the values given are probably less than 1 in the last figure given.

iii) The phonon frequency, ω_{TO} , and force constant, k_{xyz}

The transverse optical phonon frequencies and associated anharmonic force constants were calculated from changes in the energy resulting from alterations in the spacing between the cation and anion sublattices along a bond direction. In particular the energies for a stretch of about 1% and an equal compression were used, these being fitted to a cubic, $E = E_0 + au^2 + bu^3$, E_0 being the energy at $u=0$ (Here $u=t-t_0$, the sublattice separation being $(2t, 2t, 2t)$ and t_0 the equilibrium value of t .) and a and b the parameters. Thus

$$\omega_{TO} = 2.795 \times 10^{14} \sqrt{\frac{Q}{m}} \quad (B-3)$$

$$k_{xyz} = 22.95 b \quad (B-4)$$

where m is the reduced mass in atomic mass units, the energies are in Ry./cell, the frequency is in s^{-1} and k_{xyz} is in $eV/\text{\AA}^2$. As a test the same fit was performed at the reduced volume, $\Omega/\Omega_0 = 0.935$, using energies for several displacements ranging between -2% and +2%. Based on this, the fitting errors in the frequencies were probably less than two in the last digit given whereas the fitting errors in the anharmonic force constants are likely somewhat larger being of the order of 5%.

iv) c_{44} and the internal strain parameter

The calculations of the internal strain parameters and c_{44} were those which involved the most computer time. This is as a result of the large number of distortions for which total energies were calculated and the fact that these were among the lowest symmetry distortions treated here. The calculations were performed by fitting the total energies of unit cells with various

sublattice spacings along a bond direction to cubics (This was done using a least squares algorithm.), the calculations differing from those used for the transverse optical phonon frequencies in that in the present case the unit cells being considered were simultaneously subjected to trigonal stretches of 0.5% or 1% along the same direction as the sublattice displacements. For each value of the trigonal deformation total energies for about five sublattice spacings were used in the fits. From the positions of the minima for each trigonal stretch an effective internal strain parameter for that stretch was calculated, the internal strain parameter quoted being calculated by linearly extrapolating the effective internal strain parameters corresponding to the 0.5% and 1% stretches to the undeformed limit. These effective internal strain parameters were 0.52 and 0.49 respectively at the free volume and 0.39 and 0.41 respectively at the reduced volume. The energy minima for the two trigonal deformations were then fitted to a cubic, $E = E_0 + ae^2 + ce^3$, again using a least squares algorithm. Here e is the trigonal deformation (the strains are $e_{ij}=e$, for $i \neq j$ and $e_{ii}=0$), a and c are parameters, E is the energy minimum at e , determined from the fit above, and E_0 is the energy of the undistorted unit cell. The elastic constants c_{44} were then calculated from the resulting values of the parameter, a . In order to estimate the reliability of this procedure it was repeated with subsets of the data, constructed by leaving out one or two values of the total energy. Because of the limited number of total energies available it was not feasible to test this procedure more thoroughly. From the tests performed it seems probable that the fitting errors in the internal parameters are less than three in the last digit quoted and that the errors in c_{44} are less than one in the last digit quoted. The fitting errors in the anharmonic force constant k_{xyz} for non-zero trigonal deformations are estimated to be of the order of 5%. It was

found that the cubic constant, c , was highly unreliable and therefore no attempt was made to use this number.

It should be noted that more reliable calculations of the internal strain parameters and the elastic constants, c_{44} , could probably have been carried out by using the force and stress theorems (1). This is because using these results several pieces of information can be obtained at each deformation, instead of just the energy, thereby reducing the number of distortions which need be considered. Thus given a fixed amount of computer resources more attention could presumably be paid to questions of convergence if these were used. Also the forces and stresses are linear in the strain whereas the energy is quadratic. Thus in view of the small energy differences treated here it seems likely that the use of these theorems could yield more accurate results. The force and stress theorems were not used because the necessary expressions using the non-local pseudopotentials employed here are somewhat unwieldy.

TABLE B-1. Some selected values of the total energy of InSb using 531 plane waves. The energies are in Ry./cell. The sublattice spacings are given in terms of t (in a.u.) where the sublattices are separated by $(2t, 2t, 2t)$.

Calculation	Ω/Ω_0	Energy	
Cubic (undistorted)	1.035	-15.329593	
	1.000	-15.333358	
	0.985	-15.334552	
	0.938	-15.336470	
	0.935	-15.336474	
	0.892	-15.334747	
	0.847	-15.328687	
	0.804	-15.317482	
	0.762	-15.300200	
	0.722	-15.275754	
Trigonal	e=0 t=1.435	0.847	-15.328387 (at equilibrium
	e=0 t=1.465	0.847	-15.328408 t=1.45)
	e=0 t=1.46	0.892	-15.334476 (at equilibrium
	e=0 t=1.49	0.892	-15.334493 t=1.475)
	e=0 t=1.48	0.935	-15.336098 (at equilibrium
	e=0 t=1.483515	0.935	-15.336230 t=1.4985)
	e=0 t=1.49	0.935	-15.336396
	e=0 t=1.51	0.935	-15.336337
	e=0 t=1.513485	0.935	-15.336243
	e=0 t=1.52	0.935	-15.336024
	e=0 t=1.51	0.985	-15.334330 (at equilibrium
	e=0 t=1.54	0.985	-15.334342 t=1.525)
	e=0 t=1.517175	1.000	-15.333135 (at equilibrium
	e=0 t=1.5248375	1.000	-15.333303 t=1.5325)
	e=0 t=1.5401625	1.000	-15.333305
	e=0 t=1.547825	1.000	-15.333147
	e=.5% t=1.4985	0.935	-15.336242
	e=.5% t=1.502	0.935	-15.336282
	e=.5% t=1.505	0.935	-15.336292
	e=.5% t=1.508	0.935	-15.336291
	e=.5% t=1.511	0.935	-15.336267
	e=1% t=1.4985	0.935	-15.335670
	e=1% t=1.505	0.935	-15.335802
	e=1% t=1.51	0.935	-15.335863
	e=1% t=1.515	0.935	-15.335872
	e=1% t=1.52	0.935	-15.335831

(continues on next page)

TABLE B-1 (continued)

e=.5%	t=1.5325	1.000	-15.333118
e=.5%	t=1.5375	1.000	-15.333179
e=.5%	t=1.5425	1.000	-15.333194
e=.5%	t=1.5475	1.000	-15.333163
e=1%	t=1.5325	1.000	-15.332478
e=1%	t=1.5375	1.000	-15.332587
e=1%	t=1.5425	1.000	-15.332666
e=1%	t=1.5475	1.000	-15.332699
e=1%	t=1.5475	1.000	-15.332688
Tetragonal	stretch=+2%	0.935	-15.336137
	stretch=+1%	0.935	-15.336391
	stretch=+1%	1.000	-15.333273

REFERENCE

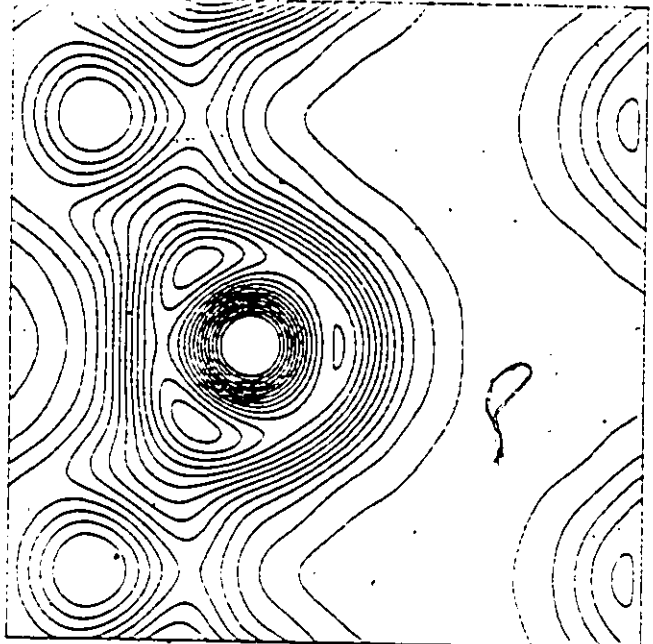
- (1) See for example, O.H. Nielsen and R.M. Martin, to be published in Electronic Structure, Dynamics and Quantum Structural Properties of Condensed Matter (1985)

FIGURES

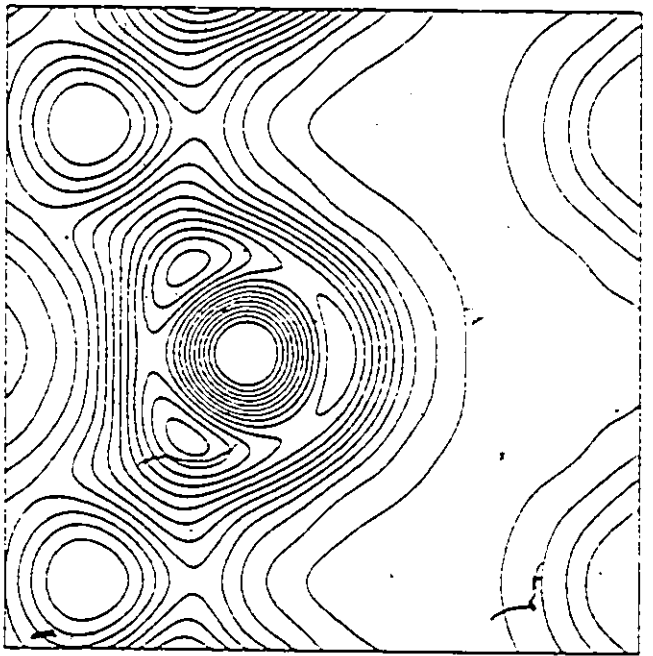
- 3-1 (110) Charge Densities for InSb. Adjacent contours are separated by 2 electrons/cell except in the difference where the separation is 0.5 electrons/cell. The dashed contours are at 0.
- 3-2 (110) Charge Densities for InAs. Adjacent contours are separated by 2 electrons/cell.
- 4-1 (110) Charge Densities and Polarizations for InSb. The charge densities are in the top row, (a), the polarization associated with a TO phonon is in the middle row, (b), and that associated with a tetragonal distortion is in the bottom row, (c). Adjacent contours are separated by 2, 0.2 and 0.04 electrons/cell in (a) through (c) respectively. The dashed contours are at 0.
- 5-1 Second sound velocities as a function of the density for hcp ⁴He. The curves were calculated from the elastic constants of Crepeau et. al. and Equation (5-16). The points refer to the three sets in Table 5-2.
- 5-2 Second sound velocities as a function of the density for hcp ⁴He. The curves were calculated from the elastic constants of Frank and Wanner and Equation (5-16). The points refer to the three sets in Table 5-2.
- 5-3 Velocity of second sound as a function of the propagation direction, θ , in hcp ⁴He at 25 bars. The experimental points are due to Mueller and Fairbank. The solid line curve was calculated from the elastic constants of Frank and Wanner extrapolated to the melting point using Equation (5-16). The dashed line curve was calculated by Maris using elastic constants which are almost the same as those of Crepeau et al.

Figure 3-1

VOLUME = 1.000



VOLUME = 0.847



DIFFERENCE

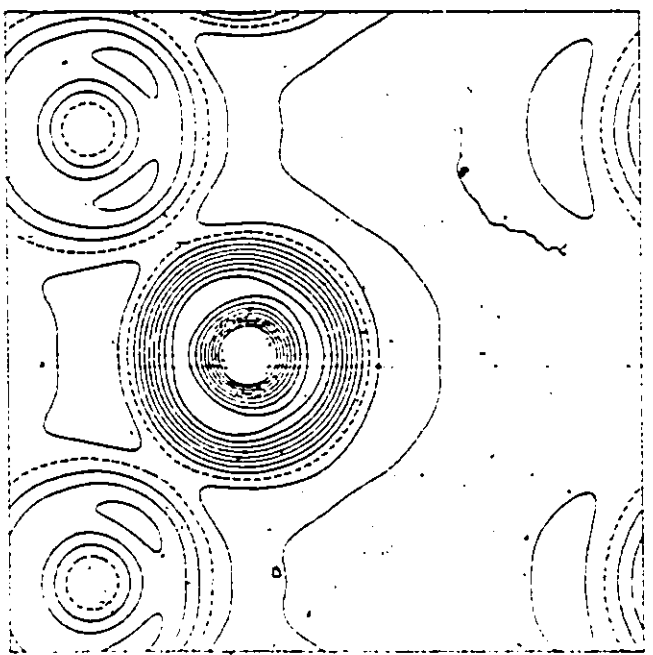
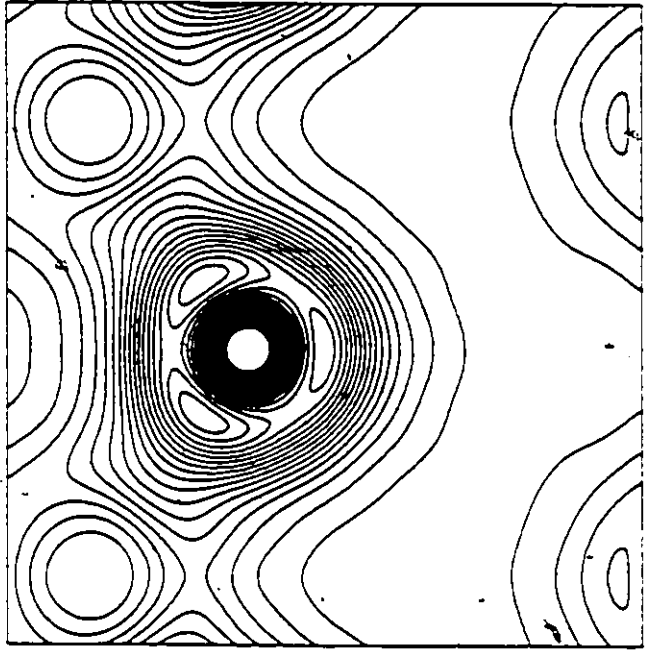
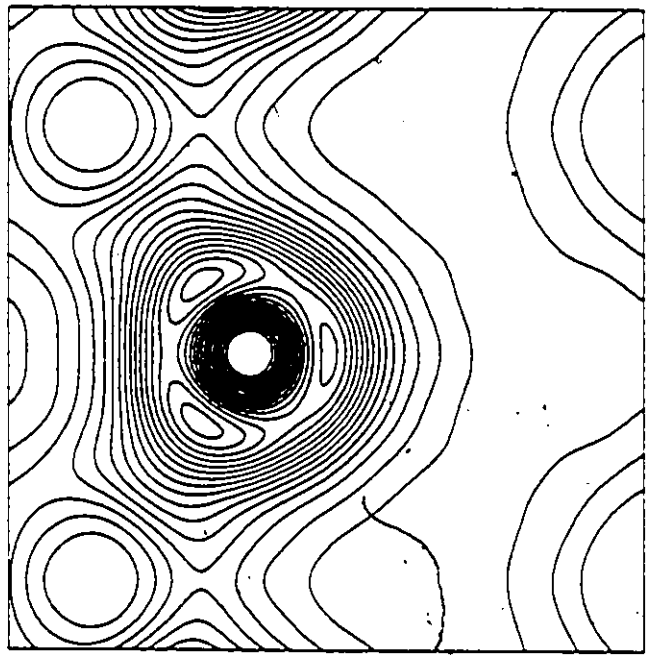


Figure 3-2

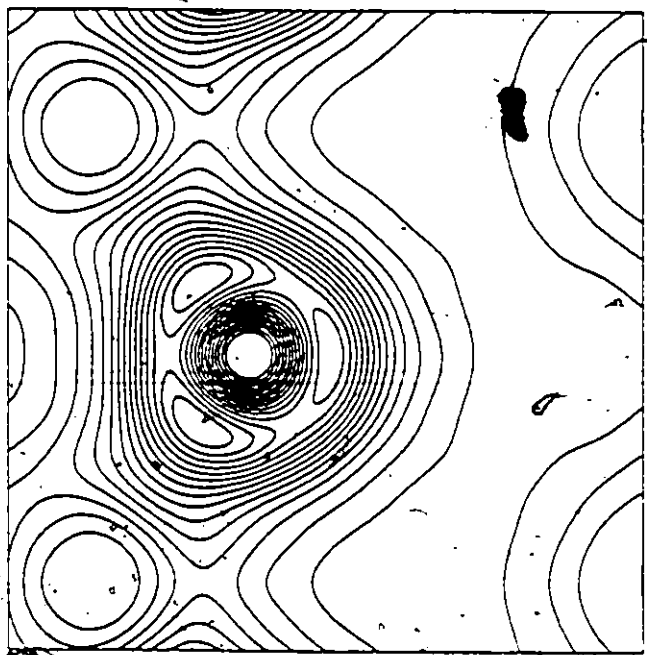
VOLUME = 1.000



VOLUME = 0.898



VOLUME = 0.850



VOLUME = 0.935

VOLUME = 1.000

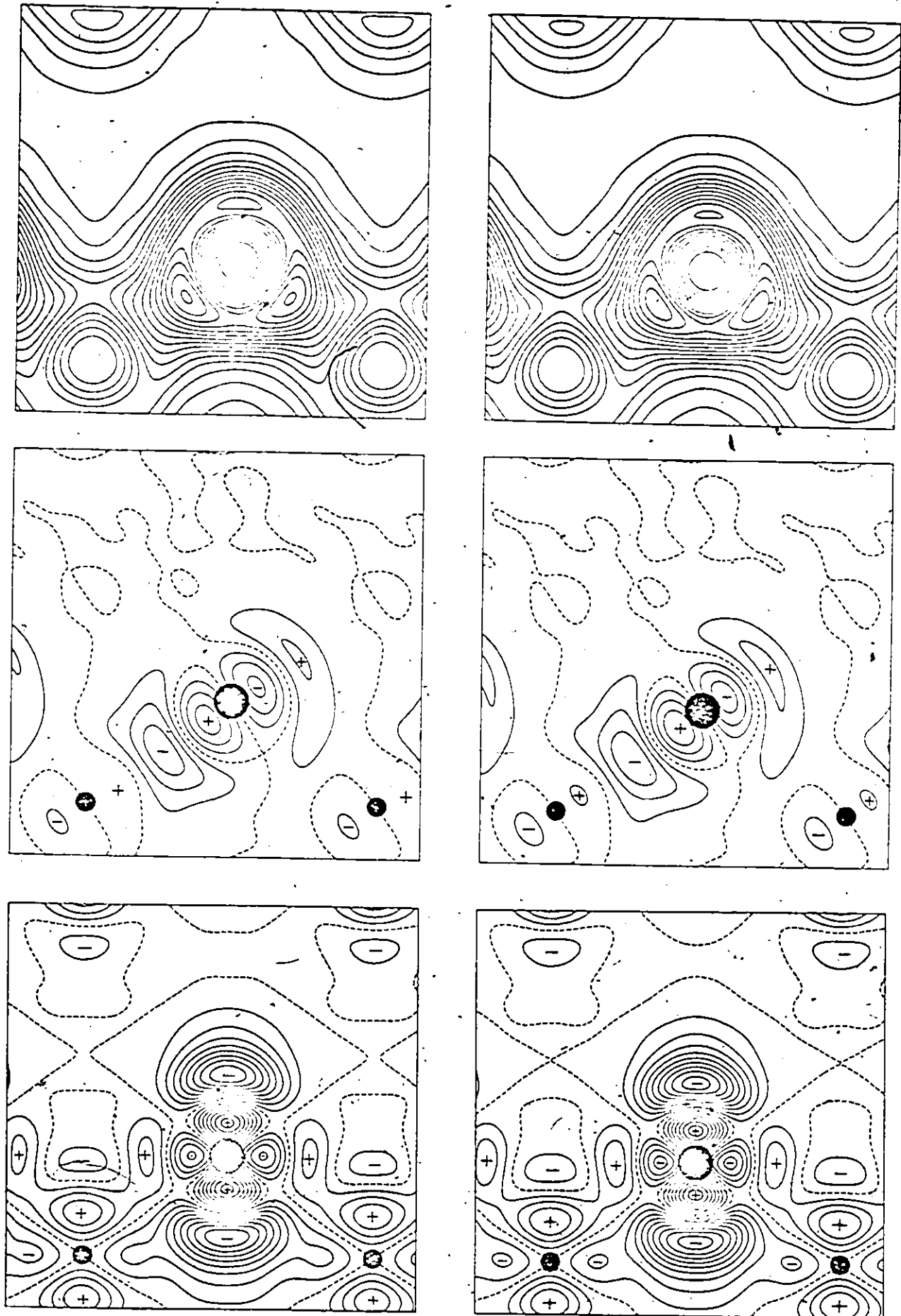


Figure 4-1

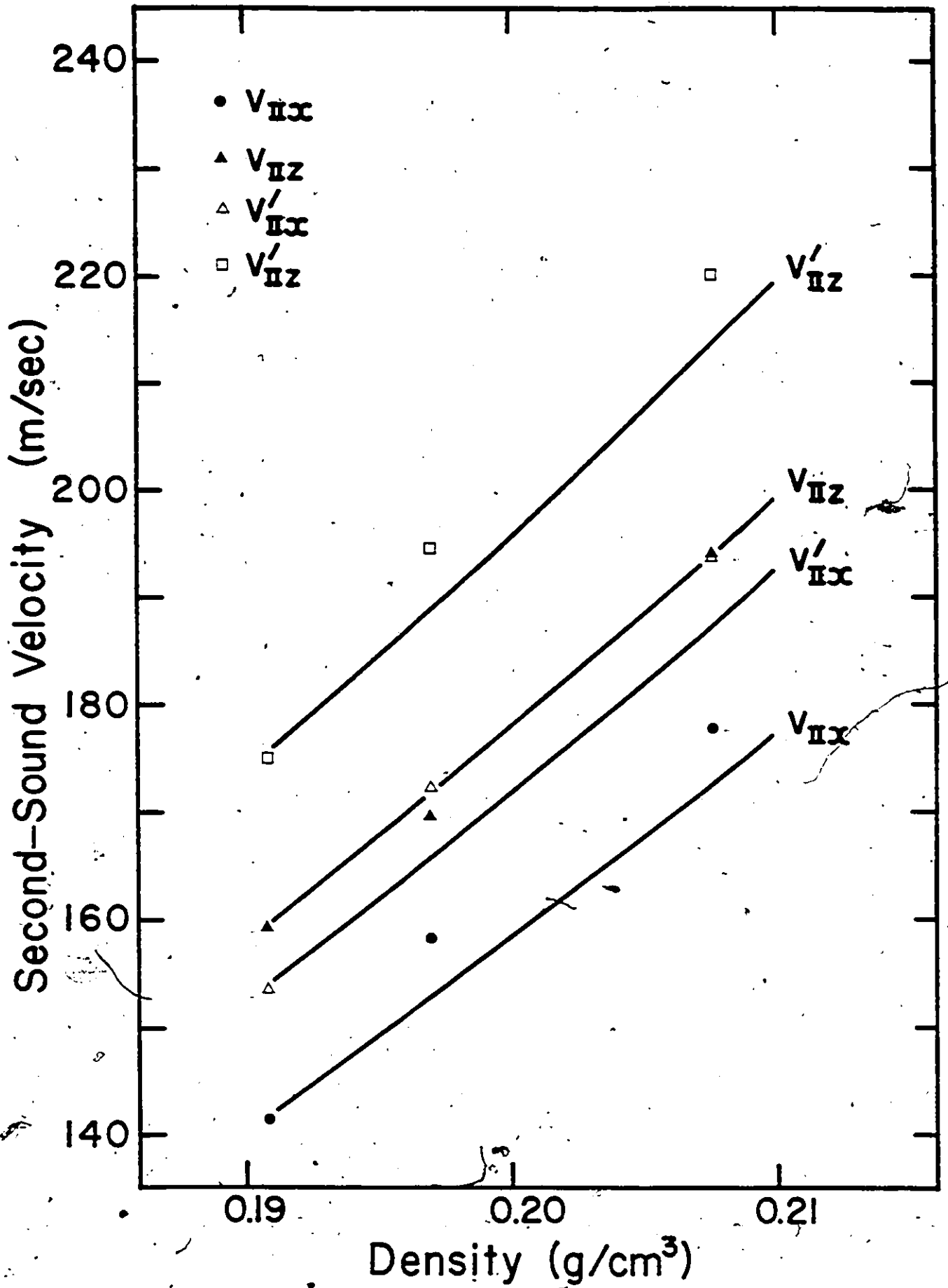


Figure 5-1

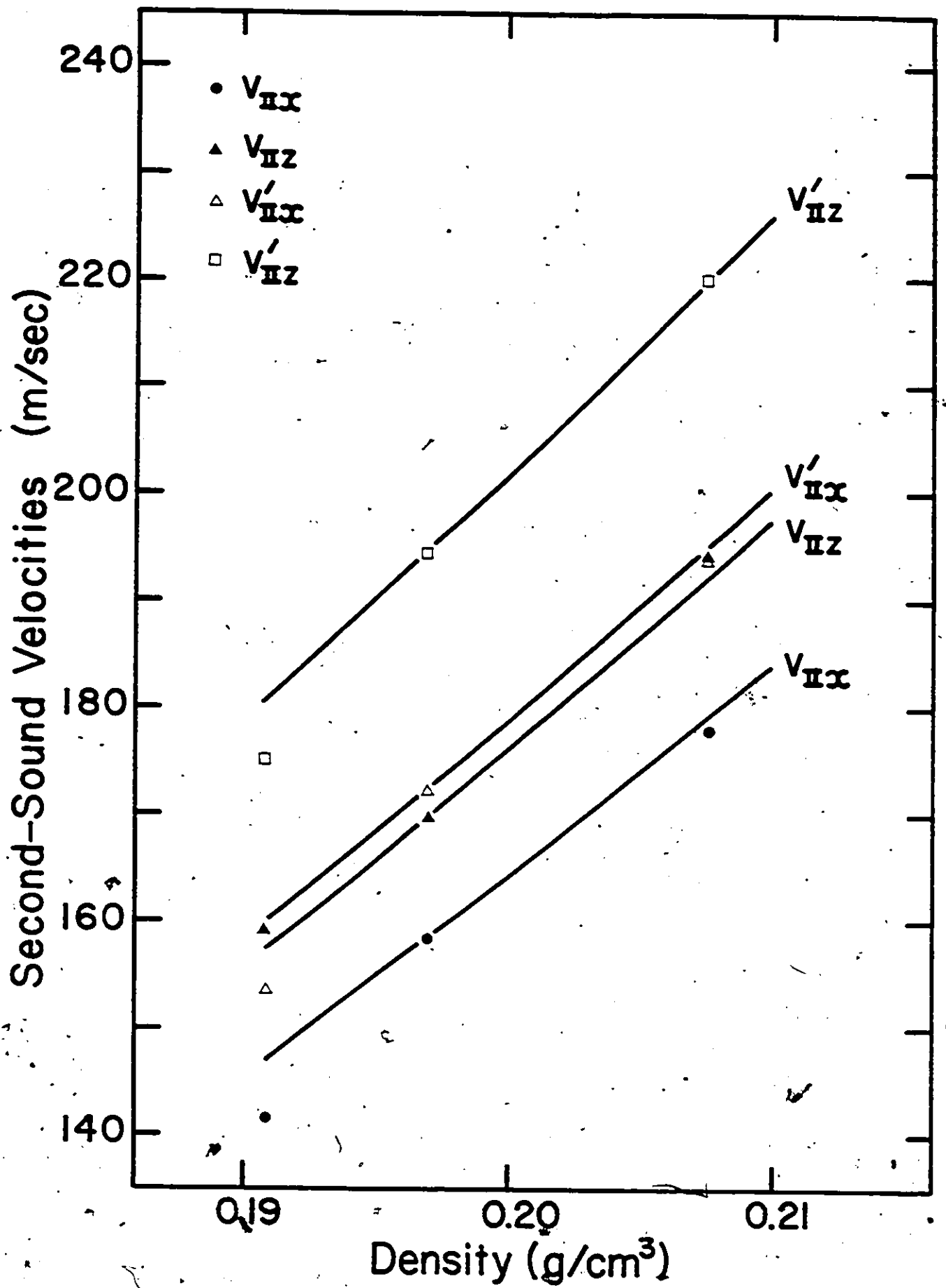


Figure 5-2

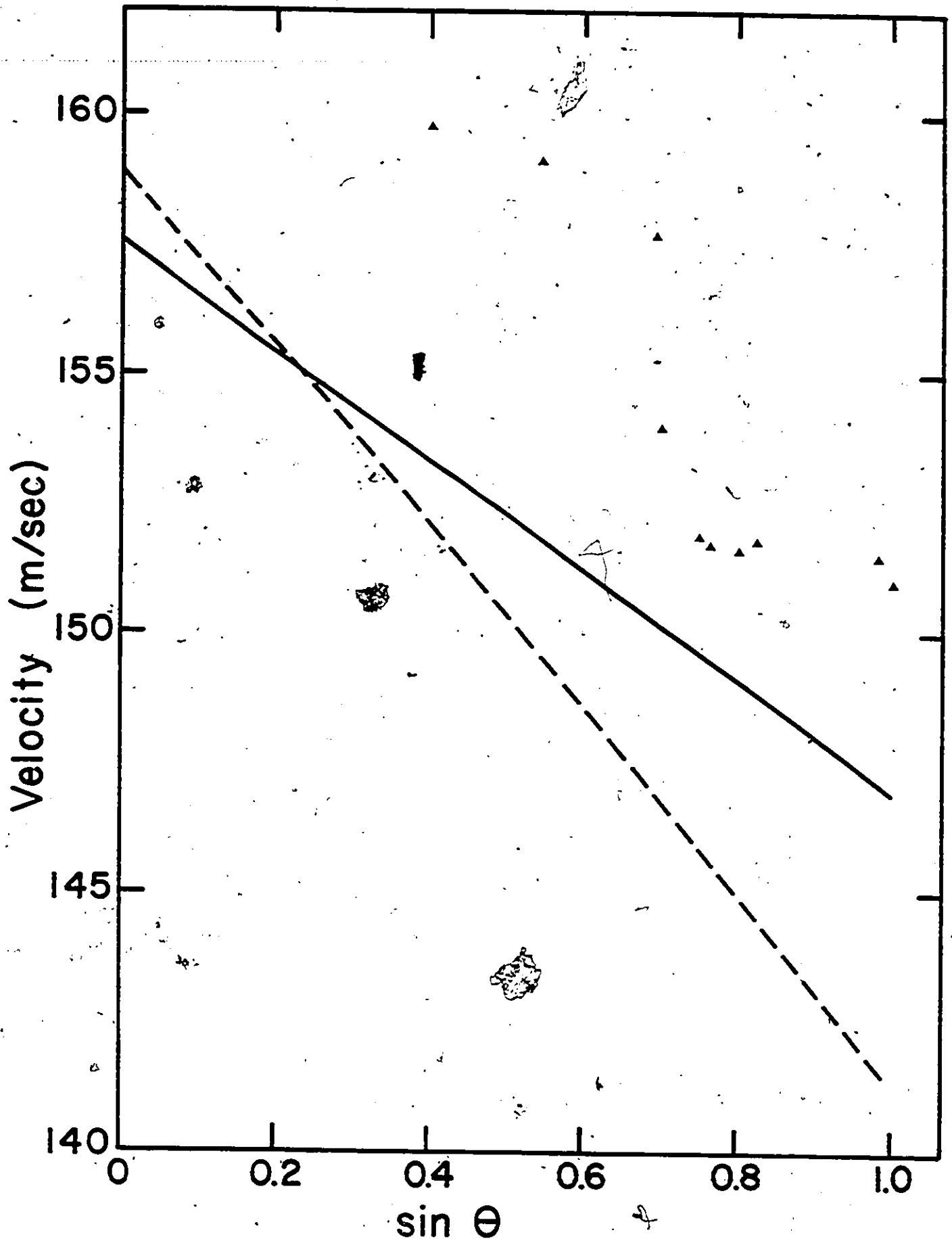


Figure 5-3

PUBLICATIONS

- (1) E. Fortin and D. Singh, 'Polarization and intensity fluctuations in He-Ne lasers', Am. J. Phys. 49, 891 (1981)
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- (13) D. Singh, Y.P. Varshni and R. Dutt, 'Bound eigenstates for two truncated Coulomb potentials', Phys. Rev. A 32, 619 (1985)
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The Computer Code for the Total Energy Calculations

REQUESTED OPTIONS (EXECUTE): NOHAP NOXREF NOOBJECT

OPTIONS IN EFFECT: NOLIST NOHAP NOXREF GOSTMI HODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG. SRCFLG
NOSYM NORENT NOSDUMP AUTODBL(NONE) NOSXM
OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

.....1.....2.....3.....4.....5.....6.....7......8

C TOTAL ENERGY PROGRAM USING
C BHS PSEUDOPOTENTIALS AND G=G'
C TO ADD MORE CHARGE-DENSITY COMPONENTS USE PROGRAM LDA2
C PROGRAM WRITTEN BY D. SINGH MAY 1983 - AUGUST 1984

1 IMPLICIT REAL*8(A-H,O-Z)
2 DIMENSION AR(533,533),VI(533,5),V1(533,5),EIG(5)
3 CALL SCF(AR,A1,VR,V1,ENG)
4 STOP
5 END

STATISTICS SOURCE STATEMENTS = 5, PROGRAM SIZE = 4588478 BYTES, PROGRAM NAME = MAIN PAGE: 1

STATISTICS NO DIAGNOSTICS GENERATED.

MAIN END OF COMPILATION 1 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTIMI MODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
MOSYM MORENT NOSDUMP AUTODBL(MOHE) MOSXH
OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)
*.....1.....2.....3.....4.....5.....6.....7.....8

1, BLOCK DATA
2, IMPLICIT REAL*8(A-H,O-Z)
3, COMMON/DENS/RH(533),RR(750),RRT(750),EX
4, COMPLEX*16 RRT,RR,RH
5, DATA RR /750*(0.00,0.00)/
6, DATA RRT/750*(0.00,0.00)/
7, END

STATISTICS SOURCE STATEMENTS = 7, PROGRAM SIZE = 0 BYTES, PROGRAM NAME = BLKDT# PAGE: 2.

STATISTICS NO DIAGNOSTICS GENERATED.

BLKDT# END OF COMPILATION 2 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTHT NODACK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSODUMP AUTODBL(NONE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  FUNCTION BESSI(L,Z)
2  CALCULATES I(Z) WITH INDEX L+1/2
3  IMPLICIT REAL*8(A-1,0-Z)
4  INTEGER*4 IND
5  DIMENSION TAB(7)
6  DATA TAB /1.00,3.00,15.00,105.00,945.00,10395.00,135135.00/
7  IF(Z.LT.1.00D0)GOTO 30
8  PREF=1.00D0/DSQRT(Z*2.00D0*.785398163397448293D0)
9  IO=DSINH(Z)
10 I1=DCOSH(Z)-DSINH(Z)/Z
11 IF(L.GT.1)GOTO 10
12 BESSI=PREF*IO
13 IF(L.EQ.1)BESSI=PREF*I1
14 RETURN
15 CONTINUE
16 DO 20 J=2,L
17 BESSI=IO-DFLOAT(2*J-1)*I1/Z
18 IO=I1
19 I1=BESSI
20 CONTINUE
21 BESSI=PREF*BESSI
22 RETURN
23 CONTINUE
24 PREF=DSQRT(Z/(2.00D0*.785398163397448293D0))*Z**L /TAB(L+1)
25 IND=0
26 CUR=1.00
27 SUM=1.00
28 Z2=0.5D0*Z*Z
29 CONTINUE
30 IND=IND+1
31 CUR=CUR*Z2/DFLOAT(IND*(1+2*(L+IND)))
32 SUM=SUM+CUR
33 IF(CUR.GT.1.D-17)GOTO 40
34 BESSI=PREF*SUM
35 RETURN
36 END

```

STATISTICS SOURCE STATEMENTS = 35, PROGRAM SIZE = 1250 BYTES, PROGRAM NAME = BESSI PAGE: 3.

STATISTICS NO DIAGNOSTICS GENERATED.

BESSI END OF COMPILATION 3 *****

LEVEL 1.4.0 (OCT 1984)

VS FORTRAN

DATE: SEP 17, 1985 TIME: 08:15:17

PAGE: 4

OPTIONS IN EFFECT:

HOLIST NOMAP NOXREF GOSTHT NODACK SOURCE TERM HOBJECT FIXED NOTEST TRMFLG SRCFLG
NOSYM NORENT NOSDUMP AUTOABL(NONE) NOSXM
OPT(O) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

ISN 1 FUNCTION ERFO(A,K2)
ISN 2 IMPLICIT REAL*8(A-N,K-Z)
ISN 3 DATA FPI /12.56637061435917D0/
ISN 4 ERFO=FPI*DEXP(-0.25D0*K2/A)/K2
ISN 5 RETURN
ISN 6 END

STATISTICS SOURCE STATEMENTS = 6, PROGRAM SIZE = 432 BYTES, PROGRAM NAME = ERFO PAGE: 4.

STATISTICS NO DIAGNOSTICS GENERATED.

ERFO END OF COMPILATION 4 *****

OPTIONS IN EFFECT: -NOLIST NOMAP NOXREF COSTHT HODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG |SRCFLG.
 NOSYM NORENT NOSDUMP AUTODBL(NONE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

```

*.....1.....2.....3.....4.....5.....6.....7.....8
FUNCTION FACT(N)
IMPLICIT REAL*8(A-H,O-Z)
DATA IT /0/
DIMENSION FAC(51)
IF(IT.NE.0)GOTO 100
FF=1.0D0
FAC(1)=1.0D0
IT=1
DO 10 J=1,50
FF=FF*DFLOAT(J)
FAC(J+1)=FF
CONTINUE
100 FACT=FAC(N+1)
RETURN
END
  
```

STATISTICS SOURCE STATEMENTS= 15, PROGRAM SIZE = 920 BYTES, PROGRAM NAME = FACT PAGE: 5.

STATISTICS NO DIAGNOSTICS GENERATED.

FACT END OF COMPILATION 5 *****

OPTIONS IN EFFECT: NOLIST NOLIST NOXREF NOSYNT NODUMP AUTOOBL(NONE) NOSXM
 OPT(O) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

TRMFLO SRCFLG

1.....2.....3.....4.....5.....6.....7.....8

```

1      FUNCTION GAMMA(N)
2      COMPUTES GAMMA(N/2)
3      IMPLICIT REAL*8(A-H,O-Z)
4      DATA IT /0/
5      DATA FF /1.772453850905500/
6      DIMENSION FAC(51)
7      IF(IT.NE.0)GOTO 100
8      FAC(1)=FF
9      IT=1
10     DO 10 J=1,50
11     FF=FF*(DFLOAT(J)-0.500)
12     FAC(J+1)=FF
13     CONTINUE
14     GAMMA=FACT((N-2)/2)
15     RETURN
16     GAMMA=FAC((N+1)/2)
17     RETURN
18     END

```

STATISTICS SOURCE STATEMENTS = 18, PROGRAM SIZE = 1066 BYTES, PROGRAM NAME = GAMMA PAGE: 6.

STATISTICS NO DIAGNOSTICS GENERATED.

GAMMA END OF COMPILATION 6 *****

SRCFLG

TRMFLG

NOTEST

FIXED

TERM NOOBJCT

NOXREF

GOSIMT NODECK

SOURCE

CHARLEN(500)

NOXMAP NOXREF
NOSYM NORENT NOSDUMP AUTOOBL(NORE)
NOXSM
OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64)

.....1.....2.....3.....4.....5.....6.....7.....8

```

1  FUNCTION GAUSSO(A,ALPHA,BETA,L)
2  IMPLICIT REAL*8(A-H,O-Z)
3  PREF=.78539816339744829300/(A*DSORT(ALPHA*BETA))
4  PREF=PREF*DEXP((ALPHA*ALPHA+BETA*BETA)/(-4.00*A))
5  GAUSSO=PREF*BESSJ(L,ALPHA*BETA/(2.000*A))
6  RETURN
7  END

```

STATISTICS SOURCE STATEMENTS = 7, PROGRAM SIZE = 676 BYTES, PROGRAM NAME = GAUSSO PAGE: 7.

STATISTICS NO DIAGNOSTICS GENERATED.

GAUSSO END OF COMPILATION 7 *****

OPTIONS IN EFFECT: HOLLIST HOMAP HOSREF GOSIMI HODECK SOURCE TERM HNOBJECT FIXED NOTEST TRMFLG SRCFLG
HOSYM HORENT HOSDUMP AUTODBL(HOME) HOSXHM
OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  FUNCTION GAUSS2(A,ALPHA,BETA,L)
2  IMPLICIT REAL*8(A-H,O-Z)
3  REAL*8 NU
4  INTEGER*4 THU
5  NU=DFLOAT(L)+0.5D0
6  THU=2*L+1
7  ALBE=ALPHA*BETA
8  PREF=0.25D0*GANH(THU+4)*ALBE**L/((FACI(THU)*DSQR(A))*A**(L+2))
9  TEM1=0.25D0*(ALPHA**2+BETA**2)/A
10 TEM2=0.5D0*ALBE/A
11 PREF=PREF*DEXP(-TEM1)
12 GAUSS2=PREF*((1.D0-TEM1)/(NU+1.D0))*IYPI(L,TEM2)+
   S TEM2*YYP2(L,TEM2)/(NU+1.D0)
13 RETURN
14 END

```

STATISTICS SOURCE STATEMENTS = 14, PROGRAM SIZE = 1042 BYTES, PROGRAM NAME = GAUSS2 PAGE: 8.

STATISTICS NO DIAGNOSTICS GENERATED.

GAUSS2 END OF COMPILATION 8 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF GOSTMI NODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYH MOREMT ROSDUMP AUTODBL(HOME) ROSXKH
 OPT(0) LANGLVL(77) NOFLIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

```

*.....1.....2.....3.....4.....5.....6.....7.....8
SUBROUTINE GCAL
IMPLICIT REAL*8(A-H,O-Z)
COMMON/INFO/A(3),B(3),C(3),G(750,4),TAU(3),VOL,NUM,NUM1
COMMON/MINUS/INDEXG(533,533)
COMMON/STARS/STAR(533,4),MAPO(4),ISTART(75),ISTOP(75),NSTARS
C
C ELEMENTS OF MAP ARE BARRIZ, 3, MXY, 2Z (IF BARRIZ, 2Z IS REDUNDANT)
C MAP(1,J)=K MEANS THAT UNDER J, C(1) GOES TO G(K)
C ** NOTE ** TIME REVERSAL IS BUILT INTO SUBROUTINE RHO AND NEED
C NOT BE TAKEN INTO ACCOUNT AT THIS LEVEL (VIA INDEXG)
C
DIMENSION G1(3),G2(3),G3(3),IORD(533),TEM(533)
EQUIVALENCE(IORD(1),INDEXG(1,1))
MAPO(1)=4
MAPO(2)=3
MAPO(3)=2
MAPO(4)=2
NSTARS=1
ISTART(1)=1
TPI=2.00*3.1415926535897900
NEST=6+DFLOAT(NUM)**(1./3.)
IF((NEST/2)*2.EQ.NEST)NEST=NEST+1
NSUB=NEST/2+1
VOL=A(1)*(B(2)*C(3)-B(3)*C(2))+A(2)*(B(3)*C(1)-B(1)*C(3))
      +A(3)*(B(1)*C(2)-B(2)*C(1))
VOL1=TPI/VOL
VOL=DABS(VOL)
WRITE(6,3)VOL
GMAX2=TPI*TPI*(1.600*DFLOAT(NUM)/(VOL*TPI))**(2.00/3.00)
G1(1)=(B(2)*C(3)-B(3)*C(2))*VOL1
G1(2)=(B(3)*C(1)-B(1)*C(3))*VOL1
G1(3)=(B(1)*C(2)-B(2)*C(1))*VOL1
G2(1)=(C(2)*A(3)-C(3)*A(2))*VOL1
G2(2)=(C(3)*A(1)-C(1)*A(3))*VOL1
G2(3)=(C(1)*A(2)-C(2)*A(1))*VOL1
G3(1)=(A(2)*B(3)-A(3)*B(2))*VOL1
G3(2)=(A(3)*B(1)-A(1)*B(3))*VOL1
G3(3)=(A(1)*B(2)-A(2)*B(1))*VOL1
IN=0
DO 10 I=1,NEST
  I1=I-NSUB
  DO 10 J=1,NEST
    I2=J-NSUB
    DO 10 K=1,NEST
      I3=K-NSUB
      X=I1*G1(I1)+I2*G2(I1)+I3*G3(I1)
      Y=I1*G1(I2)+I2*G2(I2)+I3*G3(I2)
      Z=I1*G1(I3)+I2*G2(I3)+I3*G3(I3)
      GGG=X*X+Y*Y+Z*Z
      IF(GGG.GT.GMAX2)GO TO 5
      GGG=GGG+2.71D-4*DABS(X)+DABS(Y)+3.14D-5*(DABS(X)+DABS(Y)+DABS(Z))
      2 -1.D-7*(2.D0*DABS(X)+DABS(Y))-1.D-12*(1.D2*X+1.D1*Y+1.D0*Z)
      IN=IN+1
      G(IN,1)=X
      G(IN,2)=Y
      G(IN,3)=Z
    END DO
  END DO
END DO
    
```

```

*.....1.....2.....3.....4.....5.....6.....7.....8
50  G(IN,4)=GGG
51  CONTINUE
52  CONTINUE
53  IF(IN.LE.533)GOTO 5
54  NUM=NUM-5
55  GOTO 6
56  NUM=IN
57  DO 30 I=1,NUM
58  IORD(I)=1
59  CONTINUE
60  ITES=0
61  DO 35 I=2,NUM
62  IF(G(IORD(I),4).GE.G(IORD(I-1),4))GOTO 34
63  ITES=1
64  J=IORD(I)
65  IORD(I)=IORD(I-1)
66  IORD(I-1)=J
67  CONTINUE
68  CONTINUE
69  IF(ITES.EQ.1)GOTO 33
70  DO 40 J=1,4
71  DO 39 I=1,NUM
72  TEM(I)=G(IORD(I),J)
73  DO 40 I=1,NUM
74  G(I,J)=TEM(I)
75  WRITE(6,1)NUM
76  DO 42 I=2,NUM
77  IF((G(I,4)-G(I-1,4)).LE.3.0-5)GOTO42
78  ISTOP(NSTARS)=I-1
79  NSTARS=NSTARS+1
80  ISTART(NSTARS)=I
81  CONTINUE
82  ISTOP(NSTARS)=NUM
83  MAP(1,1)=1
84  MAP(1,2)=1
85  MAP(1,3)=1
86  MAP(1,4)=1
87  IN=2
88  I1=2
89  I2=ISTOP(2)
90  DO 45 I=2,NUM
91  IF(ISTOP(IN).GE.I)GOTO47
92  IN=IN+1
93  I1=ISTART(IN)
94  I2=ISTOP(IN)
95  CONTINUE
96  DARRZ
97  TEM(1)=-G(1,2)
98  TEM(2)=G(1,1)
99  TEM(3)=-G(1,3)
100  DO 121 J=1,12
101  IF(DABS(TEM(1)-G(J,1)).GT.1.0-7)GOTO121
102  IF(DABS(TEM(2)-G(J,2)).GT.1.0-7)GOTO121
103  IF(DABS(TEM(3)-G(J,3)).GT.1.0-7)GOTO121
104  MAP(1,1)=J
105  GOTO122
106  CONTINUE
107  CONTINUE
108  TEM(1)=G(1,2)

```

.....1.....2.....3.....4.....5.....6.....7......8

```

108 ISN TEM(2)=G(1,3)
109 ISN TEM(3)=G(1,1)
110 ISN DO 123 J=1,12
111 ISN IF(DABS(TEM(1)-G(J,1)).GT.1.D-7)GOTO123
112 ISN IF(DABS(TEM(2)-G(J,2)).GT.1.D-7)GOTO123
113 ISN IF(DABS(TEM(3)-G(J,3)).GT.1.D-7)GOTO123
114 ISN MAP(1,2)=J
115 ISN GOTO124
116 ISN CONTINUE
117 ISN C

```

```

118 ISN TEM(1)=G(1,2)
119 ISN TEM(2)=G(1,1)
120 ISN TEM(3)=G(1,3)
121 ISN DO 125 J=1,12
122 ISN IF(DABS(TEM(1)-G(J,1)).GT.1.D-7)GOTO125
123 ISN IF(DABS(TEM(2)-G(J,2)).GT.1.D-7)GOTO125
124 ISN IF(DABS(TEM(3)-G(J,3)).GT.1.D-7)GOTO125
125 ISN MAP(1,3)=J
126 ISN GOTO126
127 ISN CONTINUE
128 ISN C

```

```

129 ISN TEM(1)=-G(1,1)
130 ISN TEM(2)=-G(1,2)
131 ISN TEM(3)=G(1,3)
132 ISN DO 127 J=1,12
133 ISN IF(DABS(TEM(1)-G(J,1)).GT.1.D-7)GOTO127
134 ISN IF(DABS(TEM(2)-G(J,2)).GT.1.D-7)GOTO127
135 ISN IF(DABS(TEM(3)-G(J,3)).GT.1.D-7)GOTO127
136 ISN MAP(1,4)=J
137 ISN GOTO128
138 ISN CONTINUE
139 ISN CONTINUE
140 ISN CONTINUE
141 ISN DO 41 I=1,NUM
142 ISN G(1,4)=G(1,1)**2+G(1,2)**2+G(1,3)**2
143 ISN WRITE(6,43)
144 ISN DO 20 I=1,NUM
145 ISN WRITE(6,2)I,G(1,1),G(1,2),G(1,3),G(1,4)
146 ISN NUM1=NUM
147 ISN DO 50 I1=1,NUM
148 ISN DO 50 I2=1,NUM
149 ISN G1(1)=G(1,1)-G(12,1)
150 ISN G1(2)=G(1,2)-G(12,2)
151 ISN G1(3)=G(1,3)-G(12,3)
152 ISN GGG=G1(1)**2+G1(2)**2+G1(3)**2
153 ISN DO 55 I=1,NUM
154 ISN IF(DABS(G1(1)-G(1,1)).GT.1.D-5)GOTO54
155 ISN IF(DABS(G1(2)-G(1,2)).GT.1.D-5)GOTO54
156 ISN IF(DABS(G1(3)-G(1,3)).GT.1.D-5)GOTO54
157 ISN INDEXG(1,12)=I
158 ISN GOTO 52
159 ISN CONTINUE
160 ISN CONTINUE
161 ISN INDEXG(1,12)=NUM+10
162 ISN CONTINUE
163 ISN CONTINUE
164 ISN WRITE(6,101)
165 ISN RETURN

```

*.....1.....2.....3.....4.....5.....6.....7.....8

```

166 ISN 1 FORMAT(/, ' SYMMETRICAL NUM = ', I3)
167 ISN 2 FORMAT(' G( ', I3, ') = ', 3F11.6, ' G*G= ', F12.6)
168 ISN 3 FORMAT(' VOL= ', F11.6, /)
169 ISN 43 FORMAT(' MAP FOLLOWS DARHZ, 3, MXY, 2Z')
170 ISN 101 FORMAT(' SUPPLEMENTARY G VECTORS NOT USED')
171 ISN 102 FORMAT(' G( ', I4, ') = ', 3F11.6, ' G*G= ', F12.6)
172 ISN END

```

STATISTICS SOURCE STATEMENTS = 171, PROGRAM SIZE = 10972 BYTES, PROGRAM NAME = GCAL PAGE: 9.

STATISTICS NO DIAGNOSTICS GENERATED.

GCAL END OF COMPILATION 9 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTMT NODIACK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM MORENT NOSDUMP AUTODBL(NONE) NOSXM
 OPT(0) LANGVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

.....1.....2.....3.....4.....5.....6.....7......8

```

1  SUBROUTINE MATRIX(K,LMAX,AR,AI)
2  IMPLICIT REAL*8 (A-H,O-Z)
3  COMMON/INFO/B(9),G(750,4),TAU(3),VOL,NUM,NUM1
4  COMMON/DENS/RH(533),RR(750),RRT(750),EX
5  COMMON/MINUS/INDEXG(533,533)
6  DIMENSION K(3),G1(3),G2(3),AR(NUM,NUM),AI(NUM,NUM)
7  COMPLEX*16 R,RT,TEM,RH,RR,RRT,VCOUL,STRUCT,ADD
8  REAL*8 K
9  DO 10 I1=1,NUM
10  DO 10 I2=I1,NUM
11  IND=INDEXG(I1,I2)
12  R=RR(IND)
13  RT=RRT(IND)
14  IF(IND.EQ.1)RT=(0.00,0.00)
15  DO 20 I=1,3
16  G1(I)=G(I1,I)
17  G2(I)=G(I2,I)
18  CONTINUE
19  GS=0.00
20  IF(IND.LE.NUM1)GS=G(IND,4)
21  ADD=STRUCT(K,G1,G2,LMAX)+VCOUL(R,GS)+2.00*RT
22  AR(I1,I2)=DREAL(ADD)
23  AI(I1,I2)=DIMAG(ADD)
24  AR(12,I1)=AR(I1,I2)
25  AI(12,I1)=-AI(I1,I2)
26  WRITE(4,99)G1(1),G1(2),G1(3),G2(1),G2(2),G2(3),ADD
27  FORMAT(1X,3F8.4,2X,3F8.4,2X,2F11.5)
28  CONTINUE
29  CONTINUE
30  DO 30 I=1,NUM
31  GK=(G(I,1)+K(1))**2+(G(I,2)+K(2))**2+(G(I,3)+K(3))**2
32  AR(I,1)=AR(I,1)+GK
33  RETURN
34  END

```

STATISTICS SOURCE STATEMENTS = 32, PROGRAM SIZE = 2076 BYTES, PROGRAM NAME = MATRIX PAGE: 13.

STATISTICS NO DIAGNOSTICS GENERATED.

MATRIX END OF COMPILATION 10 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF GOSTAT KODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTODBL(NONE) NOSXM
 OPT(0) LARGVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

```

*.....1.....2.....3.....4.....5.....6.....7.....8
FUNCTION PLEG(L,X)
IMPLICIT REAL*8(A-H,O-Z)
PO=1.0D0
P1=X
IF(L.GT.1)GOTO 10
PLEG=PO
IF(L.EQ.1)PLEG=P1
RETURN
CONTINUE
DO 20 I=2,L
PLEG=(DFLOAT(2*I-1)*X*P1-DFLOAT(I-1)*PO)/DFLOAT(I)
PO=P1
CONTINUE
RETURN
END
10
20

```

STATISTICS SOURCE STATEMENTS = 16, PROGRAM SIZE = 682 BYTES, PROGRAM NAME = PLEG PAGE: 14.
 STATISTICS NO DIAGNOSTICS GENERATED.
 PLEG END OF COMPILATION 11 *****

SRCFLG

TRMFLG

NOTEST

TERM NOOBSJECT FIXED

CHARLEN(500)

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF GOSINT NODCK SOURCE TERM NOOBSJECT FIXED NOTEST TRMFLG SRCFLG

NOSYM KORENT NOSDUMP AUTOBL(NONE) NOSXM OPT(O) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE READIN(IG)
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMMON/INFO/A(3),B(3),C(3),G(750,4),TAU(3),VOL,NUM,RUHT
4  COMMON/CONST1/ZV1,AC1(2),CC1(2),A01(3),C01(6),A11(3),C11(6),
5  S A21(3),C21(6)
6  S COMMON/CONST2/ZV2,AC2(2),CC2(2),A02(3),C02(6),A12(3),C12(6),
7  S A22(3),C22(6)
8  S
9  S
10 S
11 S
12 S
13 S
14 S
15 S
16 S
17 S
18 S
19 S
20 S
21 S
22 S
23 S
24 S
25 S
26 S
27 S
28 S
29 S
30 S
31 S
32 S
33 S
34 S
35 S
36 S
37 S
38 S
39 S
40 S
41 S
42 S
43 S
44 S
45 S
46 S
47 S
48 S
49 S
50 S
51 S
52 S
53 S
54 S

```

*.....1.....2.....3.....4.....5.....6.....7.....8

```

55 WRITE(6,6)(C02(1),I=1,6)
56 WRITE(6,5)(A12(1),I=1,3)
57 WRITE(6,6)(C12(1),I=1,6)
58 WRITE(6,5)(A22(1),I=1,3)
59 WRITE(6,6)(C22(1),I=1,6)
60 CALL TRANS(A01(1),A01(2),A01(3),
    C01(1),C01(2),C01(3),C01(4),C01(5),C01(6))
61 $ CALL TRANS(A11(1),A11(2),A11(3),
    C11(1),C11(2),C11(3),C11(4),C11(5),C11(6))
62 $ CALL TRANS(A21(1),A21(2),A21(3),
    C21(1),C21(2),C21(3),C21(4),C21(5),C21(6))
63 $ CALL TRANS(A02(1),A02(2),A02(3),
    C02(1),C02(2),C02(3),C02(4),C02(5),C02(6))
64 $ CALL TRANS(A12(1),A12(2),A12(3),
    C12(1),C12(2),C12(3),C12(4),C12(5),C12(6))
65 $ CALL TRANS(A22(1),A22(2),A22(3),
    C22(1),C22(2),C22(3),C22(4),C22(5),C22(6))
66 RETURN
67 END

```

STATISTICS SOURCE STATEMENTS = 67, PROGRAM SIZE = 4368 BYTES, PROGRAM NAME = READIN PAGE: 15.

STATISTICS NO DIAGNOSTICS GENERATED.

READIN END OF COMPILATION 12 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSINT NODIACK SOURCE .TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM MORENT ROSDUMP AUTODBL(NONE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) L.PRECOUNT(64) CHARACTER(500)

4.....1.....2.....3.....4.....5.....6.....7.....8

```

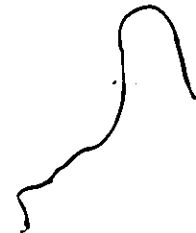
1 SUBROUTINE READK(K,WEIGHT,NUMK)
2 IMPLICIT REAL*8(A-H,O-Z)
3 REAL*8 K
4 DIMENSION K(100,3),WEIGHT(100)
5 FORMAT(2X,13)
6 1 FORMAT(4F10.0)
7 3 FORMAT(1 NUMK=,13/)
8 4 FORMAT(1 K,WEIGHT,4F11.6)
9 READ(5,1)NUMK
10 WRITE(6,3)NUMK
11 DO 10 I=1,NUMK
12 READ(5,2)K(1,1),K(1,2),K(1,3),WEIGHT(1)
13 WRITE(6,4)K(1,1),K(1,2),K(1,3),WEIGHT(1)
14 RETURN
15 END

```

STATISTICS SOURCE STATEMENTS = 15, PROGRAM SIZE = 982 BYTES, PROGRAM NAME = READK PAGE: 17.

STATISTICS NO DIAGNOSTICS GENERATED.

READK END OF COMPILATION 13 *****



OPTIONS IN EFFECT: HOLIST NOMAP NOXREF COSINT NODCK SOURCE TERM HOODJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTODBL(NORE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE RHO
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMPLEX*16 RRT,RR,RH,VC0UL
4  COMPLEX*16 TEM1,TEM2,TEM3,RCON,RCON1(48)
5  LOGICAL LGDOSM,LGF,LGDONE
6  COMMON/INFO/A(3),B(3),C(3),G(750,4),TAU(3),VOL,NUM,NUM1
7  COMMON/DENS/RH(533),RR(750),RRT(750),EX
8  COMMON/MINUS/INDEXG(533,533)
9  COMMON/STARS/MAP(533,4),MAP0(4),I,ISTART(75),I,STOP(75),N,STARS
10 COMMON/SPACE/RCON(750),WORK(750,8)
11 DIMENSION DELA(3),DELB(3),DELC(3),LGDOSM(4),LGF(48)
12 DIMENSION IEQV(48)
13 DATA DAMP/0.150000/
14 C ELEMENTS OF MAP ARE BAR4Z, 3, MXY, 2Z (IF BAR4Z, 2Z IS REDUNDANT)
15 DATA LGDOSM/.FALSE.,TRUE.,TRUE.,TRUE.,TRUE.,FALSE./
16 DAMM={1.00-DAMP}/DFLOAT(12167)
17 DO GO I=1,NUM1
18 RCON(I)=DCOMPLX(0.00,0.00)
19 DO 70 IND1=1,NUM
20 IND2=INDEXG(1,IND1)
21 RCON(IND1)=RCON(IND1)+0.500*RH(IND1)
22 RCON(IND2)=RCON(IND2)+0.500*DCONJG(RH(IND1))
23 CONTINUE
24 RCON(1)=RCON(1)/VOL
25 DO 80 NST=2,N,STARS
26 I,SHIFT=I,START(NST)-1
27 NS=I,STOP(NST)+1-I,ISTART(NST)
28 DO 79 I1=1,NS
29 DO 78 I2=1,NS
30 LGF(I2)=.FALSE.
31 LGF(I1)=.TRUE.
32 NEQ=1
33 RCON(11)=RCON(11)+I,SHIFT
34 IEQV(1)=I+I,SHIFT
35 LGDONE=.TRUE.
36 IF(.NOT.LGDOSM(1))GOTO81
37 NEQ1=NEQ
38 DO 83 J=1,NEQ1
39 JT=MAP(IEQV(J),1)
40 IF(LGF(JT-I,SHIFT))GOTO83
41 LGF(JT-I,SHIFT)=.TRUE.
42 LGDONE=.FALSE.
43 NEQ=NEQ+1
44 IEQV(NEQ)=JT
45 RCON(11)=RCON(11)+RCON(JT)
46 CONTINUE
47 CONF=TRUE
48 CONTINUE
49 IF(.NOT.LGDOSM(2))GOTO91
50 NEQ1=NEQ
51 DO 93 J=1,NEQ1
52 JT=MAP(IEQV(J),2)
53 IF(LGF(JT-I,SHIFT))GOTO93
54 LGF(JT-I,SHIFT)=.TRUE.
55 LGDONE=.FALSE.
56 NEQ=NEQ+1
57 IEQV(NEQ)=JT

```

*.....1.....2.....3.....4.....5.....6.....7.....8

```

56 RCON1(11)=RCON1(11)+RCON(JT)
57 CONTINUE
58 CONTINUE
59 IF(.NOT.LGDOSM(3))GOTO71
60 NEQ1=NEQ
61 DO 73 J=1,NEQ1
62 JT=MAP(IEQV(J),3)
63 IF(LGF(JT-ISHIFT))GOTO73
64 LGF(JT-ISHIFT)=.TRUE.
65 LGDONE=.FALSE.
66 NEQ=NEQ+1
67 IEQV(NEQ)=JT
68 RCON1(11)=RCON1(11)+RCON(JT)
69 CONTINUE
70 CONTINUE
71 IF(.NOT.LGDOSM(4))GOTO61
72 NEQ1=NEQ
73 DO 63 J=1,NEQ1
74 JT=MAP(IEQV(J),4)
75 IF(LGF(JT-ISHIFT))GOTO63
76 LGF(JT-ISHIFT)=.TRUE.
77 LGDONE=.FALSE.
78 NEQ=NEQ+1
79 IEQV(NEQ)=JT
80 RCON1(11)=RCON1(11)+RCON(JT)
81 CONTINUE
82 CONTINUE
83 IF(.NOT.LGDONE)GOTO119
84 RCON1(11)=RCON1(11)/(DFLOAT(NEQ)*VOL)
85 CONTINUE
86 DO 80 J=1,NS
87 RCON(J+ISHIFT)=RCON1(J)
88 CONTINUE
89 DO 5 I=1,3
90 DELA(I)=A(I)/23.DO
91 DELB(I)=B(I)/23.DO
92 DELC(I)=C(I)/23.DO
93 CONTINUE
94 DO 40 I=1,NUM
95 RRT(I)=DAMP*RRRT(I)
96 RR(I)=DAMP*RR(I)+(1.DO-DAMP)*RCON(I)
97 CONTINUE
98 EX=0.DO
99 DO 120 I1=1,23
100 DO 120 I2=1,23
101 DO 120 I3=1,23
102 X=DFLOAT(I1)*DELA(1)+DFLOAT(I2)*DELB(1)+DFLOAT(I3)*DELC(1)
103 Y=DFLOAT(I1)*DELA(2)+DFLOAT(I2)*DELB(2)+DFLOAT(I3)*DELC(2)
104 Z=DFLOAT(I1)*DELA(3)+DFLOAT(I2)*DELB(3)+DFLOAT(I3)*DELC(3)
105 TEM2=DCMPLX(0.DO,0.DO)
106 DO 130 IG1=1,NUM
107 RG=X*G(IG1,1)+Y*G(IG1,2)+Z*G(IG1,3)
108 TEM2=TEM2+RCON(IG1)*DCMPLX(DCOS(RG),DSIN(RG))
109 CONTINUE
110 RHI=TABS(DREAL(TEM2))
111 TT=TFORM(RHI)
112 EX=EX+RHI*EXG(RHI)
113 RHT=DAMP*TT
114 DO 120 I1=1,NUM
115 RG=G(I,1)*X+G(I,2)*Y+G(I,3)*Z

```

*.....1.....2.....3.....4.....5.....6.....7.....8

```

116 ISN RRT(1)=RRT(1)+DCHPLX(RHT*DCOS(RG),-RHT*DSIN(RG))
117 ISN CONTINUE
118 ISN EX=EX*VOL/DFLOAT(12167)
119 ISN REWIND 1
120 ISN LGDONE=.FALSE.
121 ISN READ(1,2)TEM1,TEM2
122 ISN DO 125 I=2,NUM
123 ISN IF(LGDONE)GOTO10
124 ISN READ(1,2,END=10)TEM1,TEM2
125 ISN GOTO11
126 ISN TEM1=(0.00,0.00)
127 ISN TEM2=(0.00,0.00)
128 ISN LGDONE=.TRUE.
129 ISN CONTINUE
130 ISN TEM3=(RR(1)-DAMP*TEM1)/(1.00-DAMP)
131 ISN EX=EX+VOL*DREAL(DCONJG(TEM3))*((0.2500,0.00)*
132 ISN 1 VCOUL(TEM3,G(1,4))-(0.500,0.00)*VCOUL(TEM1,G(1,4))-TEM2))
133 ISN CONTINUE
134 ISN REWIND 1
135 ISN WRITE(6,4)EX
136 ISN DO 50 I=1,NUM
137 ISN WRITE(6,1)RCON(1),RR(1),RRT(1)
138 ISN WRITE(1,2)RR(1),RRT(1)
139 ISN CONTINUE
140 ISN REWIND 1
141 ISN RETURN
142 ISN FORMAT(' EX ',F13.7)
143 ISN FORMAT(4F20.15)
144 ISN FORMAT(' RCON,RR,RRT ',3(3X,2F12.7))
145 ISN END

```

STATISTICS SOURCE STATEMENTS = 144, PROGRAM SIZE = 7818 BYTES, PROGRAM NAME = RHO PAGE: 18.

STATISTICS NO DIAGNOSTICS GENERATED.

RHO END OF COMPILATION 14 *****



OPTIONS IN EFFECT: MOLIET NOMAP NOXREF COSTMT HODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYH MORENT HOSDUMP AUTOOBL(NORE) NOSXM
 OPT(10) LANGLVL(77) NOFLIPS FLAG(1) NAME(MAIN) LINECOURT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE RSETUP(ISET,WEIGHT,VECR,VECI,EIG)
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMMON/INFO/GT(3009),TAU(4),NUM,NUM1
4  COMMON/DENS/RH(533),RR(750),RR1(750),EX
5  COMMON/MIRUS/INDEXG(533,533)
6  COMMON/TRACE/TR
7  DIMENSION VECR(NUM,5),VECI(NUM,5),EIG(5)
8  COMPLEX*16 RH,TEM,RR,RR1
9  IF(ISET.NE.0)TR=0.00
11 TR=TR+2.00*WEIGHT*(EIG(1)+EIG(2)+EIG(3)+EIG(4))
12 DO 5 I1=1,4
13 TEST=0.00
14 DO 6 I2=1,NUM
15 TEST=TEST+VECR(I2,I1)*VECR(I2,I1)+VECI(I2,I1)*VECI(I2,I1)
16 TEST=DSQRT(TEST)
17 DO 5 I2=1,NUM
18 VECR(I2,I1)=VECR(I2,I1)/TEST
19 VECI(I2,I1)=VECI(I2,I1)/TEST
20 IF(ISET.EQ.0)GOTO8
21 DO 7 I1=1,NUM
22 RH(I1)=(0.00,0.00)
23 CONTINUE
24 DO 10 I1=1,NUM
25 DO 10 I2=1,NUM
26 IND=INDEXG(I1,I2)
27 IF(IND.GT.NUM)GOTO10
28 TEM=(0.00,0.00)
29 DO 20 I=1,4
30 TEM=TEM+
31 1 DCMPLX(VECR(I2,I1),-VECI(I2,I1))*DCMPLX(VECR(I1,I1),VECI(I1,I1))
32 CONTINUE
33 RH(IND)=RH(IND)+TEM*DCMPLX(2.00*WEIGHT,0.00)
34 CONTINUE
35 RETURN
36 END

```

STATISTICS SOURCE STATEMENTS = 34, PROGRAM SIZE = 2218 BYTES, PROGRAM NAME = RSETUP PAGE: 21.

STATISTICS NO DIAGNOSTICS GENERATED.

RSETUP END OF COMPILATION 15 *****

OPTIONS IN EFFECT: HOLLIST NOMAP NOXREF COSTINT NODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTODDL(NORE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

```

*.....1.....2.....3.....4.....5.....6.....7.....8
SUBROUTINE SCF(AR,AI,VECR,VECI,EIG)
IMPLICIT REAL*8(A-H,O-Z)
REAL*8 K(100,3)
COMMON/INFO/G(3012),VOL,NUM,NUM1
COMMON/DENS/RR(533),RR(750),RRT(750),EX
COMMON/TRACE/TR
COMMON/SPACE/WORK(7500)
COMPLEX*16 RH,RR,RR1
DIMENSION WEIGHT(100),AR(1,1),AI(1,1),VECR(1,1),VECI(1,1)
DIMENSION EIG(1),TK(3)
DATA TK /3*5.D-3/
DATA INUM / 1/
DATA ETES/0.DO/
FORMAT(/,' TRACE=',F11.6,5X,'ENERGY=',F12.6,/)
FORMAT(1H1)
FORMAT('1 CONVERGED NOW DO K=0 TO GET GAP',/)
CALL READR(K,WEIGHT,NUMK)
CALL GCAL
IF(IG.EQ.0)CALL GUESS
IF(IG.NE.0)CALL LAST
CALL ITER(K,WEIGHT,NUMK,2,AR,AI,VECR,VECI,EIG)
INUM=INUM-1
CALL ENERGY(EN)
WRITE(6,1)TR,EN
WRITE(4,1)TR,EN
IF(DABS(TR-ETES).LT. 1.D-4)GOTO 20
IF(INUM.LE. 0)GOTO 21
REWIND 1
ETES=TR
WRITE(6,2)
GOTO 10
WRITE(6,4)
CONTINUE
CALL MATRIX(TK,2,AR,AI)
RLB=0.30
RUB=1.18D0
CALL EISCH3(NUM,NUM,AR,AI,RLB,RUB,4,NFOUND,
1 EIG,VECR,VECI,ICOND,WORK)
NU=NUM
IF(NU.GT.16)NU=16
WRITE(6,3)(EIG(I),I=1,NU)
3 FORMAT(1 FOR K=(0,0,0) EIG=1,8F11.6,/,21X,8F11.6)
C 24 READ(5,22,END=23)TK(1),TK(2),TK(3)
C CALL BAND(TK,2,AR,AI,VECR,VECI,EIG)
C GOTO 24
C 23 CONTINUE
22 RETURN
FORMAT(3F10.0)
END
    
```

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF GOSTMT NODCK SOURCE TERM NOOBJECT FIXED .NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTODBL(RHNE) NOSXP
 OPT(0) LANGVL(77),NOFLPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 ISN SUBROUTINE LAST
2 ISN IMPLICIT REAL*8(A-H,O-Z)
3 ISN COMPLEX*16 RRT,RR,RH
4 ISN COMMON/INFO/C(3013),NUM,NUM1
5 ISN COMMON/DENS/RH(533),RR(750),RRT(750),EX
6 ISN FORMAT(4F20.15)
7 ISN FORMAT(' USE RHO FROM LAST ITERATION')
8 ISN FORMAT(' R,RT',2F11.6,3X,2F11.6,7X,14)
9 ISN WRITE(6,2)
10 ISN DO 10 I=1,NUM1
11 ISN READ(3,1,END=99)RR(I),RRT(I)
12 ISN WRITE(1,1)RR(I),RRT(I)
13 ISN WRITE(6,3)RR(I),RRT(I),I
14 ISN REWIND 1
15 ISN RETURN
16 ISN END

```

STATISTICS SOURCE STATEMENTS = 16, PROGRAM SIZE = 886 BYTES, PROGRAM NAME = LAST PAGE: 23.

STATISTICS NO DIAGNOSTICS GENERATED.

LAST END OF COMPILATION 17 *****

OPTIONS IN EFFECT: HOLLIST NONMAP NOXRET GOSINT NODIECK SOURCE TERM NOOBJECT FIXED HOFIEST TRMFLO SRCFLO
 NOSYM NORENT ROSDUMP AUTODBL(NONE) NOSXM
 OPT(0) LANGLVL(77) HOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

```
*.....1.....2.....3.....4.....5.....6.....7.....8
FUNCTION STRUCT(K,G,GP,LMAX)
IMPLICIT REAL*8(A-H,O-Z)
REAL*8 K
COMMON/INFO/D(3009),TAU(3),VOL,RUM,NUM1
COMPLEX*16 STRUCT
DIMENSION K(3),G(3),GP(3),GG(3)
GG(1)=G(1)-GP(1)
GG(2)=G(2)-GP(2)
GG(3)=G(3)-GP(3)
```

C C C C C C C C

```
NEXT TWO STATEMENTS FIRD V(G) FOR ATOMS 1 AND 2
IF THE SAME S2=S1
ELSE EVALUATE BOTH USING SUML1 AND SUML2
S1=SUML1(K,G,GP,LMAX)
S2=S1
S2=SUML2(K,G,GP,LMAX)
QT=2.00*(GG(1)*TAU(1)+GG(2)*TAU(2)+GG(3)*TAU(3))
SS=2.00*(S1+DCOS(QT)*S2)/VOL
SA=2.00*DSIN(QT)*S2/VOL
STRUCT=DCHPLX(SS,SA)
RETURN
END
```

ISH 10 C
 ISH 11 C
 ISH 12 C
 ISH 13 C
 ISH 14 C
 ISH 15 C
 ISH 16 C
 ISH 17 C

STATISTICS SOURCE STATEMENTS = 17, PROGRAM SIZE = 894 BYTES, PROGRAM NAME = STRUCT PAGE: 24.
 STATISTICS NO DIAGNOSTICS GENERATED.
 STRUCT END OF COMPILATION 18 *****

OPTIONS IN EFFECT: ROLIST HOMAP:HOXREF COSTNT HODECK SOURCE TERM NOBJECT FIXED NOTEST TRMFLG SRCFLG
 HOSYH HORENT HOSDUMP AUTODBL(HOHE) HOSXN
 OPT(0) LARGVL(77) HOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLE(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 ISH FUNCTION ERF1(A,K2)
2 ISH IMPLICIT REAL*8(A-H,K-Z)
3 ISH DATA PI /3.14159265358979D0/
4 ISH ERF1=(PI/A)**1.5D0*DEXP(-0.25D0*K2/A)
5 ISH RETURN
6 ISH END

```

STATISTICS SOURCE STATEMENTS = 6, PROGRAM SIZE = 494 BYTES, PROGRAM NAME = ERF1 PAGE: 25.

STATISTICS NO DIAGNOSTICS GENERATED.

ERF1 END OF COMPILATION 19 *****

OPTIONS IN EFFECT: NOLIST NOHMAP NOXREF COSTMT NOXDECK SOURCE TERM NOORJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTODBL(NORE) NOSXH
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOURT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 ISH      FUNCTION ERF2(A,K2)
2 ISH      IMPLICIT REAL*8(A-H,K-Z)
3 ISH      DATA PI /3.14159265358979DD/
4 ISH      ERF2=(PI/A)**1.5D0*(6.D0*A-K2)*DEXP(-0.25D0*K2/A)/((4.D0*A*A)
5 ISH      RETURN
6 ISH      END

```

STATISTICS SOURCE STATEMENTS = 6, PROGRAM SIZE = 558 BYTES, PROGRAM NAME = ERF2 PAGE: 26.

STATISTICS NO DIAGNOSTICS GENERATED.

ERF2 END OF COMPILATION 20 *****

OPTIONS IN EFFECT: HOLLIST NOMAP HOSXREF COSTMT HODECK SOURCE TERM NOORJECT FIXED NOTEST TRMFLG SRCFLG
HOSYM HOREHT HOSDUMP AUTODBL(HOHE) HOSXN
OPT(0) LAHGLVL(77) HOFIPS FLAG(1) NAME(MAIR) LINECOUNT(64) CHARLEN(500)

.....1.....2.....3.....4.....5.....6.....7..........8

```

1  FUNCTION SUML1(K,G,GP,LMAX)
2  IMPLICIT REAL*8(A-H,O-Z)
3  REAL*8 K
4  COMMON/CONST1/ZV,A1C,A2C,C1C,C2C,A10,A20,A30,C10,C20,C30,C40,
5  C50,C60,A11,A21,A31,C11,C21,C31,C41,C51,C61,A12,A22,A32,
6  C12,C22,C32,C42,C52,C62
7  DIMENSION K(3),G(3),GP(3)
8  DATA FPI /12.56637061435917D0/
9  ALPHA=DSQRT((K(1)+G(1))*2+(K(2)+G(2))*2+(K(3)+G(3))*2)
10 BETA=DSQRT((K(1)+GP(1))*2+(K(2)+GP(2))*2+(K(3)+GP(3))*2)
11 ALBE=ALPHA*BETA
12 COSGAM=1.D0
13 IF(ALBE.GT.1.D-6)COSGAM=((K(1)+G(1))*(K(1)+GP(1))+
14 (K(2)+G(2))*(K(2)+GP(2))+(K(3)+G(3))*(K(3)+GP(3)))/ALBE
15 L=0
16 TEMP=C10*GAUSS0(A10,ALPHA,BETA,L)+C40*GAUSS2(A10,ALPHA,BETA,L)
17 +C20*GAUSS0(A20,ALPHA,BETA,L)+C50*GAUSS2(A20,ALPHA,BETA,L)
18 +C30*GAUSS0(A30,ALPHA,BETA,L)+C60*GAUSS2(A30,ALPHA,BETA,L)
19 -C12*GAUSS0(A12,ALPHA,BETA,L)-C42*GAUSS2(A12,ALPHA,BETA,L)
20 -C22*GAUSS0(A22,ALPHA,BETA,L)-C52*GAUSS2(A22,ALPHA,BETA,L)
21 -C32*GAUSS0(A32,ALPHA,BETA,L)-C62*GAUSS2(A32,ALPHA,BETA,L)
22 SUML1=FPI*DFLOAT(2*L+1)*TEMP*PLEG(L,COSGAM)
23 L=1
24 TEMP=C11*GAUSS0(A11,ALPHA,BETA,L)+C41*GAUSS2(A11,ALPHA,BETA,L)
25 +C21*GAUSS0(A21,ALPHA,BETA,L)+C51*GAUSS2(A21,ALPHA,BETA,L)
26 +C31*GAUSS0(A31,ALPHA,BETA,L)+C61*GAUSS2(A31,ALPHA,BETA,L)
27 -C12*GAUSS0(A12,ALPHA,BETA,L)-C42*GAUSS2(A12,ALPHA,BETA,L)
28 -C22*GAUSS0(A22,ALPHA,BETA,L)-C52*GAUSS2(A22,ALPHA,BETA,L)
29 -C32*GAUSS0(A32,ALPHA,BETA,L)-C62*GAUSS2(A32,ALPHA,BETA,L)
30 SUML1=SUML1+FPI*DFLOAT(2*L+1)*TEMP*PLEG(L,COSGAM)
31 CONTINUE
32 TEMP=(G(1)-GP(1))*2+(G(2)-GP(2))*2+(G(3)-GP(3))*2
33 SUML1=SUML1+C12*ERF1(A12,TEMP)+C22*ERF1(A22,TEMP)+
34 C32*ERF1(A32,TEMP)+C42*ERF2(A12,TEMP)+C52*ERF2(A22,TEMP)
35 +C62*ERF2(A32,TEMP)
36 IF(TEMP.LT.1.D-5)RETURN
37 RETURN
38 SUML1=SUML1-ZV*(C1C*ERFO(A1C,TEMP)+C2C*ERFO(A2C,TEMP))
39 ERD

```

STATISTICS SOURCE STATEMENTS = 24, PROGRAM SIZE = 2678 BYTES, PROGRAM NAME = SUML1 PAGE: 27.

STATISTICS NO DIAGNOSTICS GENERATED.

SUML1 END OF COMPILATION 21 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTANT NODRCK SOURCE TERM NOOBJECT FIXED NOFEST TRMFLG SRCFLG
 NOSYM MOREHT NOSDUMP AUTODBL(NONE) HOSXN
 OPT(O) LANGVL(77) NOFIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  FUNCTION SUML2(K,C,GP,LHMAX)
2  IMPLICIT REAL*8(A-H,O-Z)
3  REAL*8 K
4  COMMON/CONST2/ZV,A1C,A2C,C1C,C2C,A10,A20,A30,C10,C20,C30,C40,
5  C50,C60,A11,A21,A31,C11,C21,C31,C41,C51,C61,A12,A22,A32,
6  C12,C22,C32,C42,C52,C62
7  DIMENSION K(3),G(3),GP(3)
8  DATA FPI /12.5663706143591700/
9  ALPHA=DSQRT((K(1)+G(1))**2+(K(2)+G(2))**2+(K(3)+G(3))**2)
10 BETA=DSQRT((K(1)+GP(1))**2+(K(2)+GP(2))**2+(K(3)+GP(3))**2)
11 ALBE=ALPHA*BETA
12 COSGAM=1.00
13 IF(ALBE.GT.1.0-6) COSGAM=((K(1)+G(1))*(K(1)+GP(1))+
14 (K(2)+G(2))*(K(2)+GP(2))+(K(3)+G(3))*(K(3)+GP(3)))/ALBE
15 L=0
16 TEMP=C10*GAUSS0(A10,ALPHA,BETA,L)+C40*GAUSS2(A10,ALPHA,BETA,L)
17 +C20*GAUSS0(A20,ALPHA,BETA,L)+C50*GAUSS2(A20,ALPHA,BETA,L)
18 +C30*GAUSS0(A30,ALPHA,BETA,L)+C60*GAUSS2(A30,ALPHA,BETA,L)
19 -C12*GAUSS0(A12,ALPHA,BETA,L)-C42*GAUSS2(A12,ALPHA,BETA,L)
20 -C22*GAUSS0(A22,ALPHA,BETA,L)-C52*GAUSS2(A22,ALPHA,BETA,L)
21 -C32*GAUSS0(A32,ALPHA,BETA,L)-C62*GAUSS2(A32,ALPHA,BETA,L)
22 SUML2=FPI*DFLOAT(2*L+1)*TEMP*PLEG(L,COSGAM)
23 L=1
24 TEMP=C11*GAUSS0(A11,ALPHA,BETA,L)+C41*GAUSS2(A11,ALPHA,BETA,L)
25 +C21*GAUSS0(A21,ALPHA,BETA,L)+C51*GAUSS2(A21,ALPHA,BETA,L)
26 +C31*GAUSS0(A31,ALPHA,BETA,L)+C61*GAUSS2(A31,ALPHA,BETA,L)
27 -C12*GAUSS0(A12,ALPHA,BETA,L)-C42*GAUSS2(A12,ALPHA,BETA,L)
28 -C22*GAUSS0(A22,ALPHA,BETA,L)-C52*GAUSS2(A22,ALPHA,BETA,L)
29 -C32*GAUSS0(A32,ALPHA,BETA,L)-C62*GAUSS2(A32,ALPHA,BETA,L)
30 SUML2=SUML2+FPI*DFLOAT(2*L+1)*TEMP*PLEG(L,COSGAM)
31 CONTINUE
32 TEMP=(G(1)-GP(1))**2+(G(2)-GP(2))**2+(G(3)-GP(3))**2
33 SUML2=SUML2+C12*ERF1(A12,TEMP)+C22*ERF1(A22,TEMP)+
34 C32*ERF1(A32,TEMP)+C42*ERF2(A12,TEMP)+C52*ERF2(A22,TEMP)
35 +C62*ERF2(A32,TEMP)
36 IF(TEMP.LT.1.0-5)RETURN
37 RETURN
38 SUML2=SUML2-ZV*(C1C*ERFO(A1C,TEMP)+C2C*ERFO(A2C,TEMP))
39 END

```

STATISTICS SOURCE STATEMENTS = 24, PROGRAM SIZE = 2678 BYTES, PROGRAM NAME = SUML2 PAGE: 28.

STATISTICS NO DIAGNOSTICS GENERATED.

SUML2 END OF COMPILATION 22 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTANT NOCHECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYH NORENT NOSDU (P AUTO)DBL.(NONE) NOSXH
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINESCOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  FUNCTION SUM1(M,A)
2  IMPLICIT REAL*8(A-H,O-Z)
3  IF(DABS(A) .LT. 1.00D0)GOTO 20
4  F1=1.0D0
5  F2=1.0D0
6  S1=1.0D0
7  S2=1.0D0
8  SIGN=1.D0
9  IF(2*(M/2).EQ.M)SIGN=-1.D0
10 DO 10 I=1,M
11   F1=DFLOAT(M+1-I)*F1/A
12   F2=-F2
13   S1=S1+F1
14   S2=S2+F1*F2
15 CONTINUE
16 SUM1=(S2*DEXP(A)+SIGN*S1*DEXP(-A))/A
17 RETURN
18 CONTINUE
19 IF(2*(M/2) .NE. M)GOTO 30
20 INDM=0
21 A2=A**A
22 CUR=2.D0
23 SUM1=CUR/DFLOAT(M+1)
24 CONTINUE
25 INDM=INDM+2
26 CUR=CUR**A2/DFLOAT(INDM*(INDM-1))
27 SUM1=SUM1+CUR/DFLOAT(INDM+M+1)
28 IF(CUR.GT.1.D-17)GOTO 21
29 RETURN
30 CONTINUE
31 INDM=1
32 A2=A**A
33 CUR=2.D0**A
34 SUM1=CUR/DFLOAT(M+2)
35 CONTINUE
36 INDM=INDM+2
37 CUR=CUR**A2/DFLOAT(INDM*(INDM-1))
38 SUM1=SUM1+CUR/DFLOAT(INDM+M+1)
39 IF(DABS(CUR).GT.1.D-17)GOTO 22
40 RETURN
41 END

```

STATISTICS SOURCE STATEMENTS = 43, PROGRAM SIZE = 1434 BYTES, PROGRAM NAME = SUM1 PAGE: 29.

STATISTICS NO DIAGNOSTICS GENERATED.

SUM1 END OF COMPILATION 23 *****

OPTIONS IN EFFECT: NOLIST NOXREF GOSINT NODECK SOURCE TERM NOOBJECT FIXED NOTES TRMFLG SRCFLG
 NOSYM NORENT NOSDUHP AUTODBL(NONE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  FUNCTION TABS(A)
2  IMPLICIT REAL*8(A-H,O-Z)
3  TABS=A
4  IF(A.GT.0.DO)RETURN
5  TABS=0.DO
6  WRITE(6,1)A
7  RETURN
8
9  1  FORMAT(' A LESS THAN ZERO, A =',F13.5,5X,'*****')
10 END

```

STATISTICS SOURCE STATEMENTS = 9, PROGRAM SIZE = 490 BYTES, PROGRAM NAME = TABS PAGE: 30.

STATISTICS NO DIAGNOSTICS GENERATED.

TABS END OF COMPILATION 24 *****

OPTIONS IN EFFECT: MOLLIST NOHAP NOXREF GOSIMI MODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 MOSYM NORENT NOSDUMP AUTOOBL(NONE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

```

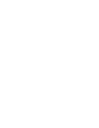
*.....1.....2.....3.....4.....5.....6.....7.....8
1      FUNCTION TFORM(RR)
2      IMPLICIT REAL*8(A-H,O-Z)
3      REAL*8 LM
4      DATA CONT /0.23873241D0/
5      DATA OT /0.3333333333333333D0/
6      IF(RR.EQ.0.D0)GOTO20
7      R=(CONJ/RR)**OT
8      TFORM=-0.61093/R
9      IF(R.LT.1.D0)GOTO 10
10     SR=DSQRT(R)
11     TFORM=TFORM-(0.1432D0+0.1759D0*SR+0.06366D0*R)/
12     S (1.D0+1.0529D0*SR+0.3334D0*R)**2
13     RETURN
14     LM=DLOG(R)
15     TFORM=TFORM-0.05837D0+0.0311D0*LM-0.0084D0*R+0.0013D0*LM*R
16     RETURN
17     TFORM=0.D0
18     RETURN
19     END

```

STATISTICS SOURCE STATEMENTS = 18, PROGRAM SIZE = 834 BYTES, PROGRAM NAME = TFORM PAGE: 31.

STATISTICS NO DIAGNOSTICS GENERATED.

TFORM END OF COMPILATION 25 *****



OPTIONS IN EFFECT: NOLIS NOMAP NOXREF GOSTMT HODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP .AUTODBL(NONE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

```

*.....1.....2.....3.....4.....5.....6.....7.....8
FUNCTION EXC(RR)
IMPLICIT REAL*8(A-H,O-Z)
DATA CON1 /0.33873241D0/
DATA OT /0.3333333333333333D0/
IF(RR.EQ.0.DD)GOTO20
R=(CON1/RR)**OT
EXC=-0.4582D0/R
IF(R.LT.1.DD)GOTO10
EXC=EXC-0.1432D0/(1.DD+1.0529D0*DSQRT(R))+0.3334D0*R)
RETURN
10 RL=DLOG(R)
EXC=EXC-0.0480D0+0.0311D0*RL-0.0116D0*R+0.0020D0*R*RL
RETURN
20 EXC=0.0D0
RETURN
16 END
  
```

STATISTICS SOURCE STATEMENTS = 16, PROGRAM SIZE = 756 BYTES, PROGRAM NAME = EXC PAGE: 32.

STATISTICS NO DIAGNOSTICS GENERATED.

EXC END OF COMPILATION 26 *****

OPTIONS IN EFFECT: HOLIST NODMAP NOXREF GOSTHT NODDECK SOURCE TERM NOOBJECT FIXED NOYEST TRMFLG SRCFLG
NOSYM NORENT NOSDUMP AUTODBL(NONE) NOSXM
OPT(O) LANGLYL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  FUNCTION TYP1(L,A)
2  IMPLICIT REAL*8(A-H,O-Z)
3  SIGN=-1.000
4  IF(2*(L/2).NE.L)SIGN= 1.000
5  FACTL=FACT(L)
6  SUM=0.000
7  L1=L+1
8  DO 10 K1=1,L1
9  K=L1-K1
10 SIGN=-SIGN
11 COEFF=FACTL/(FACT(K)*FACT(L-K))
12 SUM=SUM+SIGN*COEFF*SUM1(2*K,A)
13
14 CONTINUE
15 TYP1=SUM
16 RETURN
17 END

```

STATISTICS SOURCE STATEMENTS = 16, PROGRAM SIZE = 804 BYTES, PROGRAM NAME = TYP1 PAGE: 33.

STATISTICS NO DIAGNOSTICS GENERATED.

TYP1 END OF COMPILATION 27 *****

OPTIONS IN EFFECT: HOLLIST HOMAP HOXREF COSTMT HODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYH NORENT HOSDUMP AUTODBL(HONE) ROSXH
 OPT(0) LANGVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 ISH FUNCTION TYP2(L,A)
2 ISH IMPLICIT REAL*8(A-H,O-Z)
3 ISH SIGN=-1.0D0
4 ISH IF(2*(L/2).NE.L)SIGN= 1.0D0
6 ISH FACTL=FACT(L)
7 ISH SUM=0.0D0
8 ISH L1=L+1
9 ISH DO 10 K1=1,L1
10 ISH K=L1-K1
11 ISH SIGN=-SIGN
12 ISH COEFF=FACTL/(FACT(K)*FACT(L-K))
13 ISH SUM=SUM+SIGN*COEFF*SUM1(2*K+1,A)
14 ISH CONTINUE
15 ISH TYP2=SUM
16 ISH RETURN
17 ISH END

```

STATISTICS SOURCE STATEMENTS = 16, PROGRAM SIZE = 808 BYTES, PROGRAM NAME = TYP2 PAGE: 34.

STATISTICS NO DIAGNOSTICS GENERATED.

TYP2 END OF COMPILATION 28 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTIMI NODDECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 MOSYM MOREHT NOSDUMP AUTODBL(NONE) NOSXH
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

```

*.....1.....2.....3.....4.....5.....6.....7.*.....8
1  FUNCTION VCOUL(R,GS)
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMPLEX*16 VCOUL,R
4  DATA EPI /25.132741200/
5  IF(GS.GT.1.0-9)GOTO 10
6  VCOUL=DCMPLX(0.00,0.00)
7  RETURN
8  VCOUL=R*DCMPLX(EPI/GS,0.00)
9  RETURN
10 END

```

STATISTICS SOURCE STATEMENTS = 10, PROGRAM SIZE = 516 BYTES, PROGRAM NAME = VCOUL PAGE: 35:

STATISTICS NO DIAGNOSTICS GENERATED.

VCOUL END OF COMPILATION 29 *****

OPTIONS IN EFFECT: NOLIST NOMAP, NOXREF GOSTMT NOCHECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
NOSYM MORENT NOSDUMP AUTOBBL(MORE) NOSXXH
OPT(0) LANGVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE ITER(K,WEIGHT,MUMK,LMAX,AR,AI,VECR,VECI,EIG)
2  IMPLICIT REAL*8(A-H,O-Z)
3  REAL*8 K
4  COMMON/INFO/G(3013),NUM,NUM1
5  COMMON/SPACE/WORK(7500)
6  DIMENSION K(100,3),WEIGHT(100),AR(NUM,NUM),AI((NUM,NUM)
7  DIMENSION EIG(1),VECR(NUM,5),TK(3)
8  REAL*8 RUB(20)/0.4000,0.4800,0.4800,0.4800,0.4800,0.4800,15*0.00/
9  REAL*8 RUB(20)/1.1500,1.0600,1.1500,1.0600,1.0600,1.0600,15*0.00/
10  FORMAT(/,' SOLVE FOR K =',3F11.6)
11  FORMAT(' ',SETUP MATRIX')
12  FORMAT(' ',DIAGONALIZE')
13  FORMAT(' EIG =',9F11.6)
14  FORMAT(' EIG =',5F11.6,/,6X,4F11.6)
15  ISET=1
16  DO 10 I=1,MUMK
17  TK(1)=K(I,1)
18  TK(2)=K(I,2)
19  TK(3)=K(I,3)
20  WRITE(6,1)TK(1),TK(2),TK(3)
21  WRITE(6,2)
22  CALL MATRIX(TK,LMAX,AR,AI)
23  WRITE(6,3)

```

C CALL EISPACK DIAGONALIZATION

```

24  CALL EISCH3(NUM,NUM,AR,AI,RUB(1),RUB(1),4,RFOUND,
25  EIG,VECR,VECI,ICORD,WORK)
26  WRITE(6,4)(EIG(J),J=1,4)
27  IF(ICORD.NE.0)STOP'ERROR IN EISCH3'
28  IF(NFOUND.LT.4)STOP'NOT ENOUGH EIGENVALUES FOUND'
29  CALL RSETUP(ISET,WEIGHT(1),VECR,VECI,EIG)
30  ISET=0
31  CONTINUE
32  CALL RHO
33  RETURN
34  END

```

STATISTICS SOURCE STATEMENTS = 34, PROGRAM SIZE = 2344 BYTES, PROGRAM NAME = ITER PAGE: 36.

STATISTICS NO DIAGNOSTICS GENERATED.

ITER END OF COMPILATION 30 *****

OPTIONS IN EFFECT: NOLLIST NOMAP NOXREF COSTMT NOCHECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 HOSYH MORENT HOSDUMP AUTODBL(MOHE) HOSXH
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

```

*.....1.....2.....3.....4.....5.....6.....7.....8
SUBROUTINE GUESS
IMPLICIT REAL*8(A-H,O-Z)
COMPLEX*16 RRT,RR,RH
COMPLEX*16 TEM2
COMMON/INFO/A(3),B(3),C(3),G(750,4),TAU(4),NUM,NUM1
COMMON/DENS/RH(533),RR(750),RRT(750),EX
DIMENSION DELA(3),DELB(3),DELC(3)
DO 5 I=1,3
DELA(I)=A(I)/13.00
DELB(I)=B(I)/13.00
DELC(I)=C(I)/13.00
CONTINUE
DO 40 I=1,NUM
RR(I)=DCMPLX(0.00,0.00)
RRT(I)=DCMPLX(0.00,0.00)
DO 120 I1=1,13
DO 120 I2=1,13
DO 120 I3=1,13
X=DFLOAT(I1)*DELA(I1)+DFLOAT(I2)*DELB(I1)+DFLOAT(I3)*DELC(I1)
Y=DFLOAT(I1)*DELA(I2)+DFLOAT(I2)*DELB(I2)+DFLOAT(I3)*DELC(I2)
Z=DFLOAT(I1)*DELA(I3)+DFLOAT(I2)*DELB(I3)+DFLOAT(I3)*DELC(I3)
RHI=RHII(X,Y,Z)
RHI=TFORM(DABS(RHI))
DO 120 I=1,NUM
RG=G(I,1)*X+G(I,2)*Y+G(I,3)*Z
RRT(I)=RRT(I)+DCMPLX(RHI*DCOS(RG),-RHI*DSIN(RG))
RR(I)=RR(I)+DCMPLX(RHI*DCOS(RG),-RHI*DSIN(RG))
CONTINUE
TEM2=DCMPLX(1.00/DFLOAT(2197),0.00)
DO 50 I=1,NUM
RR(I)=RR(I)*TEM2
RRT(I)=RRT(I)*TEM2
WRITE(6,1)RR(I),RRT(I)
WRITE(1,2)RR(I),RRT(I)
CONTINUE
REWIND 1
RETURN
FORMAT(' RR,RRT ',2(3X,2F12.7))
FORMAT(1F20.15)
END

```

STATISTICS SOURCE STATEMENTS = 40, PROGRAM SIZE = 2520 BYTES, PROGRAM NAME = GUESS PAGE: 37.

STATISTICS NO DIAGNOSTICS GENERATED.

GUESS END OF COMPILATION 31 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF GOSTMT NODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTOOBL(NONE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE BAND(KM,LMAX,AR,AI,VECR,VECI,EIG)
2  IMPLICIT REAL*8(A-H,O-Z)
3  REAL*8 KM
4  COMMON/INFO/G(3013),NUM,NUM1
5  COMMON/SPACE/WORK(7500)
6  DIMENSION KM(3),AR(NUM,NUM),AI(NUM,NUM)
7  DIMENSION VECR(RUN,5),VECI(NUM,5),EIG(1)
8  FORMAT(/,' SOLVE FOR K =',3F11.6)
9  FORMAT(' EIG =',9F11.6)
10  FORMAT(' EIG =',5F13.6,/,6X,4F13.6)
11  WRITE(6,1)KM(1),KM(2),KM(3)
12  CALL MATRIX(KM,LMAX,AR,AI)
13  RLB=0.30
14  RUB=1.1800
15  CALL EISCH3(NUM,NUM,AR,AI,RLB,RUB,4,NFOUND,
16  EIG,VECR,VECI,ICOHD,WORK)
17  IF(ICOHD.NE.0)STOP'ERROR IN EISCH3'
18  IF(NFOUND.LT.4)STOP'NOT ENOUGH EIGENVALUES FOUND'
19  WRITE(6,4)(EIG(J),J=1,4)
20  WRITE(4,5)(EIG(J),J=1,4)
21  RETURN
22  END
23

```

STATISTICS SOURCE STATEMENTS = 21, PROGRAM SIZE = 1620 BYTES, PROGRAM NAME = BAND PAGE: 39.

STATISTICS NO DIAGNOSTICS GENERATED.

BAND END OF COMPILATION 33 *****

OPTIONS IN EFFECT: HOLIST NOMAP NOXREF, GOSTIMI HODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 ROSYM HOREHT NOSDUMP AUTODDL(HONE) NOSXN
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIR) L.IRECOURT(64) CHARLEN(500)

```
*.....1.....2.....3.....4.....5.....6.....7.....8
1 SUBROUTINE ENERGY(EH)
2 IMPLICIT REAL*8(A-H,O-Z)
3 COMMON/IRACE/TR
4 COMMON/DENS/RIH(533),RR(750),RRT(750),EX
5 COMMON/IRFO/B(9),G(750,4),TAU(3),VOL,NUM,HUM1
6 COMPLEX*16 RH,RR,RRT,YCOUL
7 FORMAT(' ALPHA,GEWALD',2F12.6)
8 CALL ALPHAZ(AZ)
9 CALL GEWALD(GE)
10 WRITE(6,1)AZ,GE
11 EN=TR+2.00*EX+AZ+GE
12 RETURN
13 END
```

STATISTICS SOURCE STATEMENTS = 13, PROGRAM SIZE = 552 BYTES, PROGRAM NAME = ENERGY PAGE: 40.
 STATISTICS NO DIAGNOSTICS GENERATED.
 ENERGY END OF COMPILATION 3/4 *****



OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTANT NOCHECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTODBL(MORE) NOSXN
 OPT(O) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 SUBROUTINE GEWALD(GAMMA)
2 IMPLICIT REAL*8(A-H,O-Z)
3 COMMON/INFO/A(3),B(3),C(3),G(750,4),TAU(3),V,NUM,NUM1
4 COMMON/CONST1/Z1,D1(31)
5 COMMON/CONST2/Z2,D2(31)
6 DATA PI /3.1415926535897900/
7 T1=2.00*TAU(1)
8 T2=2.00*TAU(2)
9 T3=2.00*TAU(3)
10 CHI2=2.3*(T1*T1+T2*T2+T3*T3)
11 CHI=DSQRT(CHI2)
12 V1=-2.00/(CHI*DSQRT(PI))
13 V2=0.00
14 V3=PI*CHI2
15 DO 10 I=2,NUM
16 S=DCOS(T1*G(I,1)+T2*G(I,2)+T3*G(I,3))
17 GG=0.2500*CHI2*G(I,4)
18 IF(GG.GT.35.00)GOTO10
19 TEM=PI*CHI2*DEXP(-GG)/(GG*V)
20 V1=V1+TEM
21 V2=V2+TEM*S
22 CONTINUE
23 DO 20 I11=1,9
24 I1=I11-5
25 DO 20 I12=1,9
26 I2=I12-5
27 DO 20 I13=1,9
28 I3=I13-5
29 X=DFLOAT(I1)*A(I1)+DFLOAT(I2)*B(I1)+DFLOAT(I3)*C(I1)
30 Y=DFLOAT(I1)*A(I2)+DFLOAT(I2)*B(I2)+DFLOAT(I3)*C(I2)
31 Z=DFLOAT(I1)*A(I3)+DFLOAT(I2)*B(I3)+DFLOAT(I3)*C(I3)
32 R12=X*X+Y*Y+Z*Z
33 R22=(X+T1)**2+(Y+T2)**2+(Z+T3)**2
34 R1=DSQRT(R12)
35 R2=DSQRT(R22)
36 IF(R1.GT.1.D-5)V1=V1+DERFC(R1/CHI)/R1
37 V2=V2+DERFC(R2/CHI)/R2
38 CONTINUE
39 GAMMA=(Z1*Z1+Z2*Z2)*V1+2.00*Z1*Z2*V2-(Z1+Z2)**2*V3/V
40 RETURN
41 END

```

STATISTICS SOURCE STATEMENTS = 41, PROGRAM SIZE = 2106 BYTES, PROGRAM NAME = GEWALD PAGE: 41.

STATISTICS NO DIAGNOSTICS GENERATED.

GEWALD END OF COMPILATION 35 *****

OPTIONS IN EFFECT: HOLIST HOMAP HOSREF COSTINT HODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
HOSYH HORENT HOSDUMP AUTOOBL(HORE) HOSXH
OPT(O) LANGLVL(77) HOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

```

*.....1.....2.....3.....4.....5.....6.....7.....8
SUBROUTINE ALPHAZ(ZALPHA)
  IMPLICIT REAL*8(A-H,O-Z)
  COMMON/INFO/G(3012),V,RUN,NUM1
  COMMON/CONST1/Z1,A1(2),C1(2),D1(27)
  COMMON/CONST2/Z2,A2(2),C2(2),D2(27)
  ZALPHA=(8.D0*0.7853981600/V)*Z1*(C1(1)/A1(1)+C1(2)/A1(2))+
    Z2*(C2(1)/A2(1)+C2(2)/A2(2))*Z1+Z2
  RETURN
END

```

STATISTICS SOURCE STATEMENTS = 8, PROGRAM SIZE² = 512 BYTES, PROGRAM NAME = ALPHAZ PAGE: 42.

STATISTICS NO DIAGNOSTICS GENERATED.

ALPHAZ END OF COMPILATION 36 *****

OPTIONS IN EFFECT: HOLLIST HONAP HONREF COSIMT HODECK SOURCE TERM HONOBJECT FIXED HONEST TRMFLG SRCFLG
 NOSYM HONRENT HOSDUMP AUTODBL(HONR) HOSXM
 OPT(O) LANGVL(77) HONFIPS FLAG(1) NAME(MAIN) LINECOURT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

1 SUBROUTINE TRANS(A1,A2,A3,C1,C2,C3,C4,C5,C6)
 2 IMPLICIT REAL*8(A-H,O-Z)
 3 REAL*16 S,Q,Y,TEMP,B2,B4,B6
 4 DIMENSION S(6,6),Q(6,6),Y(6,6)
 5 B2=0.500*QSQR(QATAN(1.Q0))
 6 B4=1.500*B2
 7 B6=2.500*B4

8 SET UP S
 9 S(1,1)=B2/((A1+A1)**1.500)
 10 S(1,2)=B2/((A1+A2)**1.500)
 11 S(1,3)=B2/((A1+A3)**1.500)
 12 S(2,2)=B2/((A2+A2)**1.500)
 13 S(2,3)=B2/((A2+A3)**1.500)
 14 S(3,3)=B2/((A3+A3)**1.500)
 15 S(1,4)=B4/((A1+A1)**2.500)
 16 S(1,5)=B4/((A1+A2)**2.500)
 17 S(1,6)=B4/((A1+A3)**2.500)
 18 S(2,5)=B4/((A2+A2)**2.500)
 19 S(2,6)=B4/((A2+A3)**2.500)
 20 S(3,6)=B4/((A3+A3)**2.500)
 21 S(2,4)=S(1,5)
 22 S(3,4)=S(1,6)
 23 S(4,4)=B6/((A1+A1)**3.500)
 24 S(4,5)=B6/((A1+A2)**3.500)
 25 S(4,6)=B6/((A1+A3)**3.500)
 26 S(5,5)=B6/((A2+A2)**3.500)
 27 S(5,6)=B6/((A2+A3)**3.500)
 28 S(6,6)=B6/((A3+A3)**3.500)

29 NOW SET UP Q
 30 Q(1,1)=QSQR(S(1,1))
 31 DO 10 L=2,6
 32 L=L-1
 33 DO 30 I=1,L1
 34 TEMP=0.Q0
 35 IF(1.EQ.1)GOTO 39
 36 I1=I-1
 37 DO 40 K=1,I1
 38 TEMP=TEMP-Q(K,I)*Q(K,L)
 39 Q(I,L)=(TEMP+S(I,L))/Q(I,1)
 40 CONTINUE
 41 TEMP=0.Q0
 42 DO 20 K=1,L1
 43 TEMP=TEMP-Q(K,L)*Q(K,L)
 44 Q(L,L)=QSQR(TEMP+S(L,L))
 45 CONTINUE

45 NOW FIND -Q INVERSE AND PUT IN Y
 46 Y(1,1)=-1.Q0/Q(1,1)
 47 DO 50 I=2,6
 48 Y(I,1)=-1.Q0/Q(I,1)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

48 ISN      I1=I-1
49 ISN      DO 60 JJ=1,I1
50 ISN      J=1-JJ
51 ISN      TEMP=0.00
52 ISN      J1=J+1
53 ISN      DO 70 K=J1,I
54 ISN      TEMP=TEMP-Q(J,K)*Y(K,I)
55 ISN      Y(J,I)=TEMP/Q(J,J)
56 ISN      CONTINUE

```

C C NOW FIND A'S AND STORE IN SAME PLACE AS C'S

```

57 ISN      C1=C1*Y(1,1)+C2*Y(1,2)+C3*Y(1,3)+C4*Y(1,4)+C5*Y(1,5)+C6*Y(1,6)
58 ISN      C2=C2*Y(2,2)+C3*Y(2,3)+C4*Y(2,4)+C5*Y(2,5)+C6*Y(2,6)
59 ISN      C3=C3*Y(3,3)+C4*Y(3,4)+C5*Y(3,5)+C6*Y(3,6)
60 ISN      C4=C4*Y(4,4)+C5*Y(4,5)+C6*Y(4,6)
61 ISN      C5=C5*Y(5,5)+C6*Y(5,6)
62 ISN      C6=C6*Y(6,6)
63 ISN      RETURN
64 ISN      END

```

C C

STATISTICS SOURCE STATEMENTS = 64, PROGRAM SIZE = 6626 BYTES, PROGRAM NAME = TRANS PAGE: 43.

**STATISTICS* NO DIAGNOSTICS GENERATED.

TRANS END OF COMPILATION 37 *****

Sample Input Data for the Total Energy Program



F

VM/SP CONVERSATIONAL MONITOR SYSTEM

FILE: INAS

DATA	B	IN	AS
580 10			
5.50000	0.00000		
5.50000	5.50000		
0.00000	5.50000		
1.37500	1.37500		
3.00000	0.71000	IN	
6.72510	-5.72510		
1.09000	1.66000		
-6.35770	-0.39020	0.30240	0.00960 -0.02180
0.99000	1.24000		
-5.11500	-0.07270	0.15520	0.07910 0.01390
0.64000	0.72000		
-5.29750	-1.15210	0.04970	-0.04930 0.04480
5.00000	2.60000	AS	
2.62180	-1.62180		
2.41000	2.77000		
-4.71620	0.79520	0.13260	-0.01520 -0.02690
1.74000	1.92000		
-3.71410	0.18770	0.08300	-0.01710 -0.01060
1.67000	1.93000		
-3.38450	0.09480	-0.04780	-0.07890 -0.02270
2			
.142800	.142800	.25000000	TWO SPECIAL POINTS FOR FCC
.428399	.142800	.75000000	

2

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The Computer Code for the SCH Approximation

2

REQUESTED OPTIONS (EXECUTE): NOMAP NOXREF NOOBJECT

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF GOSTMT NODRCK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTODBL(NONE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

C SELF CONSISTENT HARMONIC APPROXIMATION FOR FCC RARE GAS SOLIDS
 C PROGRAM WRITTEN BY D. SINGH (1984)
 C
 C
 C

```

1 ISN      IMPLICIT REAL*8(A-H,O-Z)
2 ISN      DATA WPREV/0.D0/
3 ISN      DATA PREC /5.DF6/
4 ISN      DATA ITERM/75/
5 ISN      CALL READIN
6 ISN      ITERM=0
7 ISN      CALL DYHAM1(WAV,FS)
8 ISN      IF(DABS(WAV-WPREV).LE.PREC)GOTO20
9 ISN      WPREV=WAV
10 ISN     ITERM=ITER+1
11 ISN     WRITE(4,2)ITER,WAV,FS
12 ISN     IF(ITER.LE.ITERM)GOTO10
13 ISN     WRITE(6,1)ITER
14 ISN     STOP
15 ISN     CALL BRANCH
16 ISN     FREE=FS*0.5D0*AVEO(0)
17 ISN     WRITE(6,3)FREE
18 ISN     STOP
19 ISN     FORMAT(//,' NOT CONVERGED AFTER',I3,' ITERATIONS',/,
20 ISN     ' ABANDONING CALCULATION **')
21 ISN     FORMAT(2X,I4,3X,F15.8,D17.8)
22 ISN     FORMAT(' FREE ENERGY FOLLOWS',/,/, ' FREE =',F13.2)
    END
    
```

STATISTICS SOURCE STATEMENTS = 22, PROGRAM SIZE = 806 BYTES, PROGRAM NAME = MAIN PAGE: 1.

STATISTICS NO DIAGNOSTICS GENERATED.

MAIN END OF COMPILATION 1 *****

OPTIONS IN EFFECT:	HOLLIST	NOHMAP	NOXREF	COSTMT	RODECK	SOURCE	TERM	NOBJECT	FIXED	NOTEST	TRMFLG	SRCFLG
	ROSYH	KORENT	NOSDUMP	AUTODBL	(NONE)	ROSYH						
	OPT(0)	LARGLVL(77)	NOFTPS	FLAG(1)	NAME(MAIN)					CHARLEN(500)		

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE CALCS
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMMON/ATOMS/H(2400,4),ISH(2400),RSHELL(80),DD(80,7),IS,R
4  COMMON/WIDTH/A(80,3),RM(80,3)
5  COMMON/WAVEF/D(80,3,3),S(80,3,3),RL(80,3)
6  DIMENSION SI(3,3),X(3),DTEH(3,3),WORK(10)
7  DO 1000 ISHELL=2,IS
8  DO 6 I=1,3
9  DO 6 J=1,3
10 DTEM(I,J)=D(ISHELL,I,J)

```

C CALL IMSL DIAGONALIZATION ROUTINE

```

11 CALL EIGRS(DTEH,3,12,X,ST,3,WORK,IER)
12 IF(DABS(X(1)).LT.1.D-20)X(1)=1.D-20
13 IF(DABS(X(2)).LT.1.D-20)X(2)=1.D-20
14 IF(DABS(X(3)).LT.1.D-20)X(3)=1.D-20
15 A(ISHELL,1)=1.D0/X(1)
16 A(ISHELL,2)=1.D0/X(2)
17 A(ISHELL,3)=1.D0/X(3)
18 DO 10 I=1,3
19 RM(ISHELL,I)=0.00
20 DO 10 J=1,3
21 RM(ISHELL,I)=RM(ISHELL,I)+ST(J,I)*RL(ISHELL,J)
22 S(ISHELL,I,J)=SI(J,I)
23 CONTINUE
24 RETURN
25 END

```

STATISTICS SOURCE STATEMENTS = 25, PROGRAM SIZE = 1556 BYTES, PROGRAM NAME = CALCS PAGE: 2.

STATISTICS NO DIAGNOSTICS GENERATED.

CALCS END OF COMPILATION 2 *****

OPTIONS IN EFFECT: HOLLIST HOMAP HOXREF COSTMT HODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYH MORENT HOSDUMP AUTODBL(NONE) NOSXX
 OPT(0) LANGVL(77) NOFIPS FLAG(1) NAME(MAIN) LIWCOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE FORCE1(ICRID)
C
C  CALCULATES THE SEVEN AVERAGES NEEDED FOR THE FORCE CONSTANTS
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMMON/SPHERE/R(2000,3), IH(2000), N1, N2, N3
4  COMMON/ATOMS/H(2400,4), ISH(2400), RSHELL(80), DD(80,7), IS, N
5  COMMON/WIDTH/A(80,3), RM(80,3)
6  REAL*4 R
7  DATA ITEST/0/
8  DATA EPS/2.0-4/
9  DATA PI/3.1415926535897932300/
10 IF (ITEST.EQ.0) CALL GEN5(ICRID)
11 ITEST=1
12 WRITE(6,2) N1, N2, N3, EPS
13 DO 1000 ISHELL=2, IS
14 X=RM(ISHELL,1)
15 Y=RM(ISHELL,2)
16 Z=RM(ISHELL,3)
17 A1=A(ISHELL,1)
18 A2=A(ISHELL,2)
19 A3=A(ISHELL,3)
20 RM1=DSQRT(-2.00*DLOG(EPS)/A1)
21 RM2=DSQRT(-2.00*DLOG(EPS)/A2)
22 RM3=DSQRT(-2.00*DLOG(EPS)/A3)
23 S11=0.00
24 S12=0.00
25 S13=0.00
26 S14=0.00
27 S15=0.00
28 S16=0.00
29 S17=0.00
30 S21=0.00
31 S22=0.00
32 S23=0.00
33 S24=0.00
34 S25=0.00
35 S26=0.00
36 S27=0.00
37 S31=0.00
38 S32=0.00
39 S33=0.00
40 S34=0.00
41 S35=0.00
42 S36=0.00
43 S37=0.00
44
45 C (1,J,S) (1,1,1),(1,2,2),(1,3,3),(2,2,4),(2,3,5),(3,3,6)
46 C ALPHA=BETA ( , , 7)
47 DO 10 I=1, N3
48 R1=RM1*R(1,1)
49 R2=RM2*R(1,2)
50 R3=RM3*R(1,3)
51 IND=IH(I)
52 C1=R1+X
53 C2=R2+Y
54 C3=R3+Z

```

```

53  CC=C1*C1+C2*C2+C3*C3
54  DIST=DSRT(C1)
55  CALL DDIAZIZ(DIST,01,02)
56  PREF=DEXP(-0.500*(A1*R1+A2*R2+A3*R3*R3))
57  SS1=C1*C1*02*PREF/CC
58  SS2=C1*C2*02*PREF/CC
59  SS3=C1*C3*02*PREF/CC
60  SS4=C2*C2*02*PREF/CC
61  SS5=C2*C3*02*PREF/CC
62  SS6=C3*C3*02*PREF/CC
63  SS7=01*PREF
64  S31=S31+SS1
65  S32=S32+SS2
66  S33=S33+SS3
67  S34=S34+SS4
68  S35=S35+SS5
69  S36=S36+SS6
70  S37=S37+SS7
71  IF(IRD.EQ.3)GOTO10
72  S21=S21+SS1
73  S22=S22+SS2
74  S23=S23+SS3
75  S24=S24+SS4
76  S25=S25+SS5
77  S26=S26+SS6
78  S27=S27+SS7
79  IF(IRD.EQ.2)GOTO10
80  S11=S11+SS1
81  S12=S12+SS2
82  S13=S13+SS3
83  S14=S14+SS4
84  S15=S15+SS5
85  S16=S16+SS6
86  S17=S17+SS7
87  CONTINUE
88  PREF=-DSQRT(A1*A2*A3/(2.00*PI)**3)
89  VOL=(4.00*PI/3.00)*RM1*RM2*RM3
90  P1=PREF*VOL/DFLOAT(45*N1)
91  P2=-20.00*PREF*VOL/DFLOAT(45*N2)
92  P3=64.00*PREF*VOL/DFLOAT(45*N3)
93  DD(SHELL,1)=P1*S11+P2*S21+P3*S31
94  DD(SHELL,2)=P1*S12+P2*S22+P3*S32
95  DD(SHELL,3)=P1*S13+P2*S23+P3*S33
96  DD(SHELL,4)=P1*S14+P2*S24+P3*S34
97  DD(SHELL,5)=P1*S15+P2*S25+P3*S35
98  DD(SHELL,6)=P1*S16+P2*S26+P3*S36
99  DD(SHELL,7)=P1*S17+P2*S27+P3*S37
5  FORMAT(/,7(/,1X,3D20.10))
C  S11=S11/DFLOAT(N1)
C  S21=S21/DFLOAT(N2)
C  S31=S31/DFLOAT(N3)
C  S12=S12/DFLOAT(N1)
C  S22=S22/DFLOAT(N2)
C  S32=S32/DFLOAT(N3)
C  S13=S13/DFLOAT(N1)
C  S23=S23/DFLOAT(N2)
C  S33=S33/DFLOAT(N3)
C  S14=S14/DFLOAT(N1)
C  S24=S24/DFLOAT(N2)
C  S34=S34/DFLOAT(N3)

```

*.....1.....2.....3.....4.....5.....6.....7.....8

```

C S15=S15/DFLOAT(N1)
C S25=S25/DFLOAT(N2)
C S35=S35/DFLOAT(N3)
C S16=S16/DFLOAT(N1)
C S26=S26/DFLOAT(N2)
C S36=S36/DFLOAT(N3)
C S17=S17/DFLOAT(N1)
C S27=S27/DFLOAT(N2)
C S37=S37/DFLOAT(N3)
C WRITE(7,5)S11,S21,S31,S12,S22,S32,S13,S23,S33,S14,S24,S34,
1 WRITE(6,1)ISHELL,(DD(ISHELL,I),I=1,7)
C WRITE(6,3)A(ISHELL,1),A(ISHELL,2),A(ISHELL,3)
C WRITE(6,4)X,Y,Z
C CONTINUE
C 1000 RETURN
C 1 FORMAT(' ISHELL, DD ',12,3X,7F13.5)
C 2 FORMAT(' 1 AVERAGES USE N1,N2,N3,316,5X,EPS =',08.1,/,/)
C 3 FORMAT(' A1,A2,A3 ',3F13.7)
C 4 FORMAT(' R1,R2,R3 ',3F13.7,/)
C END

```

STATISTICS SOURCE STATEMENTS = 108, PROGRAM SIZE = 3692 BYTES, PROGRAM NAME = FORCE1 PAGE: 3.

STATISTICS NO DIAGNOSTICS GENERATED.

FORCE1 END OF COMPILATION 3 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTMT NODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTODBL(NORE) NOSXM
 OPT(0) LANGVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 SUBROUTINE GENS(NUM)
2 IMPLICIT REAL*4(A-H,O-Z)
3 COMMON/SPHERE/R(20000,3), IH(20000), N1,N2,N3
4 N1=0
5 N2=0
6 N3=0
7 LIM=2*NUM+1
8 DEL=1./FLOAT(NUM)
9 DO 10 I1=1,LIM
10 J1=11-NUM-1
11 X=DEL*FLOAT(J1)
12 DO 10 I2=1,LIM
13 Y=DEL*FLOAT(J2)
14 DO 10 I3=1,LIM
15 J3=13-NUM-1
16 Z=DEL*FLOAT(J3)
17 R2=X*X+Y*Y+Z*Z
18 IF(R2.GE.1.0001)GOTO10
19 I=3
20 N3=N3+1
21 IF(N3.GT.20000)STOX00320
22 R(N3,1)=X
23 R(N3,2)=Y
24 R(N3,3)=Z
25 IF(2*(J1/2).NE.J1)GOTO5
26 IF(2*(J2/2).NE.J2)GOTO5
27 IF(2*(J3/2).NE.J3)GOTO5
28 I=2
29 N2=N2+1
30 IF(4*(J1/4).NE.J1)GOTO5
31 IF(4*(J2/4).NE.J2)GOTO5
32 IF(4*(J3/4).NE.J3)GOTO5
33 I=1
34 N1=N1+1
35 IH(N3)=1
36 CONTINUE
37 RETURN
38 END
39
40

```

STATISTICS SOURCE STATEMENTS = 39, PROGRAM SIZE = 1354 BYTES, PROGRAM NAME = GENS PAGE: 6.
 STATISTICS NO DIAGNOSTICS GENERATED.
 GENS END OF COMPILATION **

OPTIONS IN EFFECT: HOLLIST NOMAP NOXREF COSTMT NOCHECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 HOSYH HOREHT HOSDUMP AUTODBL(HOHE) HOSXH
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLER(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  C SUBROUTINE DAZIZ(R,01,02)
    C AZIZ CHEN POTENTIAL FOR ARGON HFD-C
    C RETURNS 01,02
    C J. CHEM. PHYS. 67,5719 (1977)
    C UNITS R IN ANGSTROMS, ENERGIES AZIZ IN DEGREES K,
    C IMPLICIT REAL*8(A-H,O-Z)
    C DATA A/O.9502720D0/
    C DATA ALPHA/16.345655D0/
    C DATA C6 /1.0914254D0/
    C DATA C8 /0.6002595D0/
    C DATA C10/0.3700113D0/
    C DATA D/1.4D0/
    C DATA E/143.224D0/
    C DATA GAMMA/2.D0/
    C DATA RM/3.759D0/
    C KRYPTON -- MOL. PHYS. 38,177 (1979)
    C DATA A/O.1215312D8/
    C DATA ALPHA/16.496763D0/
    C DATA C6 /1.1561739D0/
    C DATA C8 /0.5414923D0/
    C DATA C10/0.2839735D0/
    C DATA D/1.28D0/
    C DATA E/199.900D0/
    C DATA GAMMA/2.4D0/
    C DATA RM/4.012D0/
    C X=R/RM
    C 01=0.D0
    C 02=0.D0
    C AX=ALPHA*X
    C IF(AX.GT.100.D0)GOTO5
    C PREF=A**X*(GAMMA-2.D0)*DEXP(-AX)
    C 01=PREF*(GAMMA-AX)
    C 02=PREF*(GAMMA*(GAMMA-1.D0)-AX*2.D0*(GAMMA+AX)*AX)
    C CONTINUE
    C 5
    C X6=1.D0/X**6
    C X7=X6/X
    C X8=X7/X
    C X9=X8/X
    C X10=X9/X
    C X11=X10/X
    C X12=X11/X
    C 00=-C6*X6-C8*X8-C10*X10
    C D1=6.D0*C6*X7+8.D0*C8*X9+10.D0*C10*X11
    C D2=-42.D0*C6*X8-72.D0*C8*X10-110.D0*C10*X12
    C E0=1.D0
    C E1=0.D0
    C E2=0.D0
    C IF(X.GE.D)GOTO10
    C DX=D/X
    C E0=0.D0
    C IF(DX.GT.11)GOIQ10
    C E0=DEXP(-(DX-1.D0)**2)
    C E1=2.D0*DX*(DX-1.D0)*E0/X
    C E2=2.D0*DX*(DX-1.D0)*E1/X+2.D0*DX*(2.D0-3.D0*DX)*E0/(X*X)
    C CONTINUE
    C 10
    C 01=(01*(D0*E1+E0*D1)/X)*E/(RM*RM)
  
```

*.....1.....2.....3.....4.....5.....6.....7.....8

ISH 43 02=(02+D0*E2+2.00*D1*E1+D2*E0)*E/(RM*RH)-01
ISH 44 RETURN
ISH 45 END

STATISTICS SOURCE STATEMENTS = 45, PROGRAM SIZE = 1594 BYTES, PROGRAM NAME = DAZIZ PAGE: 7.

STATISTICS NO DIAGNOSTICS GENERATED.

DAZIZ END OF COMPILATION 5 *****

OPTIONS IN EFFECT: ROLIST HOMAP HOSREF GOSTMT HODECK SOURCE TERM HOOBJECT FIXED HOFEST TRNFLG SRCFLG
 ROSYH HORENT HOSDUMP AUTODBL(HOME) HOSXN
 OPT(0) LANGLVL(77) HOFIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE GENFCC(A,RAD)
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMMON/ATOMS/R(2400,4),ISHELL(2400),RSHELL(80),DD(80,7),IS,N,H
4  DIMENSION INDEX(2400),TEMP(2400)
5  R=0
6  A2=0.500*A
7  IMAX=RAD/A2
8  IH=2*IMAX+1
9  DO 10 I=1, IH
10  I1=I1-IMAX-1
11  DO 10 I2=1, IH
12  I2=I2-IMAX-1
13  DO 10 I3=1, IH
14  I3=I3-IMAX-1
15  X=DFLOAT(I2+I3)*A2
16  Y=DFLOAT(I1+I3)*A2
17  Z=DFLOAT(I1+I2)*A2
18  RR=DSQRT(X*X+Y*Y+Z*Z)
19  IF(RR.GT. RAD)GOTO10
20  R=R+1
21  IF(N.GT.2399)STOP00812
22  INDEX(N)=N
23  R(N,1)=X
24  R(N,2)=Y
25  R(N,3)=Z
26  R(N,4)=RR*DABS(X*Y*Z)*1.11D-5+1.3D-8*(DABS(X)+DABS(Y)+DABS(Z))
27  CONTINUE
28  10
29  HEAPIFY
30  MAXI=R/2
31  DO 20 K=1,MAXI
32  I=MAX1+1-K
33  J=2*I
34  ITEM=INDEX(I)
35  TEM=R(ITEM,4)
36  IF(J-N)17,18,16
37  IF(R(INDEX(J),4).LT.R(INDEX(J+1),4))J=J+1
38  IF(TEM.GE.R(INDEX(J),4))GOTO16
39  INDEX(J/2)=INDEX(J)
40  J=2*J
41  GOTO15
42  CONTINUE
43  INDEX(J/2)=ITEM
44  CONTINUE
45  SORT HEAP
46  NI=R-1
47  DO 30 I=1,NI
48  J=N-I+1
49  I1=INDEX(J)
50  INDEX(J)=INDEX(I)
51  INDEX(I)=I1
52  J=J-1
53  RESTORE HEAP
54  I1=1
55  I1=2*I1
56  IF(11-J)31,35,30
57  IF(R(INDEX(I1),4).LT.R(INDEX(I1+1),4))I1=I1+1

```

*.....1.....2.....3.....4.....5.....6.....7.....8

```

57 ISN IF(R(INDEX(11),4).GE.R(INDEX(11),4))GOTO30
58 ISN I11=INDEX(11)
59 ISN INDEX(11)=INDEX(I11)
60 ISN INDEX(11)=I11
61 ISN I1=I1
62 ISN GOTO25
63 ISN CONTINUE
64 ISN DO 40 I=1,4
65 ISN DO 45 J=1,N
66 ISN TEMP(J)=R(J,I)
67 ISN DO 40 J=1,N
68 ISN R(J,I)=TEMP(INDEX(J))
69 ISN CONTINUE
70 ISN IS=1
71 ISN RR=R(1,4)
72 ISN RSHELL(1)=0.00
73 ISN WRITE(6,2)IS,RSHELL(IS)
74 ISN DO 50 I=2,N
75 ISN ISHELL(I-1)=IS
76 ISN IF((R(1,4)-RR).LT.1.0-9)GOTO50
77 ISN IS=IS+1
78 ISN IF(IS.GT.80)STOP0800
79 ISN
80 ISN RR=R(1,4)
81 ISN RSHELL(IS)=DSQRT(R(1,1)**2+R(1,2)**2+R(1,3)**2)
82 ISN WRITE(6,1)IS,RSHELL(IS)
83 ISN CONTINUE
84 ISN ISHELL(N)=IS
85 ISN DO 60 I=1,N
86 ISN R(1,4)=RSHELL(ISHELL(I))
87 ISN ISHELL(N)=IS
88 ISN RETURN
89 ISN 1 FORMAT(1X,12,2X,F13.7)
90 ISN 2 FORMAT(//,1'DISTANCES OF SHELLS USED',/,1X,12,2X,F13.7)
91 ISN END

```

STATISTICS SOURCE STATEMENTS = 87, PROGRAM SIZE = 32186 BYTES, PROGRAM NAME = GENFCC PAGE: 9.

STATISTICS NO DIAGNOSTICS GENERATED.

GENFCC END OF COMPILATION 6 *****

OPTIONS IN EFFECT: HOLIST NOMAP NOXREF GOSTMT NODRICK SOURCE TERM HOONJECT FIXED NOFIST TRMFLG SRCFLG
HOSYM NORENT HOSDUMP AUTODIR.(NONE) NOSXM
OPT(0) L'ANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOURT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 SUBROUTINE PHIAB(IGRID)
2 IMPLICIT REAL*8(A-H,O-Z)
3 COMMON/ATONS/R(200,4), ISHELL(200), RSHELL(80), DD(80,7), IS,H
4 COMMON/WAVEFN/D(80,3,3), S(80,3,3), RL(80,3)
5 COMMON/DYHAM/PHI(80,3,3), INDEX(80)
6 DATA ITES/0/
7 IF(ITES.NE.0)GOTO5
8 ITES=1
9 DO 20 I=2, IS
10 DO 20 J=1,3
11 RL(I,J)=R(INDEX(I),J)
12 CONTINUE
13 CALL CALCS
14 CALL FORCE1(IGRID)
15 WRITE(6,1)
16 DO 30 I=2, IS
17 DO 25 J=1,3
18 DO 25 K=J,3
19 PHI(I,J,K)=S(I,1,J)*S(I,1,K)*DD(I,1)+S(I,2,J)*S(I,2,K)*DD(I,4)+
20 1 S(I,3,J)*S(I,3,K)*DD(I,6)+
21 2 (S(I,1,J)*S(I,2,K)+S(I,2,J)*S(I,1,K))*DD(I,2)+
22 3 (S(I,1,J)*S(I,3,K)+S(I,3,J)*S(I,1,K))*DD(I,3)+
23 4 (S(I,2,J)*S(I,3,K)+S(I,3,J)*S(I,2,K))*DD(I,5)
24 IF(J.EQ.K)PHI(I,J,K)=PHI(I,J,K)+DD(I,7)
25 IF(J.NE.K)PHI(I,K,J)=PHI(I,J,K)
26 CONTINUE
27 WRITE(6,2)
28 WRITE(6,3)((PHI(I,J,K),K=1,3),J=1,3)
29 CONTINUE
30 RETURN
31 FORMAT('1 FORCE CONSTANTS FOLLOW FOR REFERENCE VECTORS',/)
32 FORMAT('/',/, ' SHELL ',12,/)
33 FORMAT('3(5X,3F15.7,/)')
34 END

```

STATISTICS SOURCE STATEMENTS = 30, PROGRAM SIZE = 2398 BYTES, PROGRAM NAME = PHIAB PAGE: 11.

STATISTICS NO DIAGNOSTICS GENERATED.

PHIAB END OF COMPILATION 7 *****

OPTIONS IN EFFECT: HOLIST NOMAP NOXREF COSTANT MODICK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
HOSYH MOREHT HOSDUMP AUTOBUL(NONE) HOSXH
OPT(O) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOURT(64) CHARLEN(500)

```

*.....1.....2.....3.....4.....5.....6.....7.....8
SUBROUTINE SYMPHI(PHIP, PHI, R1, R2)
  IMPLICIT REAL*8(A-H,O-Z)
  DIMENSION PHIP(3,3), PHI(3,3), R2(3), R1(3)
  INTEGER P(3), S(3)
  SET UP P
C
C
  INDEX 1
  IF(DABS(DABS(R2(1))-DABS(R1(1))))GT.1.D-8)GOTO5
  P(1)=1
  S(1)=1
  IF(R2(1)*R1(1).LT.0.D0)S(1)=-1
  GOTO100
  5  IF(DABS(DABS(R2(1))-DABS(R1(2))))GT.1.D-8)GOTO10
  P(1)=2
  S(1)=1
  IF(R2(1)*R1(2).LT.0.D0)S(1)=-1
  GOTO100
  10 IF(DABS(DABS(R2(1))-DABS(R1(3))))GT.1.D-8)GOTO15
  P(1)=3
  S(1)=1
  IF(R2(1)*R1(3).LT.0.D0)S(1)=-1
  GOTO100
  15 CONTINUE
  WRITE(6,1)(R1(I),I=1,3),(R2(I),I=1,3)
  FORMAT(' CAN NOT DO SYMMETRY TRANSFORMATION -- ABANDONING',/
  1, ' R1,R2',/,1X,3F13.5/,1X,3F13.5)
  STOP00514
C
C
  INDEX 2
  IF(DABS(DABS(R2(2))-DABS(R1(1))))GT.1.D-8)GOTO20
  IF(P(1).EQ.1)GOTO20
  P(2)=1
  S(2)=1
  IF(R2(2)*R1(1).LT.0.D0)S(2)=-1
  GOTO200
  20 IF(DABS(DABS(R2(2))-DABS(R1(2))))GT.1.D-8)GOTO25
  IF(P(1).EQ.2)GOTO25
  P(2)=2
  S(2)=1
  IF(R2(2)*R1(2).LT.0.D0)S(2)=-1
  GOTO200
  25 IF(DABS(DABS(R2(2))-DABS(R1(3))))GT.1.D-8)GOTO15
  IF(P(1).EQ.3)GOTO15
  P(2)=3
  S(2)=1
  IF(R2(2)*R1(3).LT.0.D0)S(2)=-1
  GOTO200
C
  INDEX 3
  IF(DABS(DABS(R2(3))-DABS(R1(1))))GT.1.D-8)GOTO30
  IF(P(1).EQ.1.OR.(P(2).EQ.1))GOTO30
  P(3)=1
  S(3)=1
  IF(R2(3)*R1(1).LT.0.D0)S(3)=-1
  GOTO300
  30 IF(DABS(DABS(R2(3))-DABS(R1(2))))GT.1.D-8)GOTO35
  IF(P(1).EQ.2.OR.(P(2).EQ.2))GOTO35
  P(3)=2
  
```

```

*.....1.....2.....3.....4.....5.....6.....7.....8
59 S(3)=1
60 IF(R2(3)*R1(2).LT.0.D0)S(3)=-1
61 GOT0300
62
63 35 IF(DABS(DABS(R2(3))-DABS(R1(3))).GT.1.D-8)GOTO15
64 IF((P(1).EQ.3).OR.(P(2).EQ.3))GOTO15
65 P(3)=3
66 S(3)=1
67 IF(R2(3)*R1(3).LT.0.D0)S(3)=-1
68 CONTINUE
69 C SET UP PHIP
70 DO 50 I=1,3
71 DO 50 J=1,3
72 PHIP(I,J)=DFLOAT(S(I)*S(J))*PHI(P(I),P(J))
73 CONTINUE
74 RETURN
75 END

```

STATISTICS SOURCE STATEMENTS = 66, PROGRAM SIZE = 2708 BYTES, PROGRAM NAME = SYMPHI PAGE: 12.

STATISTICS NO DIAGNOSTICS GENERATED.

SYMPHI END OF COMPILATION 8 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF GOSTMT NODRCK SOURCE TERM NOORJECT FIX'D NOTEST TRMFLG SRCFLG
ROSYH NORENT NOSDUMP AUTODBL(NONE) NOSXH
OPT(0) LANGLVL(77) MOFIPS FLAG(1) NAME(MAIN) LINECOURT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  K SUBROUTINE READQ
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMMON/VECTOR/Q(2000,3),WEIGHT(2000),NQ
4  COMMON/PARMS/XX(3),AO,RMAX,IGRID
5  DATA PI/3.1415926535897932300/
6  FORMAT(4F10.0)
7  FORMAT(1X,14,3F12.7,3X,F13.6)
8  FORMAT(1 Q-VECTORS AND WEIGHTS - UNITS 2*PI/AO =',F9.6,./.)
9  PREF=2.DO*PI/AO
10  NQ=0
11  WRITE(6,3)PREF
12  READ(5,1,END=20)(Q(NQ+1),I=1,3),WEIGHT(NQ+1)
13  NQ=NQ+1
14  WRITE(6,2)NQ,(Q(NQ,1),I=1,3),WEIGHT(NQ)
15  Q(NQ,1)=PREF*Q(NQ,1)
16  Q(NQ,2)=PREF*Q(NQ,2)
17  Q(NQ,3)=PREF*Q(NQ,3)
18  GOTO10
19  RETURN
20  END

```

STATISTICS SOURCE STATEMENTS = 20, PROGRAM SIZE = 1186 BYTES, PROGRAM NAME = READQ PAGE: 14.
STATISTICS NO DIAGNOSTICS GENERATED.
READQ END OF COMPILATION 9 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF GOSTMT HODECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFIG SRCFLG
 NOSYM MORERT NOSDUMP AUTODBL(NONE) NOSXM
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE DYNAM1(WAV,FS)
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMMON/VECTOR/Q(2000,3),WEIGHT(2000),HQ
4  COMMON/ATOMS/R(2400,4),ISHELL(2400),RSHELL(80),DD(80,7),IS,H
5  COMMON/WAVEFH/D(80,3,3),S(80,3,3),RL(80,3)
6  COMMON/DYNAM/PHI(80,3,3),INDEX(80)
7  COMMON/PARMS/BETA,HB,MASS,AO,RMAX,IGRID
8  REAL*8 MASS
9  DIMENSION DYN(3,3),VEC(3,3),PP(3,3),W2(3),IPER(6,3),QI(3)
10 DIMENSION ISG(3),W(3),WORK(10)
11 DATA ITES/0/
12 DATA DAMP/0.300D0/
13 IF(ITES.NE.0)GOTO7
14 IPER(1,1)=1
15 IPER(1,2)=2
16 IPER(1,3)=3
17 IPER(2,1)=1
18 IPER(2,2)=3
19 IPER(2,3)=2
20 IPER(3,1)=2
21 IPER(3,2)=1
22 IPER(3,3)=3
23 IPER(4,1)=2
24 IPER(4,2)=3
25 IPER(4,3)=1
26 IPER(5,1)=3
27 IPER(5,2)=1
28 IPER(5,3)=2
29 IPER(6,1)=3
30 IPER(6,2)=2
31 IPER(6,3)=1
32 CALL GENFCC(AO,RMAX)
33 CALL FORCEO
34 CALL READQ
35 ITES=1
36 CONTINUE.
37 WAV=0.D0
38 FS=0.D0
39 IF(ITES.NE.1)CALL PH1AB(IGRID)
40 ITES=ITES+1
41 DO 5 I=2,IS
42 DO 5 J=1,3
43 DO 5 K=1,3
44 D(I,J,K)=DAMP*D(I,J,K)
45 WRITE(6,4)
46 DO 1000 IQ=1,IQ
47 DO 9 I=1,3
48 DO 9 J=1,3
49 DYN(I,J)=0.D0
50 DO 20 K=2,H
51 NSHELL=ISHELL(K)
52 IREF=INDEX(NSHELL)
53 W2(I)=R(IREF,I)
54 W(I)=R(K,I)
55 DO 11 J=1,3
56 DO 11 J=1,3
57 I
  
```

*.....1.....2.....3.....4.....5.....6.....7.....8

```

58 11  VEC(1,J)=PHI(NSHELL,I,J)
59    CALL SYMPHI(PP,VEC,W2,W)
60    DO 15 I=1,3
61    DYH(1,J)=DYH(I,J)+(DCOS(Q(IQ,1))*R(K,1)+Q(IQ,2))*R(K,2)+
62      1 Q(IQ,3)*R(K,3)-1.DO)*PP(1,J)/MASS
63    CONTINUE
64    DO 20 I=1,3
65    DO 20 J=1,3
66    IF(1.NE.J)DYH(J,I)=DYH(I,J)
68    CONTINUE
69    CALL EIGRS(DYN,3,11,W2,VEC,3,WORK,IER)
70    IF(W2(1).GE.0.DO)GOTO22
71    WRITE(6,3)
72    WRITE(6,1)(W2(J),J=1,3)
73    STOP
74    W(1)=DSQRT(W2(1))
75    DO 25 I=1,6
76    DO 25 IS1=1,2
77    ISG(1)=2*IS1-3
78    DO 25 IS2=1,2
79    ISG(2)=2*IS2-3
80    DO 25 IS3=1,2
81    ISG(3)=2*IS3-3
82    DO 30 I=1,3
83    QI(I)=DFLOAT(ISG(I))*Q(IQ,IPER(I,I))
84    DO 30 J=1,3
85    DYN(I,J)=DFLOAT(ISG(J))*VEC(IPER(I,I),J,1)
86    IREF=INDEX(NSHELL)
87    IREF=IB*(1.DO-DCOS(QI(1)*R(IREF,1)+QI(2)*R(IREF,2)+
88      1 QI(3)*R(IREF,3))*WEIGHT(IQ)*(1.DO-DAMP))/(48.DO*MASS)
89    DO 40 IBR=1,3
90    BINW=0.5DO*BETA*IBW*(IBR)
91    PREF2=DCOTR(BINW)/W(IBR)
92    PREF3=DLOG(2.DO*DSINH(BINW))/BETA-0.25DO*IBW*(IBR)*DCOTR(BINW)
93    FS=FS+PREF3*WEIGHT(IQ)
94    DO 40 I=1,3
95    DO 40 J=1,3
96    D(NSHELL,I,J)=D(NSHELL,I,J)+PREF*PREF2*DYN(IBR,I)*DYN(IBR,J)
97    CONTINUE
98    CONTINUE
99    WAV=WAV+(W(1)+W(2)+W(3))*WEIGHT(IQ)
100  WRITE(6,2)(Q(IQ,I),I=1,3),(W(I),I=1,3)
101  WAV=WAV/DFLOAT(3)
102  WRITE(6,6)WAV,FS.
103  RETURN
104  FORMAT(' W2',3F13.6)
105  FORMAT('X,3F12.7,4X,3F12.7)
106  FORMAT(' FREQUENCY IMAGINARY .. ABANDONING CALCULATION **')
107  FORMAT(' Q-VECTORS AND FREQUENCIES FOLLOW - 3 BRANCHES',/)
108  FORMAT('/',, W-AVERAGE =,F11.8,5X, FS =,F13.5)
109
110

```

STATISTICS SOURCE STATEMENTS = 108, PROGRAM SIZE = 5180 BYTES, PROGRAM NAME = DYNAM1 PAGE: 15.

STATISTICS NO DIAGNOSTICS GENERATED.

DYNAM1 END OF COMPILATION 10 *****

OPTIONS IN EFFECT: HOLLIST HOMAP HOSREF GOSTHT MODECK SOURCE TERM NOORJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYH NORENT NOSDUMP AUTODBL(NONE) NOSXH
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

1 ISH
 2 ISH
 3 ISH
 4 ISH
 5 ISH

BLOCK DATA
 IMPLICIT REAL*8(A-H,O-Z)
 COMMON/WAVEFH/D(80,3,3),S(80,3,3),RL(80,3)
 DATA D/720*0.00/
 END

STATISTICS SOURCE STATEMENTS = 5, PROGRAM SIZE = 0 BYTES, PROGRAM NAME = BLKDT# PAGE: 17.

STATISTICS NO DIAGNOSTICS GENERATED.

BLRDT# END OF COMPILATION 11 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTMT NOCHECK SOURCE TERM NOOBJECT FIXED NOTEST TRMFLG SRCFLG
 NOSYM NORENT NOSDUMP AUTODBL(NONE) NOSXH
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  SUBROUTINE READIN
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMMON/PARMS/BETA,IBAR,MASS,AO,RMAX,IGRID
4  REAL*8 MASS
5  IBAR=7.6382829D0
6  BOLTZ=1.D0
7  READ(5,1)MASS,AO,T,RMAX,IGRID
8  WRITE(6,2)
9  WRITE(6,3)MASS,AO,T,RMAX,IGRID
10 MASS=MASS*1.2027313D0
11 BETA=1.D0/(T*BOLTZ)
12 WRITE(6,4)
13 RETURN
14 FORMAT(4F10.0,15)
15 FORMAT(1H1)
16 FORMAT(' MASS =',F9.5,' A.M.U.',/, ' AO =',F9.5,' ANGSTROMS',/,
17 ' TEMP =',F9.5,' DEGREES K',/, ' RMAX,IGRID',F9.4,14)
18 FORMAT(/,/, ' ALL FREQUENCIES IN THZ (10E12 HZ)',/)
    END
    
```

STATISTICS SOURCE STATEMENTS = 18, PROGRAM SIZE = 800 BYTES, PROGRAM NAME = READIN PAGE: 18.

STATISTICS NO DIAGNOSTICS GENERATED.

READIN END OF COMPILATION 12.*****

OPTIONS IN EFFECT: ROLIST NOHAP NOXREF CCONST NODECK SOURCE TERM NOOBJECT FIXED NOTEST TRNFLG SRCFLG
ROSYN HORERT MODUMP AUTODBL(RONE) ROSXH
OPT(0) LANGLV(77) NOFPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 ISH FUNCTION DCOTH(X)
2 ISH IMPLICIT REAL*8(A-H,O-Z)
3 ISH IF(X.GT.50.DO)GOTO5
4 ISH IF(X.LT.-50.DO)GOTO10
5 ISH E1=DEXP(2.DO*X)
6 ISH DCOTH=(E1+1.DO)/(E1-1.DO)
7 ISH RETURN
8 ISH DCOTH=1.DO
9 ISH RETURN
10 ISH DCOTH=-1.DO
11 ISH RETURN
12 ISH END

```

STATISTICS SOURCE STATEMENTS = 12, PROGRAM SIZE = 552.BYTES, PROGRAM NAME = DCOIH. PAGE: 19.

STATISTICS NO DIAGNOSTICS GENERATED.

DCOTH END OF COMPILATION 13 *****

OPTIONS IN EFFECT: ROLLST ROMAP ROXREF GOSTMT RODECK SOURCE TERM ROBJECT FIXED NOTEST TRMFLG SRCFLG
ROSYH MOREHT NOSDUMP AUTODBL(NONE) ROSXH
OPT(0) LANGLVL(77) ROFIPS FLAG(1) NAME(MAIN) L(ACCOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 SUBROUTINE DYNAM2
2 IMPLICIT REAL*8(A-H,O-Z)
3 COMMON/VECTOR/Q(2000,3),WEIGHT(2000),RQ
4 COMMON/ATOMS/R(2400,4),ISHELL(2400),RSHELL(80),DD(80,7),IS,N
5 COMMON/WAVEFN/D(80,3,3),S(80,3,3),RL(80,3)
6 COMMON/DYNAM/PHI(80,3,3),INDEX(80)
7 COMMON/PARMS/BETA,HB,MASS,A0,RMAX,IGRID
8 REAL*8 MASS
9 DIMENSION DYH(3,3),VEC(3,3),PP(3,3),W2(3),QT(3),WORK(10)
10 DIMENSION ISC(3),W(3)
11 DATA THOPI/6.28318530800/
12 DATA CONV/4.1356700/
13 DO 1000 IQ=1,RQ
14 DO 9 I=1,3
15 DO 9 J=1,3
16 DYH(I,J)=0.00
17 DO 20 K=2,N
18 RSHELL=ISHELL(K)
19 IREF=INDEX(RSHELL)
20 DO 11 I=1,3
21 W2(I)=R(IREF,I)
22 W(I)=R(K,I)
23 DO 11 J=1,3
24 VEC(I,J)=PHI(RSHELL,I,J)
25 CALL SYMPHI(PP,VEC,W2,W)
26 DO 15 I=1,3
27 DO 15 J=1,3
28 DYH(I,J)=DYH(I,J)+(DCOS(Q(IQ,1)*R(K,1)+Q(IQ,2)*R(K,2)+
1 Q(IQ,3)*R(K,3))-1.00)*PP(I,J)/MASS
29 CONTINUE
30 DO 20 I=1,3
31 DO 20 J=1,3
32 IF(1.NE.J)DYH(J,I)=DYH(I,J)
33 CONTINUE
34 CALL EIGRS(DYH,3,11,W2,VEC,3,WORK,IER)
35 DO 22 I=1,3
36 IF(W2(I).GE.0.00)GOTO22
37 WRITE(6,3)
38 WRITE(6,1)(W2(J),J=1,3)
39 STOP
40 W(1)=DSQRT(W2(1))/THOPI
41 WRITE(6,2)(Q(IQ,I),I=1,3),(W(I),I=1,3)
42 W(1)=W(1)*CONV
43 W(2)=W(2)*CONV
44 W(3)=W(3)*CONV
45 WRITE(6,4)W(1),W(2),W(3)
46 RETURN
47 FORMAT(' W2',3F13.6)
48 FORMAT('X,3F12.7,4X,3F12.7)
49 FORMAT(' FREQUENCY IMAGINARY .. ABANDONING CALCULATION **')
50 FORMAT('41X,3F12.7,/)
51 END

```

LEVEL 1.4.0 (OCT 1984)

VS (ORTRAM)

DATE: SEP 17, 1985

TIME: 08:16:09

NAME: DYNAM2 PAGE: 21

DYNAM2 END OF COMPILATION 14 *****

OPTIONS IN EFFECT: NOLIST NOMAP NOXREF COSTRT NODDECK SOURCE TERM NOOBJECT FIXED NOFEST TRMFLG SRCFLG
 MOSYH MORENT ROSDUMP AUTODBI(HOHE) MOSXH
 OPT(0) LANGLVL(77) NOFIPS FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 ISH SUBROUTINE BRANCH
2 ISH IMPLICIT REAL*8(A-H,O-Z)
3 ISH COMMON/VECTOR/Q(2000,3),WEIGHT(2000),NQ
4 ISH COMMON/PAIRS/XX(3),A0,RMAX,IGRID
5 ISH DATA PI/3.14159265358979323846
6 ISH PREF=2.00*PI/A0
7 ISH NQ=20
8 ISH WRITE(6,1)
9 ISH WRITE(6,2)
10 ISH DO 10 I=1,20
11 ISH Q(I,1)=PREF*DFLOAT(I)/20.00
12 ISH Q(I,2)=0.00
13 ISH Q(I,3)=0.00
14 ISH CALL DYH2
15 ISH WRITE(6,1)
16 ISH WRITE(6,2)
17 ISH DO 20 J=1,20
18 ISH Q(J,1)=PREF*DFLOAT(J)/40.00
19 ISH Q(J,2)=PREF*DFLOAT(J)/40.00
20 ISH Q(J,3)=PREF*DFLOAT(J)/40.00
21 ISH CALL DYH2
22 ISH WRITE(6,1)
23 ISH WRITE(6,2)
24 ISH DO 30 I=1,20
25 ISH Q(I,1)=4.00*PREF*DFLOAT(I)/80.00
26 ISH Q(I,2)=4.00*PREF*DFLOAT(I)/80.00
27 ISH Q(I,3)=0.00
28 ISH CALL DYH2
29 ISH RETURN
30 ISH FORMAT('1 DOING SPECIAL DIRECTION',/)
31 ISH FORMAT(19X,'Q',26X,'FREQUENCY(HZ) / ENERGY(MEV)',/,/)
32 ISH END

```

STATISTICS SOURCE STATEMENTS = 32, PROGRAM SIZE = 1270 BYTES, PROGRAM NAME = BRANCH PAGE: 22.

STATISTICS NO DIAGNOSTICS GENERATED.

BRANCH END OF COMPILATION 15 *****

OPTIONS IN EFFECT: HOLLIST HOPAP HOPREF .COSINT HODECK SOURCE TERM HODRJECT FIXED HODEST TRMFLG SRCFLG
 HOSYH HOREHT HOSDURP .AUTODBL(HOHE) HOSXN
 OPT(O) LANGLVL(77) HOFIPS .FLAG(1) NAME(MAIN) LINECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1  C FUNCTION AZIZ(R)
2  C AZIZ CHEM POTENTIAL FOR ARGON HFD-C
3  C J. CHEM. PHYS. 67,5719 (1977)
4  C UNITS R IN ANGSTROMS , ENERGIES AZIZ IN DEGREES K
5  C .IMPLICIT REAL*8(A-H,O-Z)
6  C DATA A/O.9502720D//
7  C DATA ALPHA/16.345655D0/
8  C DATA C6 /1.091425400/
9  C DATA C8 /0.600259500/
10 C DATA C10/0.3700113D0/
11 C DATA D/1.400/
12 C DATA E/143.22400/
13 C DATA GAMMA/2.00/
14 C DATA RH/3.75900/
15 C KRYPTON -- MOL. PHYS. 38,111 (1979)
16 C DATA A/O.121531200/
17 C DATA ALPHA/16.496763D0/
18 C DATA C6 /1.156173900/
19 C DATA C8 /0.541492300/
20 C DATA C10/0.283973500/
21 C DATA D/1.2800/
22 C DATA E/199.90000/
23 C DATA GAMMA/2.400/
24 C DATA RH/4.01200/
25 C X=R/RH
26 C AZIZ=-((C6/X**6+C8/X**8+C10/X**10)
27 C DX=D/X
28 C IF((DX.GT.1.00).AND.(DX.LT.11.00))AZIZ=AZIZ*DEXP(-(DX-1.00)**2)
29 C IF(DX.GE.11.00)AZIZ=0.00
30 C AX=ALPHA*X
31 C IF(AX.GT.125.00)GOTO10
32 C AZIZ=AZIZ+AX*DEXP(-AX)*X**GAMMA
33 C CONTINUE
34 C AZIZ=E*AZIZ
35 C RETURN
36 C END

```

STATISTICS SOURCE STATEMENTS = 23, PROGRAM SIZE = 904 BYTES, PROGRAM NAME = AZIZ PAGE: 23.

STATISTICS NO DIAGNOSTICS GENERATED.

AZIZ END OF COMPILATION 16 *****

OPTIONS IN EFFECT: HOLIST NOMAP ROSREF GOSHI MODICK SOURCE TERM NOOBJECT FIXED ROTEST TERMIG SRCFIG
ROSYM MOREHT ROSDUMP AUTODIR (HORI) ROSXII
OPT(4) LARGV(77) ROTIPS FLAG(1) RARE(MATH) (RECCOUR(64) CHARPR(500)

*.....1.....2.....3.....4.....5.....6.....7.....8.....9.....

```

1  FUNCTION AVEO(LDUMMY)
2  IMPLICIT REAL*8(A-H,O-Z)
3  COMMON/SPHER/R(20000,3),CH(20000),H1,H2,H3
4  COMMON/ATOMS/M(2400,4),ISH(2400),RSR(1(60),DD(80,7),IS,M
5  COMMON/HIDIB/A(80,3),RM(80,3)
6  REAL*8 R
7  DATA EPS/2.D-6/
8  DATA PI/3.1415926535897931307/
9  WRITE(6,2)
10 AVEO=0.D0
11 DO 1000 ISHELL=2,15
12 X=RM(ISHLL,1)
13 Y=RM(ISHLL,2)
14 Z=RM(ISHLL,3)
15 A1=A(ISHLL,1)
16 A2=A(ISHLL,2)
17 A3=A(ISHLL,3)
18 RM=DSQR((-2.D0*DILOG(EPS)/A1)
19 RM2=DSQR((-2.D0*DILOG(EPS)/A2)
20 RM3=DSQR((-2.D0*DILOG(EPS)/A3)
21 S1=0.D0
22 S2=0.D0
23 S3=0.D0
24 DO 10 I=1,R3
25 R1=RM1*(I,1)
26 R2=RM2*(I,2)
27 R3=RM3*(I,3)
28 C1=R1*X
29 C2=R2*Y
30 C3=R3*Z
31 THD=TH(I)
32 DIST=DSQR(C1*C1+C2*C2+C3*C3)
33 PREF=DEXP(-0.500*(A1*R1+R1*A2*R2+R2*A3*R3+R3))
34 SS=A7/(DIST)*PREF
35 S1=S1+SS
36 IF(IRD.IQ.3)GO1010
37 S2=S2+SS
38 IF(IRD.IQ.2)GO1010
39 S1=S1+SS
40 CONTINUE
41 PREF=DSQR(A1*A2*A3/(2.D0*PI)**3)
42 VOL=(4.D0*PI/3.D0)*RM1*RM2*RM3
43 P1=PREF*VOL/DELTA(45*H1)
44 P2=-20.D0*PREF*VOL/DELTA(45*H2)
45 P3=64.D0*PREF*VOL/DELTA(45*H3)
46 AVERAG=P1*S1+P2*S2+P3*S3
47 WRITE(6,1)ISHLL,AVERAG
48 WRITE(6,3)A(ISHLL,1),A(ISHLL,2),A(ISHLL,3)
49 WRITE(6,4)X,Y,Z
50 AVEO=AVEO+AVERAG
51 CONTINUE
52 WRITE(6,5)AVEO
53 RETURN
54 FORMAT(1,ISHLL,AVERAGE',I2,3X,D13.5)
55 FORMAT(1,1 COMPUTE AVERAGE OF A7/2-CHEM POTENTIAL',/,/)
56 FORMAT(1, A1,A2,A3',3F13.7)

```

```
1SH 57 4 FORMAT(' R1,R2,R3 ',3F13.7,/)
1SH 58 5 FORMAT('/',/,',',RET AVEO =',F14.7)
1SH 59 END
```

STATISTICS SOURCE STATEMENTS = 59, PROGRAM SIZE = 2530 BYTES, PROGRAM NAME = AVEO PAGE: 24.

STATISTICS NO DIAGNOSTICS GENERATED.

AVEO END OF COMPILATION 17 *****

OPTIONS IN EFFECT: HOLLIST KOMAP NOXREF COSTMT HODECK SOURCE TERM NOOBJECT FIXED MOTEST TRMFLG SACFLG
 NOSYM NORENT NOSDUMP AUTODBL(HORE) NOSXH
 OPT(0) LANGLVL(77) ROTIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLEN(500)

*.....1.....2.....3.....4.....5.....6.....7.....8

```

1 ISH SUBROUTINE DDAZIZ(R,01,02)
2 ISH /ZIZ-CHEM POTENTIAL BY INTERPOLATION
3 ISH /IMPLICIT REAL*8(A-H,O-Z),LOGICAL(S)
4 ISH DIMENSION X1(10000),X2(10000)
5 ISH DATA SFIRST/.FALSE./
6 ISH COMMON/ATOMS/H(9600),ISHELL(2400),RSHELL(80),DD(80,7),IS,N
7 ISH IF(SFIRST)GOTO90
8 ISH SFIRST=.TRUE.
9 ISH RMAX=6.DD+RSHELL(1S)
10 ISH DELTA=RMAX/DFLOAT(10000)
11 ISH DO 10 I=1,10000
12 ISH CALL DAZIZ(DELTA*DFLOAT(I),01,02)
13 ISH X1(I)=01
14 ISH X2(I)=02
15 ISH CONTINUE
16 ISH I=R/DELTA
17 ISH IF(I.LE.1)GOTO60
18 ISH IF(I-10000)30,20,40
19 ISH I=I-1
20 ISH RO=DELTA*DFLOAT(I)
21 ISH DEL=R-RO
22 ISH 01=X1(I)+DEL*(0.500*(X1(I+1))-X1(I-1))+DEL*(X1(I+1)+X1(I-1))-
23 ISH 2.D0*X1(I)/DELTA/DELTA
24 ISH 02=X2(I)+DEL*(0.500*(X2(I+1))-X2(I-1))+DEL*(X2(I+1)+X2(I-1))-
25 ISH 2.D0*X2(I)/DELTA/DELTA
26 ISH RETURN
27 ISH 01=X1(I)
28 ISH 02=X2(I)
29 ISH RETURN
30 ISH END

```

STATISTICS SOURCE STATEMENTS = 30, PROGRAM SIZE = 161286 BYTES, PROGRAM NAME = DDAZIZ PAGE: 26.

STATISTICS NO DIAGNOSTICS GENERATED.

DDAZIZ END OF COMPILATION 18 *****

OPTIONS IN EFFECT: HOLLIST HOMAP HOSXREF COSTMT NODECK SOURCE TERM NOORJECT FIXED NOTEST TRMFLG SRCFLG
 HOSYH HORENT HOSDUMP AUTODDBI(NONE) HOSXH
 OPT(0) LANGLVL(77) HOFIPS FLAG(1) NAME(MAIN) LIRECOUNT(64) CHARLER(500)

```

* .....1 .....2 .....3 .....4 .....5 .....6 .....7 .....8
1 SUBROUTINE FORCEO
2 IMPLICIT REAL*8(A-H,O-Z)
3 COMMON/ATOMS/R(2400,4), ISH(2400), RSHELL(80), OD(80,7), IS,N
4 COMMON/DYNAM/PHI(80,3,3), INDEX(80)
5 DIMENSION FOR(3,3)
6 FORMAT(1, 'NON-AVERAGED FORCE CONSTANTS - UNITS DEG K/A**2')
7 FORMAT(1, 'SHELL', I3, '/')
8 FORMAT(3(1X,3F15.7, '/))
9 FORMAT(1, 'REFERENCE VECTORS FOR SHELLS 2 TO 15', '/')
10 FORMAT(1X,12,2X,3F13.7,116.7)
11 FORMAT(1, '*** NOW DO HARMONIC DISPERSION CURVES ***')
12 INDEX(1)=1
13 J=1
14 DO 10 I=2,N
15 IF(ISH(I-1).EQ.ISH(I))GO1010
16 J=J+1
17 INDEX(J)=I
18 CONTINUE
19 IF(J.EQ.15)STOP00700
20 WRITE(6,4)
21 DO 9 I=2,15
22 WRITE(6,5)I,(R(INDEX(I),J),J=1,3),RSHELL(I)
23 WRITE(6,1)
24 DO 20 I=2,15
25 RR=RSHELL(I)
26 WRITE(6,2)I
27 CALL DAZI2(RR,01,02)
28 DO 15 J=1,3
29 DO 15 K=1,3
30 FOR(J,K)=-R(INDEX(I),J)*R(INDEX(I),K)*02/RR**2
31 DO 16 J=1,3
32 FOR(J,J)=FOR(J,J)-01
33 DO 17 J=1,3
34 DO 17 K=1,3
35 PHI(I,J,K)=FOR(J,K)
36 WRITE(6,3)((FOR(J,K),K=1,3),J=1,3)
37 WRITE(6,6)
38 CALL BRANCH
39 RETURN
40 END
41

```

STATISTICS SOURCE STATEMENTS = 40, PROGRAM SIZE = 2156 BYTES, PROGRAM_NAME = FORCEO PAGE: 27.

STATISTICS NO DIAGNOSTICS GENERATED.

FORCEO END OF COMPILATION 19 *****